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Xyce™ Parallel Electronic Simulator

Reference Guide, Version 4.0

Eric R. Keiter, Scott A. Hutchinson, Robert J. Hoekstra, Thomas V. Russo, Eric L. Rankin, Roger P. Pawlowski, Richard L. Schiek, Todd S. Coffey, Heidi K. Thornquist, Deborah A. Fixel, David N. Shirley and Phillip M. Campbell

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Abstract

This document is a reference guide to the **Xyce** Parallel Electronic Simulator, and is a companion document to the **Xyce** Users' Guide. The focus of this document is (to the extent possible) exhaustively list device parameters, solver options, parser options, and other usage details of **Xyce**. This document is *not* intended to be a tutorial. Users who are new to circuit simulation are better served by the **Xyce** Users' Guide.

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1. Introduction

Welcome to **Xyce**

The **Xyce** Parallel Electronic Simulator has been written to support, in a rigorous manner, the simulation needs of the Sandia National Laboratories electrical designers. It is targeted specifically to run on large-scale parallel computing platforms but also runs well on a variety of architectures including single processor workstations. It also aims to support a variety of devices and models specific to Sandia needs.

1.1 Overview

This document is intended to compliment the **Xyce** Users' Guide [1]. It contains comprehensive, detailed information about a number of topics pertinent to the usage of **Xyce**. Included in this document is a netlist reference for the input-file commands and elements supported within **Xyce**; a command line reference, which describes the available command line arguments for **Xyce**; and quick-references for users of other circuit codes, such as Orcad's PSpice [2] and Sandia's ChileSPICE.

1.2 How to Use this Guide

This guide is designed so you can quickly find the information you need to use **Xyce**. It assumes that you are familiar with basic Unix-type commands, how Unix manages applications and files to perform routine tasks (e.g., starting applications, opening files and saving your work). Note that while Windows versions of **Xyce** are available, they are command-line programs meant to be run under the "Command Prompt," and are used almost identically to their Unix counterparts.

Typographical conventions

Before continuing in this Reference Guide, it is important to understand the terms and typographical conventions used. Procedures for performing an operation are generally numbered with the following typographical conventions.

Notation	Example	Description
`Verbatim text`	`xmpirun -np 4`	Commands entered from the keyboard on the command line or text entered in a netlist.
Bold Roman Font	Set nominal temperature using the **TNOM** option.	SPICE-type parameters used in models, etc.
Gray Shaded Text	DEBUGLEVEL	Feature that is designed primarily for use by **Xyce** developers.
`[text in brackets]`	`Xyce [options] <netlist>`	Optional parameters.
`<text in angle brackets>`	`Xyce [options] <netlist>`	Parameters to be inserted by the user.
`<object with asterisk>*`	`K1 <ind. 1> [<ind. n>*]`	Parameter that may be multiply specified.
`<TEXT1|TEXT2>`	`.PRINT TRAN` `+ DELIMITER=<TAB|COMMA>`	Parameters that may only take specified values.

Table 1.1. **Xyce** typographical conventions.

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2. Netlist Reference

Chapter Overview

This chapter contains reference material directed towards working with circuit analyses in **Xyce** using the netlist interface. Included are detailed command descriptions, start-up option definitions and a list of devices supported by the **Xyce** netlist interface.

2.1 Netlist Commands

This section outlines the netlist commands that can be used with **Xyce** to setup and control circuit analysis.

DC Sweep Analysis

Calculates the operating point for the circuit for a range of values. Primarily, this capability is applied to independent voltage sources, but it can also be applied to most device parameters. Note that this may be repeated for multiple sources in the same `.DC` line.

The .DC command can specify a linear sweep, decade logarithmic sweep, octave logarithmic sweep, or a list of values.

Parameter	Description	Meaning
LIN	linear sweep	The sweep variable is swept linearly from the starting to the ending value.
OCT	sweep by octaves	Sweep by octaves. The sweep variable is swept logarithmically by octaves.
DEC	sweep by decades	Sweep by decades. The sweep variable is swept logarithmically by decades.
LIST	list of values	Use a list of values.

Linear Sweeps

General Form

```
.DC [LIN] <sweep variable name> <start> <stop> <step>
+ [<sweep variable name> <start> <stop> <step>]...
```

Examples

```
.DC LIN V1 5 25 5

.DC VIN -10 15 1

.DC R1 0 3.5 0.05 C1 0 3.5 0.5
```

Decade Sweeps

General Form

```
.DC DEC <sweep variable name> <start> <stop> <points>
+ [DEC <sweep variable name><start> <stop> <points>]...
```

Examples

```
.DC DEC VIN 1 100 2

.DC DEC R1 100 10000 3 DEC VGS 0.001 1.0 2
```

Octave Sweeps

General Form

```
.DC OCT <sweep variable name> <start> <stop> <points>
+ [OCT <sweep variable name><start> <stop> <points>]...
```

Examples

```
.DC OCT VIN 0.125 64 2

.DC OCT R1 0.015625 512 3 OCT C1 512 4096 1
```

List Sweeps

General Form

```
.DC <sweep variable name> LIST <val> <val> <val> ...
+ [<sweep variable name> LIST <val> <val> ...]...
```

Examples

```
.DC VIN LIST 1.0 2.0 5.0 6.0 10.0

.DC VDS LIST 0 3.5 0.05 VGS LIST 0 3.5 0.5
.DC TEMP LIST 10.0 15.0 18.0 27.0 33.0
```

STEP Parametric Analysis

Calculates a full analysis (`.DC` or `.TRAN`) over a range of parameter values. This type of analysis is very similar to .DC analysis. Similar to .DC analysis, .STEP supports sweeps which are linear, decade logarithmic, octave logarithmic, or a list of values.

Parameter	Description	Meaning
LIN	linear sweep	The sweep variable is swept linearly from the starting to the ending value.
OCT	sweep by octaves	Sweep by octaves. The sweep variable is swept logarithmically by octaves.
DEC	sweep by decades	Sweep by decades. The sweep variable is swept logarithmically by decades.
LIST	list of values	Use a list of values.

Linear Sweeps

General Form

```
.STEP <parameter name> <initial> <final> <step>
```

Examples

```
.STEP TEMP -45 -55 -10

.STEP R1 45 50 5

.STEP C101:C 45 50 5

.STEP DLEAK:IS 1.0e-12 1.0e-11 1.0e-12

.STEP V1 20 10 -1
```

Arguments and Options

`<initial>`

Initial value for the parameter.

`<final>`

Final value for the parameter.

`<step>`

Value that the parameter is incremented at each step.

Comments

STEP parameter analysis will sweep a parameter from its initial value to its final value, at increments of the step size. At each step of this sweep, it will conduct a full analysis (`.DC` or `.TRAN`) of the circuit.

The specification is similar to that of a `.DC` sweep, except that each parameter gets its own `.STEP` line in the input file, rather than specifying all of them on a single line.

Output, as designated by a `.PRINT` statement, is slightly more complicated in the case of a `.STEP` simulation. If the user has specified a `.PRINT` line in the input file, **Xyce** will output two files. All steps of the sweep to a single output file as usual, but with the results of each step appearing one after another with the "Index" column starting over at zero. Additionally, a file with a ".res" suffix will be produced indicating what parameters were used for each iteration of the step loops.

This is a similar capability to that of PSPICE and ChileSPICE, but not identical. In future releases, this capability will be fully compatible.

Decade Sweeps

General Form

```
.STEP DEC <sweep variable name> <start> <stop> <points>
```

Examples

```
.STEP DEC VIN 1 100 2
.STEP DEC R1 100 10000 3
.STEP DEC TEMP 1.0 10.0 3
```

Octave Sweeps

General Form

```
.STEP OCT <sweep variable name> <start> <stop> <points>
```

Examples

```
.STEP OCT VIN 0.125 64 2
.STEP OCT TEMP 0.125 16.0 2
.STEP OCT R1 0.015625 512 3
```

List Sweeps

General Form

```
.STEP <sweep variable name> LIST <val> <val> <val> ...
+ [<sweep variable name> LIST <val> <val> ...]...
```

Examples

```
.STEP VIN LIST 1.0 2.0 10. 12.0
.STEP TEMP LIST 8.0 21.0
```

Transient Analysis

Calculates the time-domain response of a circuit for a specified duration.

General Form

```
.TRAN <print step value> <final time value>
+[<start time value> [<step ceiling value>]] [NOOP]
```

Examples

```
.TRAN 1us 100ms

.TRAN 1ms 100ms 0ms .1ms
```

Arguments and Options

`<print step value>`

Used to calculate the initial time step (see below).

`<final time value>`

Sets the end time (duration) for the analysis.

`[<start time value>]`

Sets the time at which output of the simulation results is to begin. Defaults to zero.

`[<step ceiling value>]`

Sets a maximum time step. Defaults to ((final time value)-(start time value))/10, unless there are breakpoints (see below).

`[NOOP]`

Specifies that no operating point calculation is to be performed.

Comments

The transient analysis calculates the circuit's response over an interval of time beginning with `TIME=0` and finishing at `<final time value>`. Use a `.PRINT` (print) statement to get the results of the transient analysis.

Before calculating the transient response **Xyce** computes a bias point for the circuit that is different from the regular bias point. This is necessary because at the start of a transient analysis, the independent sources can have different values than their DC values. Specifying `NOOP` on the `.TRAN` line causes **Xyce** to begin the transient analysis without performing the usual bias point calculation.

The time integration algorithms within **Xyce** use adaptive time-stepping methods that adjust the time-step size according to the activity in the analysis. The default ceiling for the internal time step is `(<final time value>-<start time value>)/10`. This default ceiling value is automatically adjusted if breakpoints are present, to insure that there are always at least 10 time steps between breakpoints. If the user specifies a ceiling value, however, it overrides any internally generated ceiling values.

Xyce is not strictly compatible with SPICE in its use of the values on the `.TRAN` line. In **Xyce**, `<print step value>` is not used as the printing interval. It is used in determining the initial step size, which is chosen to be the smallest of three quantities: the print step value, the step ceiling value, and 1/200th of the time until the next breakpoint.

The third argument to `.TRAN` simply determines the earliest time for which results are to be output. Simulation of the circuit always begins at `TIME=0` irrespective of the setting of `<start time value>`.

Device Modeling

.MODEL (Model Definition)

Modeled device definition.

.SUBCKT (subcircuit)

The .SUBCKT statement begins a subcircuit definition by giving its name, the number and order of its nodes and the names and default parameters that direct its behavior. The .ENDS statement signifies the end of the subcircuit definition.

General Form

```
.SUBCKT <name> [node]*
+ [PARAMS: < <name> = <value> >* ]
...
.ENDS
```

Examples

```
.SUBCKT OPAMP 10 12 111 112 13
...
.ENDS

.SUBCKT FILTER1 INPUT OUTPUT PARAMS: CENTER=200kHz,
+ BANDWIDTH=20kHz
...
.ENDS

.SUBCKT PLRD IN1 IN2 IN3 OUT1
+ PARAMS: MNTYMXDELY=0 IO_LEVEL=1
...
.ENDS

.SUBCKT 74LS01 A B Y
+ PARAMS: MNTYMXDELY=0 IO_LEVEL=1
...
.ENDS
```

Arguments and Options

`<name>`

The name used to reference a subcircuit.

`[node]*`

An optional list of nodes. This is not mandatory since it is feasible to define a subcircuit without any interface nodes.

`[PARAMS:]`

Keyword that provides values to subcircuits as arguments for use as expressions in the subcircuit. Parameters defined in the `PARAMS:` section may be used in expressions within the body of the subcircut and will take the default values specified in the subcircuit definition unless overridden by a `PARAMS:` section when the subcircuit is instantiated.

A subcircuit designation ends with a `.ENDS` command. The entire netlist between `.SUBCKT` and `.ENDS` is part of the definition. Each time the subcircuit is called via an `X` device, the entire netlist in the subcircuit definition replaces the `X` device.

There must be an equal number of nodes in the subcircuit call and in its definition. As soon as the subcircuit is called, the actual nodes (those in the calling statement) substitute for the argument nodes (those in the defining statement).

Node zero cannot be used in this node list, as it is the global ground node.

Subcircuit references may be nested to any level. However, their definitions cannot be nested. That is, a `.SUBCKT` statement cannot be placed between a `.SUBCKT` and a `.ENDS` statements.

Comments

Subcircuits should include only device instantiations and possibly these statements:

- `.MODEL` (model definition)
- `.PARAM` (parameter)
- `.FUNC` (function)

Models, parameters, and functions defined within a subcircuit are scoped to that definition. That is they are only accessible within the subcircuit definition in which they are included. Further, if a `.MODEL`, `.PARAM` or a `.FUNC` statement is included in the main circuit netlist, it is accessible from the main circuit as well as all subcircuits.

Node, device, and model names are scoped to the subcircuit in which they are defined. It is allowable to use a name in a subcircuit that has been previously used in the main circuit netlist. When the subcircuit is flattened (expanded into the main netlist), all of its names are given a prefix via the subcircuit instance name. For example, `Q17` becomes `X3:Q17` after expansion. After expansion, all names are unique. The single exception occurs in the use of global node names, which are not expanded.

`.ENDS` (end subcircuit)

Marks the end of a subcircuit definition.

Output Control

.PRINT (print)

Send analysis results to an output file. **Xyce** supports several options on the .PRINT line of netlists:

General Form

```
.PRINT <analysis type> [FORMAT=<STD|NOINDEX|PROBE|TECPLOT>]
+ [FILE=<output filename>] [WIDTH=<print field width>]
+ [PRECISION=<floating point output precision>]
+ [FILTER=<absolute value below which a number outputs as 0.0>]
+ [DELIMITER=<TAB|COMMA>]
+ <output variable>
```

Examples

```
.print tran format=tecplot V(1) I(Vsrc) {V(1)*(I(Vsrc)**2.0)}

.PRINT TRAN FORMAT=PROBE FILE=foobar.csd V(1) {abs(V(1))-5.0}

.PRINT DC FILE=foobar.txt WIDTH=19 PRECISION=15 FILTER=1.0e-10
+ I(VSOURCE5) I(VSOURCE6)
```

```
R1 1 0 100
X1 1 2 3 MySubcircuit
V1 3 0 1V
.SUBCKT MYSUBCIRCUIT 1 2 3
R1 1 2  100K
R2 2 4  50K
R3 4 3  1K
.ENDS
.PRINT DC V(X1:4) V(2) I(V1)
```

Arguments and Options

`<analysis type>`

Only one analysis type (DC or TRAN) may be given for each `.PRINT` netlist entry.

`[FORMAT=<STD|NOINDEX|PROBE|TECPLOT>]`

The output format may be specified using the `FORMAT` option. The `STD` format outputs the data divided up into data columns. The `NOINDEX` format is the same as the `STD` format except that the index column is omitted. The `PROBE` format specifies that the output should be formatted to be compatible with the PSpice Probe plotting utility. The `TECPLOT` format specifies that the output should be formatted to be compatible with the Tecplot plotting program.

`[FILE=<output filename>]`

Specifies the name of the file to which the output will be written.

`[WIDTH=<print field width>]`

Controls the output width used in formatting the output.

`[PRECISION=<floating point precision >]`

Number of floating point digits past the decimal for output data.

`[FILTER=<filter floor value>]`

Used to specify the absolute value below which output variables will be printed as `0.0`.

`[DELIMITER=<TAB|COMMA>]`

Used to specify an alternate delimiter in the STD or NOINDEX format output.

`<output variable>`

Following the analysis type and other options is a list of output variables. There is no upper bound on the number of output variables. The output is divided up into data columns and output according to any specified options (see options given above). Output variables can be specified in four ways:

- `V(<circuit node>)` to output the voltage at a point in the circuit
- `I(<device>)` to output current through a two terminal device.
- `I<lead abbreviation>(<device>)` to output current into a particular lead of a three or more terminal device.
- `{expression}` to output an expression involving `V` and `I` values.

Further explanation of current specification is in comments section below.

Comments

Currents are positive flowing from node 1 to node 2 for two node devices, and currents are positive flowing into a particular lead for leads. `<circuit node>` is simply the name of any node in your top-level circuit, or `<subcircuit name>:<node>` to reference nodes that are internal to a subcircuit. `<device>` is the name of any device in your top-level circuit, or `<subcircuit name>:<device>` to reference devices that are internal to a subcircuit. `<lead abbreviation>` is a single character designator for individual leads on a device with three or more leads. For bipolar transistors these are: c (collector), b (base), e (emitter), s (substrate). For mosfets, lead abbreviations are: d (drain), g (gate), s (source), and b (bulk). SOI transistors have: d, g, s, e (bulk), and b (body). For PDE devices, the nodes are numbered according to the order they appear, so lead currents are referenced like i1(`<device>`), i2(`<device>`), etc.

The values of the output variables are output as a series of columns (one for each output variable). Note that while the `.PRINT` line supports expressions, `.PRINT` line expressions do not recognize `.PARAM` specified parameters. For example, this `.PRINT` line:

```
.PARAM tmpval=0.33
R1  0  1  tmpval
.PRINT TRAN V(1) {tmpval*V(1)}
```

will fail with an error saying that tmpval is not recognized in the `.PRINT` expression.

Netlist Processing

.END (End of Circuit)

End of netlist file.

.FUNC (function)

User defined functions that can be used in expressions appearing later in the same scope as the .FUNC statement.

General Form	`.FUNC <name>([arg]*) <body>`

Examples	`.FUNC E(x) {exp(x)}`
	`.FUNC DECAY(CNST) {E(-CNST*TIME)}`
	`.FUNC TRIWAV(x) {ACOS(COS(x))/3.14159}`
	`.FUNC MIN3(A,B,C) {MIN(A,MIN(B,C))}`

Arguments and Options	`.FUNC`
	Must precede the first use of the function name. Functions cannot be redefined and the function name must not be the same as any of the predefined functions (e.g., SIN and SQRT). .FUNC arguments cannot be node names.
	`<body>`
	May refer to other (previously defined) functions; the second example, DECAY, uses the first example, E.
	`[arg]`
	The number of arguments in the use of a function must agree with the number in the definition. Parameters, TIME, and other functions are allowed in the body of function definitions.

Comments	The `<body>` of a defined function is handled in the same way as any math expression; it must be enclosed in curly braces .

.INC or .INCLUDE (include file)

Include specified file in netlist.

The file name can be surrounded by double quotes, ”filename”, but this is not necessary. The directory for the include file is assumed to be the execution directory unless a full or

relative path is given as a part of the file name.

.PARAM (parameter)

User defined parameter that can be used in expressions throughout the netlist.

General Form	`.PARAM [<name>=<value>]*`
Examples	`.PARAM A_Param=1K` `.PARAM B_Param={A_Param*3.1415926535}`
Comments	Parameters defined using `.PARAM` are evaluated hen the netlist is read in, and therefore must evaluate to constants at the time the netlist is parsed. It is therefore illegal to use any time- or solution-dependent terms in parameter definitions, including the TIME variable or any nodal voltages. Since they must be constants, these parameters may also not be used in .STEP loops.

.GLOBAL_PARAM (global parameter)

User defined global parameter that can be time dependent, or that can be used in .STEP loops.

General Form	`.GLOBAL_PARAM [<name>=<value>]*`
Examples	`.GLOBAL_PARAM T={27+100*time}`
Comments	You may use parameters defined by .PARAM in expressions used to define global parameters, but you may *not* use global parameters in .PARAM definitions. Unlike .PARAM parameters, global parameters are evaluated at the time they are needed and may therefore be time dependent and may depend on other time dependent quantities in the circuit. Global parameters are accessible and have the same value throughout all levels of the netlist hierarchy. It is not legal to redefine global parameters in different levels of the netlist hierarchy.

Miscellaneous Commands

* (Comment)

Create a netlist comment line.

; (In-line Comment)

Add a netlist in-line comment

+ (Line Continuation)

Continue the text of the previous line

.OPTIONS Statements

.OPTIONS (Analysis Options)

Set various simulation limits, analysis control parameters and output characters. In general, they use the following format:

```
.OPTIONS <PKG> [<TAG>=<VALUE>]*
```

Exceptions to this format include the OUTPUT and RESTART options that use their own format, which will be defined under their respective descriptions.

The designator PKG refers to the Unified Modeling Language (UML) *package* which refers loosely to a *module* in the code. Thus, the term is used here as identifying a specific *module* to be controlled via *options* set in the netlist input file. The packages which currently support .OPTIONS, and the keywords to use in place of <PKG> are:

Package	PKG keyword
Global:	GLOBAL
Device Model:	DEVICE
Time Integration:	TIMEINT
Nonlinear Solver:	NONLIN
Transient Nonlinear Solver:	NONLIN-TRAN
Continuation/Bifurcation Tracking:	LOCA
Linear Solver:	LINSOL
Output:	OUTPUT
Restart:	RESTART

As an example, the following netlist line will set the value of **ABSTOL** in the time integration package to 1×10^{-8}:

Example: `.OPTIONS TIMEINT ABSTOL=1E-8`

Below is an outline of the supported packages and their respective options:

Device Package Options

The device package parameters listed in Table 2.1 outline the options available for specifying device specific parameters. Some of these (`DEFAS`, `DEFAD`, `TNOM` etc.) have the same meaning as they do for the `.OPTION` line from Berkeley SPICE (3f5). Parameters which apply globally to all device models will be specified here. Parameters specific to a particular device instance or model are specified in section 2.2.

Device Model (PKG = DEVICE) Tag	Description	Default
DEFAS	MOS Drain Diffusion Area	0.0
DEFAD	MOS Source Diffusion Area	0.0
DEFL	MOS Default Channel Length	1.0E-4
DEFW	MOS Default Channel Width	1.0E-4
GMIN	Minimum Conductance	1.0E-12
GMAX	Maximum Conductance	1.0E+20
MINRES	Lead resistance for semiconductor device leads specified as zero	0.0
MINCAP	Capacitance to use for semiconductor junction capacitance specified as zero	0.0
TEMP	Temperature	27.0 °C (300.15K)
TNOM	Nominal Temperature	27.0 °C (300.15K)
SCALESRC	Scaling factor for source scaling	0.0
NUMJAC	Numerical Jacobian flag (only use for small problems)	0 (FALSE)
VOLTLIM	Voltage limiting	1 (TRUE)

Device Model (PKG = DEVICE) Tag	Description	Default
icFac	This is a multiplicative factor which is applied to right-hand side vector loads of .IC initial conditions during the DCOP phase.	10000.0
LAMBERTW	This flag determines if the Lambert-W function should be applied in place of exponentials in hard-to-solve devices. Currently, this capability is implemented in the diode and BJT. Try this for BJT circuits that have convergence problems. For best effect, this option should be tried with voltlim turned off. A detailed explanation of the Lambert-W function, and its application to device modeling can be found in reference [3].	0 (FALSE)
MAXTIMESTEP	Maximum time step size	1.0E+99
MOSFET Homtopy parameters		
VDSSCALEMIN	Scaling factor for Vds	0.3
VGSTCONST	Initial value for Vgst	4.5 Volt
LENGTH0	Initial value for length	5.0e-6
WIDTH0	Initial value for width	200.0e-6
TOX0	Initial value for oxide thickness	6.0e-8
Debug output parameters		
DEBUGLEVEL	The higher this number, the more info is output	1
DEBUGMINTIMESTEP	First time-step debug information is output	0
DEBUGMAXTIMESTEP	Last time-step of debug output	65536

Device Model (PKG = DEVICE) Tag	Description	Default
DEBUGMINTIME	Same as DEBUGMINTIMESTEP except controlled by time (sec.) instead of step number	0.0
DEBUGMAXTIME	Same as DEBUGMAXTIMESTEP except controlled by time (sec.) instead of step number	100.0

Table 2.1: Options for Device Package

Time Integration Options

The time integration parameters listed in Table 2.2 give the available options for helping control the time integration algorithms for transient analysis.

Time Integration (PKG = TIMEINT) Tag	Description	Default
METHOD	Time integration method. This parameter is only relevant when running **Xyce** in transient mode. Supported methods: ■ 1 (BDF 1) ■ 2 (BDF 2) ■ 3 (Trapezoid)	1 (BDF 1)
CONSTSTEP	Constant time step flag. If set to true, the code will use a constant time step in transient mode.	0 (FALSE)
RELTOL	Relative error tolerance	1.0E-02
ABSTOL	Absolute error tolerance	1.0E-06
RESTARTSTEPSCALE	This parameter is a scalar which determines how small the initial time step out of a breakpoint should be. In the current version of the time integrator, the first step after a breakpoint isn't subjected to much error analysis, so for very stiff circuits, this step can be problematic.	0.005

Time Integration (PKG = TIMEINT) Tag	Description	Default
NLNEARCONV	This flag sets if “soft” failures of the nonlinear solver, when the convergence criteria are almost, but not quite, met, should result in a ”success” code being returned from the nonlinear solver to the time integrator. If this is enabled, it is expected that the error analysis performed by the time integrator will be the sole determination of whether or not the time step is considered a “pass” or a “fail”. This is on by default, but occasionally circuits need tighter convergence criteria.	1 (TRUE)
NLSMALLUPDATE	This flag is another “soft” nonlinear solver failure flag. In this case, if the flag is set, time steps in which the nonlinear solver stalls, and is using updates that are numerically tiny, can be considered to have converged by the nonlinear solver. If this flag is set, the time integrator is responsible for determining if a step should be accepted or not.	1 (TRUE)
RESETTRANNLS	The nonlinear solver resets its settings for the transient part of the run to something more efficient (basically a simpler set of options with smaller numbers for things like max Newton step). If this is set to false, this resetting is turned off. Normally should be left as default.	1 (TRUE)
ERROPTION	This parameter determines if predictor-corrector error control is turned on or not. If it is off, then only the nonlinear solver success is used to adjust the time step size. If this is used, NLNEARCONV and NLSMALLUPDATE should both be set to 0.	0 (predictor-corrector is used)

Time Integration (PKG = TIMEINT) Tag	Description	Default
DOUBLEDCOPSTEP	This option should only be set to TRUE for a PDE device run. PDE devices often have to solve an extra "setup" problem to get the initial condition. This extra setup problem solves a nonlinear Poisson equation (see the device appendix for more details), while the normal step solves a full drift-diffusion(DD) problem. The name of this flag refers to the fact that the code is essentially taking two DC operating point steps instead of one. If you set this to TRUE, but have no PDE devices in the circuit, the code will repeat the same identical DCOP step twice. Generally there is no point in doing this.	• 0 (FALSE), if no PDE devices are present. • 1 (TRUE), if at least one PDE device is in the circuit.
FIRSTDCOPSTEP	This is the index of the first DCOP step taken in a simulation for which DOUBLEDCOPSTEP is set to TRUE. The special initialization (nonlinear Poisson) step is referred to as step 0, while the normal (drift-diffusion) step is indexed with a 1. These two options(FIRSTDCOPSTEP and LASTDCOPSTEP) allow you to set the 1st or second DCOP step to be either kind of step. If FIRSTDCOPSTEP and LASTDCOPSTEP are both set to 0, then only the initial setup step happens. If FIRSTDCOPSTEP and LASTDCOPSTEP are both set to 1, then the initialization step doesn't happen, and only the real DD problem is attempted, with a crude initial guess. You should *never* set FIRSTDCOPSTEP to 1 and SECONDDCOPSTEP to 0. Normally, they should always be left as the defaults.	0
LASTDCOPSTEP	This is the second step taken in a simulation for which DOUBLEDCOPSTEP is set to TRUE.	1

Time Integration (PKG = TIMEINT) Tag	Description	Default
BPENABLE	Flag for turning on/off breakpoints (1 = ON, 0 = OFF). It is unlikely anyone would ever set this to FALSE, except to help debug the breakpoint capability.	1 (TRUE)
EXITTIME	If this is set to nonzero, the code will check the simulation time at the end of each step. If the total time exceeds the exittime, the code will ungracefully exit. This is a debugging option, the point of which is the have the code stop at a certain time during a run without affecting the step size control. If not set by the user, it isn't activated.	-
EXITSTEP	Same as EXITTIME, only applied to step number. The code will exit at the specified step. If not set by the user, it isn't activated.	-

Table 2.2: Options for Time Integration Package.

Multi-Time Partial Differential Equation Options (MPDE)

Xyce has the ability to quickly simulate systems with two separated time scales, *i.e.* a *fast* and *slow* time scale. In this case, **Xyce** computes a set of solutions on the *fast* time scale and then tries to integrate this set of solutions forward in time along the *slow* time scale. Please see the **Xyce** Users' Guide for more information.

Multi-Time Partial Differential Equation Analysis (PKG = MPDE) Tag	Description	Default
N2	Number of time points in the fast time domain	20

Multi-Time Partial Differential Equation Analysis (PKG = MPDE) Tag	Description	Default
AUTON2	Do a one period initial transient run to determine the number and location of the fast time points.	false
AUTON2MAX	The maximum number of fast time points to keep from an initial transient run.	20
OSCSRC	A list of voltage or current sources which change on the fast time scale.	VIN
STARTUPPERIODS	The number of fast time periods to integrate through before calculating the MPDE initial conditions.	0
OSCOUT	Node for periodicity condition for Warped MPDE	
PHASE	Phase specification for Warped MPDE	0
PHASECOEFF	Phase coefficient for Warped MPDE	
T2	The time in seconds of the fast time period. This overrides any automatically determined period from OSCSRC.	0
WAMPDE	Flag specifying that this will be Warped MPDE calculation	false
FREQDOMAIN		
ICPER		
IC	Initial condition calculation method to use. Use 0 for Sawtooth or 1 for a transient run.	0
DIFF	Differentiation scheme to use on the fast time scale. Use 0 for backwards difference and 1 for central differences.	0
DIFFORDER	Differentiation order for fast time scale time derivatives.	1

Table 2.3: Options for MPDE Package.

Nonlinear Solver Options

The nonlinear solver parameters listed in Table 2.4 provide methods for controlling the nonlinear solver for DC, Transient. Note that the nonlinear solver options for DCOP and transient are specified in separate options statements, using `.OPTIONS NONLIN` and `.OPTIONS NONLIN-TRAN`, respectively. The defaults for each are specified in the third and fourth columns of Table 2.4.

Nonlinear Solver (PKG = NONLIN) and (PKG = NONLIN-TRAN) Tags	Description	NONLIN Default	NONLIN-TRAN Default
NLSTRATEGY	Nonlinear solution strategy. Supported Strategies: ■ 0 (Newton) ■ 1 (Gradient) ■ 2 (Trust Region)	0 (Newton)	0 (Newton)
SEARCHMETHOD	Line-search method used by the nonlinear solver. Supported line-search methods: ■ 0 (Full Newton - no line search) ■ 1 (Interval Halving) ■ 2 (Quadratic Interpolation) ■ 3 (Cubic Interpolation) ■ 4 (More'-Thuente)	0 (Full Newton) (NOTE: for iterative linear solves, the default is Quadratic Linesearch - 2)	0 (Full Newton)
ABSTOL	Absolute residual vector tolerance	1.0E-12	1.0E-06
RELTOL	Relative residual vector tolerance	1.0E-03	1.0E-02
DELTAXTOL	Weighted nonlinear-solution update norm convergence tolerance	1.0	0.33
RHSTOL	Residual convergence tolerance (unweighted 2-norm)	1.0E-06	1.0E-02
MAXSTEP	Maximum number of Newton steps	200	20

Nonlinear Solver (PKG = NONLIN) and (PKG = NONLIN-TRAN) Tags	Description	NONLIN Default	NONLIN-TRAN Default
MAXSEARCHSTEP	Maximum number of line-search steps	9	2
NORMLVL	Norm level used by the nonlinear solver algorithms *(NOTE: not used for convergence tests)*	2	2
LINOPT	Linear optimization flag	0 (FALSE)	0 (FALSE)
CONSTRAINTBT	Constraint backtracking flag	0 (FALSE)	0 (FALSE)
CONSTRAINTMAX	Global maximum setting for constraint backtracking	DBL_MAX (Machine Dependent Constant)	DBL_MAX
CONSTRAINTMIN	Global minimum setting for constraint backtracking	-DBL_MAX (Machine Dependent Constant)	-DBL_MAX
CONSTRAINTCHANGE	Global percentage-change setting for constraint backtracking	sqrt(DBL_MAX) (Machine Dependent Constant)	sqrt(DBL_MAX)
IN_FORCING	Inexact Newton-Krylov forcing flag	1 (TRUE)	1 (TRUE)
AZ_TOL	Sets the minimum allowed linear solver tolerance. Valid only if IN_FORCING=1.	1.0E-12	1.0E-12
RECOVERYSTEPTYPE	If using a line search, this option determines the type of step to take if the line search fails. Supported strategies: ■ 0 (Take the last computed step size in the line search algorithm) ■ 1 (Take a constant step size set by RECOVERYSTEP)	0	0
RECOVERYSTEP	Value of the recovery step if a constant step length is selected	1.0	1.0

Nonlinear Solver (PKG = NONLIN) and (PKG = NONLIN-TRAN) Tags	Description	NONLIN Default	NONLIN-TRAN Default
CONTINUATION	Enables the use of Homotopy/Continuation algorithms for the nonlinear solve. Options are: ■ 0 (Standard nonlinear solve) ■ 1 (Natural parameter homotopy. See LOCA options list) ■ 2 (Specialized dual parameter homotopy for MOSFET circuits)	0 (Standard nonlinear solve)	0 (Standard nonlinear solve)
DLSDEBUG	Debug output for direct linear solver	0 (FALSE)	0 (FALSE)
DEBUGLEVEL	The higher this number, the more info is output	1	1
DEBUGMINTIMESTEP	First time-step debug information is output	0	0
DEBUGMAXTIMESTEP	Last time-step of debug output	99999999	99999999

Nonlinear Solver (PKG = NONLIN) and (PKG = NONLIN-TRAN) Tags	Description	NONLIN Default	NONLIN-TRAN Default
DEBUGMINTIME	Same as DEBUGMINTIMESTEP except controlled by time (sec.) instead of step number	0.0	0.0
DEBUGMAXTIME	Same as DEBUGMAXTIMESTEP except controlled by time (sec.) instead of step number	1.0E+99	1.0E+99

Table 2.4: Options for Nonlinear Solver Package.

Continuation and Bifurcation Tracking Package Options

The continuation selections listed in Table 2.5 provide methods for controlling continuation and bifurcation analysis. These override the defaults and any that were set simply in the continuation package. This option block is only used if the nonlinear solver or transient nonlinear solver enable continuation through the CONTINUATION flag.

Continuation and Bifurcation (PKG = LOCA) Tag	Description	Default
STEPPER	Stepping algorithm to use: ■ 0 (Natural or Zero order continuation) ■ 1 (Arc-length continuation)	0 (Natural)
PREDICTOR	Predictor algorithm to use: ■ 0 (Tangent) ■ 1 (Secant) ■ 2 (Random) ■ 3 (Constant)	0 (Tangent)

Continuation and Bifurcation (PKG = LOCA) Tag	Description	Default
STEPCONTROL	Algorithm used to adjust the step size between continuation steps: ■ 0 (Constant) ■ 1 (Adaptive)	0 (Constant)
CONPARAM	Parameter in which to step during a continuation run	VA:V0
INITIALVALUE	Starting value of the continuation parameter	0.0
MINVALUE	Minimum value of the continuation parameter	-1.0E20
MAXVALUE	Maximum value of the continuation parameter	1.0E20
BIFPARAM	Parameter to compute during bifurcation tracking runs	VA:V0
MAXSTEPS	Maximum number of continuation steps (includes failed steps)	20
MAXNLITERS	Maximum number of nonlinear iterations allowed (set this parameter equal to the MAXSTEP parameter in the NONLIN option block	20
INITIALSTEPSIZE	Starting value of the step size	1.0
MINSTEPSIZE	Minimum value of the step size	1.0E20
MAXSTEPSIZE	Maximum value of the step size	1.0E-4
AGGRESSIVENESS	Value between 0.0 and 1.0 that determines how aggressive the step size control algorithm should be when increasing the step size. 0.0 is a constant step size while 1.0 is the most aggressive.	0.0

Table 2.5: Options for Continuation and Bifurcation Tracking Package.

Linear Solver Options

Xyce uses both a sparse-direct solver as well as Krylov iterative methods for the solution of the linear equations generated by Newton's method. For the advanced users, there are a variety of options that can be set to help improve these solvers. Many of these options (for the Krylov solvers) are simply passed through to the underlying Trilinos/Aztec solution settings and thus have an "AZ_" prefix on the flag; the "AZ_" options are all case-sensitive. The list in Table 2.6 only provides a partial list of the more commonly used Trilinos/Aztec

options. For a full list of the available options, please see the Aztec User's Guide [4] available for download at `http://www.cs.sandia.gov/CRF/Aztec1`. However, for most users, the default options should prove adequate.

Linear Solver (PKG = LINSOL) Tag	Description	Default
`AZ_max_iter`	Maximum number of iterative solver iterations	500
`AZ_precond`	Iterative solver preconditioner flag	`AZ_dom_decomp (14)`
`AZ_solver`	Iterative solver type	`AZ_gmres (1)`
`AZ_conv`	Convergence type	`AZ_r0 (0)`
`AZ_pre_calc`	Type of precalculation	`AZ_recalc (1)`
`AZ_keep_info`	Retain calculation info	`AZ_true (1)`
`AZ_orthog`	Type of orthogonalization	`AZ_modified (1)`
`AZ_subdomain_solve`	Subdomain solution for domain decomposition preconditioners	`AZ_ilut (9)`
`AZ_ilut_fill`	Approximate allowed fill-in factor for the ILUT preconditioner	3.0
`AZ_drop`	Specifies drop tolerance used in conjunction with LU or ILUT preconditioners	1.0E-03
`AZ_reorder`	Reordering type	`AZ_none (0)`
`AZ_scaling`	Type of scaling	`AZ_none (0)`
`AZ_kspace`	Maximum size of gmres kspace	500
`AZ_tol`	Convergence tolerance	1.0E-12
`AZ_output`	Output level	50
`AZ_overlap`	Schwarz overlap level for ILU preconditioners	0
`AZ_rthresh`	Diagonal shifting relative threshold for ILU preconditioners	1.0001
`AZ_athresh`	Diagonal shifting absolute threshold for ILU preconditioners	1.0E-04
`TR_partition`	Perform load-balance partitioning on the linear system	1 (TRUE)

Linear Solver (PKG = LINSOL) Tag	Description	Default
TR_filter	Providing a non-zero value for THRESHOLD triggers filtering of the Jacobian entries by ROW_SUM * THRESHOLD	0.0
TR_singleton_filter	Triggers use of singleton filter for linear system	0 (FALSE)
TR_reindex	Reindexes linear system parallel global indices in lexigraphical order, recommended with singleton filter	1 (TRUE)
TR_solvermap	Triggers remapping of column indices for parallel runs, recommended with singleton filter	1 (TRUE)
adaptive_solve	Triggers use of AztecOO adaptive solve algorithm for preconditioning of iterative linear solves	0 (FALSE)
use_ifpack_precond	Triggers use of IfPack for preconditioning of iterative linear solves	1 (TRUE)
type	Determines which linear solver will be used. ■ KSPARSE (Serial Only) ■ SUPERLU ■ KLU ■ AZTECOO Note that while SuperLU and KLU are available for parallel execution they will solve the linear system in serial. Therefore they will be useful for moderate problem sizes but will not scale in memory or performance for large problems	KLU (Serial) AZTECOO (Parallel)

Table 2.6: Options for Linear Solver Package.

Output Options

The main purpose of the .OPTIONS OUTPUT command is to allow control of the output frequency of data to files specified by .PRINT TRAN commands. The format is:

```
.OPTIONS OUTPUT INITIAL_INTERVAL=<interval> [<t0> <i0> [<t1> <i1>...]]
```

where INITIAL_INTERVAL=<interval> specifies the starting interval time for output and <tx> <ix> specifies later simulation times <tx> where the output interval will change to <ix>.

Note: Xyce will output data at the next time that is greater-than or equal to the current interval time. This means that output will not exactly correspond to the time intervals due to the adaptive time stepping algorithms.

Checkpointing and Restarting Options

The .OPTIONS RESTART command is used to control all checkpoint output and restarting.

- Checkpointing command format:

```
.OPTIONS RESTART [PACK=<0|1>] JOB=<job prefix>
+ [INITIAL_INTERVAL=<initial interval time>
+  [<t0> <i0> [<t1> <i1>...]]]
```

PACK=<0|1> indicates whether the restart data will be byte packed or not. Parallel restarts must always be packed while currently Windows/MingW runs are always not packed. Otherwise, by default data will be packed unless explicitly specified. JOB=<job prefix> identifies the prefix for restart files. The actual restart files will be the job name with the current simulation time appended (e.g. name1e-05 for JOB=name and simulation time 1e-05 seconds). Furthermore, INITIAL_INTERVAL=<initial interval time> identifies the initial interval time used for restart output. The <tx> <ix> intervals identify times <tx> at which the output interval (ix) should change. This functionality is identical to that described for the .OPTIONS OUTPUT command.

To generate checkpoints at every time step (default):

Example: .OPTIONS RESTART JOB=checkpt

To generate checkpoints every 0.1 μs:

Example: .OPTIONS RESTART JOB=checkpt INITIAL_INTERVAL=0.1us

To generate unpacked checkpoints every 0.1 μs:

Example: `.OPTIONS RESTART PACK=0 JOB=checkpt INITIAL_INTERVAL=0.1us`

To specify an initial interval of 0.1 μs, at 1 μs change to interval of 0.5 μs, and at 10 μs change to interval of 0.1 μs:

Example:

```
.OPTIONS RESTART JOB=checkpt INITIAL_INTERVAL=0.1us 1.0us
+ 0.5us 10us 0.1us
```

To restart from an existing restart file, specify the file by either `FILE=<restart file name>` to explicitly use a restart file or by `JOB=<job name> START_TIME=<specified name>` to specify a file prefix and a specified time. The time must exactly match an output file time for the simulator to correctly identify the correct file. To continue generating restart output files, `INITIAL_INTERVAL=<interval>` and following intervals can be appended to the command in the same format as described above. New restart files will be packed according to the previous restart file read in. Here are several examples:

- Restarting command format:

```
.OPTIONS RESTART <FILE=<restart file name> |
+ JOB=<job name> START_TIME=<time>)>
+ [ INITIAL_INTERVAL=<interval> [<t0> <i0> [<t1> <i1> ...]]]
```

Example restarting from checkpoint file at 0.133 μs:

Example: `.OPTIONS RESTART JOB=checkpt START_TIME=0.133us`

To restart from checkpoint file at 0.133 μs:

Example: `.OPTIONS RESTART FILE=checkpt0.000000133`

Restarting from 0.133 μs and continue checkpointing at 0.1 μs intervals:

Example:

```
 .OPTIONS RESTART FILE=checkpt0.000000133 JOB=checkpt_again
+ INITIAL_INTERVAL=0.1us
```

Restart with two-level

Large parallel problems which involve power supply parasitics often require a two-level solve, in which different parts of the problem are handled separately. In most respects,

restarting a two-level simulation is similar to restarting a conventional simulation. However, there are a few differences:

- When running with a two-level algorithm, **Xyce** requires (at least) two different input files. In order to do a restart of a two-level **Xyce** simulation, it is neccessary to have an `.OPTIONS RESTART` statement in each file.
- It is neccessary for the statements to be consistent. For example, the output times must be exactly the same, meaning the initial intervals must be exactly the same.
- Currently, **Xyce** will *not* check to make sure that the restart options used in different files match, so it is up to the user to insure matching options.
- Finally, as each netlist that is part of a two-level solve will have its own `.OPTIONS RESTART` statement, that means that each netlist will generate and/or use its own set of restart files. As a result, the restart file name used by each netlist must be unique.

2.2 Analog Devices

Xyce supports many analog devices, including sources, subcircuits and behavioral models. This section serves as a reference for the analog devices supported by **Xyce**. Each device is described separately and includes the following information, if applicable:

- a description and an example of the correct netlist syntax.
- the matching model types and their description.
- the matching list of model parameters and associated descriptions.
- the corresponding and characteristic equations for the model (as required).
- references to publications on which the model is based.

You can also create models and macromodels using the `.MODEL` (model definition) and `.SUBCKT` (subcircuit) statements, respectively.

Please note that the characteristic equations are provided to give a general representation of the device behavior. The actual **Xyce** implementation of the device may be slightly different in order to improve, for example, the robustness of the device.

Table 2.7 gives a summary of the analog device types and the form of their netlist formats. Each of these is described below in detail.

Device Type	Designator Letter	Typical Netlist Format
Nonlinear Dependent Source (B Source)	B	B<name> <+ node> <- node> + <I or V>={<expression>}
Capacitor	C	C<name> <+ node> <- node> [model name] <value> + [IC=<initial value>]
Diode	D	D<name> <anode node> <cathode node> + <model name> [area value]
Voltage Controlled Voltage Source	E	E<name> <+ node> <- node> <+ controlling node> + <- controlling node> <gain>
Current Controlled Current Source	F	F<name> <+ node> <- node> + <controlling V device name> <gain>
Voltage Controlled Current Source	G	G<name> <+ node> <- node> <+ controlling node> + <- controlling node> <transconductance>
Current Controlled Voltage Source	H	H<name> <+ node> <- node> + <controlling V device name> <gain>
Independent Current Source	I	I<name> <+ node> <- node> [[DC] <value>] + [transient specification]
Mutual Inductor	K	K<name> <inductor 1> [<ind. n>*] + <linear coupling or model>
Inductor	L	L<name> <+ node> <- node> [model name] <value> + [IC=<initial value>]
JFET	J	J<name> <drain node> <gate node> <source node> + <model name> [area value]
MOSFET	M	M<name> <drain node> <gate node> <source node> + <bulk/substrate node> [SOI node(s)] + <model name> [common model parameter]*
Bipolar Junction Transistor (BJT)	Q	Q<name> <collector node> <base node> + <emitter node> [substrate node] [SOI node(s)] + <model name> [area value]
Resistor	R	R<name> <+ node> <- node> [model name] <value> + [L=<length>] [W=<width>]
Voltage Controlled Switch	S	S<name> <+ switch node> <- switch node> + <+ controlling node> <- controlling node> + <model name>
Transmission Line	T	T<name> <A port + node> <A port - node> + <B port + node> <B port - node> + <ideal specification>
Independent Voltage Source	V	V<name> <+ node> <- node> [[DC] <value>] + [transient specification]
Subcircuit	X	X<name> [node]* <subcircuit name> + [PARAMS:[<name>=<value>]*]

Device Type	Designator Letter	Typical Netlist Format
Current Controlled Switch	W	W<name> <+ switch node> <- switch node> + <controlling V device name> <model name>
Digital Devices	Y<name>	Y<name> [node]* <model name>
PDE Devices	YPDE	YPDE <name> [node]* <model name>
MESFET	Z	Z<name> <drain node> <gate node> <source node> + <model name> [area value]

Table 2.7: Analog Device Quick Reference.

Voltage Nodes

Devices in a netlist are connected between *nodes*, and all device types in **Xyce** require at least two nodes on each instance line. Node names can consist of any printable characters *except* white space (space, tab, newline), parentheses ("(" or ")"), braces ("{" or "}"), commas, or the equal sign.

Except for global nodes (below), voltage node names appearing in a subcircuit that are not listed in the subcircuit's argument list are accessible only to that subcircuit; devices outside the subcircuit cannot connect to local nodes.

Global nodes

A special syntax is used to designate certain nodes as *global* nodes. Any node whose name starts with the two characters "$G" is a global node, and such nodes are available to be used in any subcircuit. A typical usage of such global nodes is to define a VDD or VSS signal that all subcircuits need to be able to access, but without having to provide `V`SS and `V`DD input nodes to every subcircuit. In this case, a global `$`GVDD node would be use for the VDD signal.

The node named `0` is a special global node. Node `0` is always ground, and is accessible to all levels of a hierarchical netlist.

Capacitor

General Form

```
C<name> <(+) node> <(-) node> [model name] [value] [device parameters]
```

Examples

```
CM12 2 4 5.288e-13
CLOAD 1 0 4.540pF IC=1.5V
CFEEDBACK 2 0 CMOD 1.0pF
CAGED 2 3 4.0uF D=0.0233 AGE=86200
```

Symbol

Model Form

```
.MODEL <model name> C [model parameters]
```

Parameters and Options

`(+)` and `(-)` nodes

Polarity definition for a positive voltage across the capacitor. The first node is defined as positive. Therefore, the voltage across the component is the first node voltage minus the second node voltage.

`[model name]`

If [model name] is omitted, then `<value>` is the capacitance in farads. If [model name] is given then the value is determined from the model parameters; see the capacitor value formula below.

`[value]`

Positional specification of device parameter C (capacitance). Alternately, this can be specified as a parameter, `C=<value>`, or in the (optional) model.

`[device parameters]`

Parameters listed in Table 2.8 may be provided as space separated `<parameter>=<value>` specifications as needed. Any number of parameters may be specified.

Comments	Positive current flows through the capacitor from the `(+)` node to the `(-)` node. In general, capacitors should have a positive capacitance value (`<value>` property). In all cases, the capacitance must not be zero. However, cases exist when a negative capacitance value may be used. This occurs most often in filter designs that analyze an RLC circuit equivalent to a real circuit. When transforming from the real to the RLC equivalent, the result may contain a negative capacitance value. In a transient run, negative capacitance values may cause the simulation to fail due to instabilities they cause in the time integration algorithms.

Device Parameters

Table 2.8 gives the available device parameters for the capacitor.

Parameter	Description	Units	Default
AGE	Age of capacitor	hour	0
C	Capacitance	F	1
D	Age degradation coefficient	–	0.0233
IC	Initial voltage drop across device	V	0
L	Semiconductor capacitor width	m	1
TEMP	Device temperature	°C	27
W	Semiconductor capacitor length	m	1e-06

Table 2.8: Capacitor Device Parameters.

Model Parameters

Table 2.9 gives the available model parameters for the capacitor.

Parameter	Description	Units	Default
CJ	Junction bottom capacitance	F/m^2	0
CJSW	Junction sidewall capacitance	F/m	0
DEFW	Default device width	m	1e-06
NARROW	Narrowing due to side etching	m	0
TC1	Linear temperature coefficient	$°C^{-1}$	0
TC2	Quadratic temperature coefficient	$°C^{-2}$	0
TNOM	Nominal device temperature	°C	27

Parameter	Description	Units	Default

Table 2.9: Capacitor Model Parameters.

Capacitor Equations

Capacitance Value Formula

If `[model name]` is specified, then the capacitance is given by:

$$\mathbf{C} \cdot (1 + \mathbf{TC1} \cdot (T - T_0) + \mathbf{TC2} \cdot (T - T_0)^2)$$

where `C` is the base capacitance specified on the device line and is normally positive (though it can be negative, but not zero). T_0 is the nominal temperature (set using $\mathbf{TNOM}$ option).

Age-aware Formula

If $\mathbf{AGE}$ is given, then the capacitance is:

$$\mathbf{C}[1 - \mathbf{D}\log(\mathbf{AGE})]$$

Semiconductor Formula

If `[model name]` and $\mathbf{L}$ and $\mathbf{W}$ are given, then the capacitance is:

$$\mathbf{CJ}(\mathbf{L} - \mathbf{NARROW})(\mathbf{W} - \mathbf{NARROW}) + 2 \cdot \mathbf{CJSW}(\mathbf{L} - \mathbf{W} + 2 \cdot \mathbf{NARROW})$$

Inductor

General Form	`L<name> <(+) node> <(-) node> <value>` `+ [IC=<initial value>]`
Examples	`L1 1 5 3.718e-08` `LLOAD 3 6 4.540mH IC=2mA`
Symbol	
Model Form	`.MODEL <model name> I [model parameters]`
Parameters and Options	`(+)` and `(-)` nodes Polarity definition for a positive voltage across the inductor. The first node is defined as positive. Therefore, the voltage across the component is the first node voltage minus the second node voltage. `<initial value>` The initial current through the inductor during the bias point calculation.
Comments	In general, inductors should have a positive inductance value (`VALUE` property). In all cases, the inductance must not zero. However, cases exist when a negative value may be used. This occurs most often in filter designs that analyze an RLC circuit equivalent to a real circuit. When transforming from the real to the RLC equivalent, the result may contain a negative inductance value. When an inductor is named in the list of coupled inductors in a mutual inductor device line (see page 59) , and that mutual inductor is of the nonlinear-core type, the `<value>` is interpreted as a number of turns rather than as an inductance in Henries.

Model Parameters

Table 2.10 gives the available model parameters for the inductor.

Model parameters	Description	Units	Default
`L`	Inductance Multiplier		1.0
`TC1`	Linear Temperature Coefficient	$^\circ\mathrm{C}^{-1}$	0.0
`TC2`	Quadratic Temperature Coefficient	$^\circ\mathrm{C}^{-2}$	0.0
`TNOM`	Parameter Measurement Temperature	$^\circ\mathrm{C}$	27.0

Table 2.10: Inductor Model Parameters.

Inductor Equations

Inductance Value Formula

If `[model name]` is specified, then the inductance is given by:

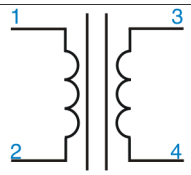
$$\mathbf{L} \cdot (1 + \mathbf{TC1} \cdot (T - T_0) + \mathbf{TC2} \cdot (T - T_0)^2)$$

where `L` is the base inductance specified on the device line and is normally positive (though it can be negative, but not zero). T_0 is the nominal temperature (set using $\mathbf{TNOM}$ option).

Mutual Inductors

General Form	`K<name> L<inductor name> [L<inductor name>*] <coupling value>` `+ [model name]`

Examples	`KTUNED L3OUT  L4IN .8`
	`KTRNSFRM LPRIMARY LSECNDRY 1`
	`KXFRM L1 L2  L3  L4 .98 KPOT_3C8`

Symbol	
Model Form	`.MODEL <model name> CORE [model parameters]`

Parameters and Options

`L<inductor name> [L<inductor name>*]`

Identifies the inductors to be coupled. The inductors are coupled and in the dot notation the dot is placed on the first node of each inductor. The polarity is determined by the order of the nodes in the L devices and not by the order of the inductors in the K statement.

`<coupling value>`

The coefficient of mutual coupling, which must be between -1.0 and 1.0.

This coefficient is defined by the equation

`<coupling value>` = $\frac{M_{ij}}{L_i L_j}$

where

L_i is the inductance of the ith named inductor in the K-line

M_{ij} is the mutual inductance between L_i and L_j

For transformers of normal geometry, use 1.0 as the value. Values less than 1.0 occur in air core transformers when the coils do not completely overlap.

`<model name>`

If `<model name>` is present, four things change:

- The mutual coupling inductor becomes a nonlinear, magnetic core device.
- The inductors become windings, so the number specifying inductance now specifies the number of turns.
- The list of coupled inductors could be just one inductor.
- A model statement is required to specify the model parameters.

Model Parameters

Table 2.11 gives the available model parameters for mutual inductors.

Model parameters	Description	Units	Default
AREA	mean magnetic cross-sectional area	cm^2	0.01
GAP	effective air gap length	cm	0.0
PATH	total mean magnetic path length	cm	1.0
MS	saturation magnetization	$\mathrm{amp/m}$	1.0e6

Model parameters	Description	Units	Default
A	thermal energy parameter	amp/m	1000.0
C	domain flexing constant		0.2
ALPHA	domain coupling parameter		5.0e-5
KIRR	irreversible magnetization	amp/m	500.0
DELV	modeling parameter	V	0.001
BETAH	modeling parameter		0.00001
BETAM	modeling parameter		3.124e-5
K	alternative specification of KIRR for compatibility with PSpice	$\frac{A}{m}$	500.0
PACK	PSpice compatibility parameter, ignored by **Xyce**		
LEVEL	PSpice compatibility parameter, ignored by **Xyce**		

Table 2.11: Inductor Model Parameters.

Resistor

General Form

```
R<name> <(+) node> <(-) node> [model name] [value] [device parameters]
```

Examples

```
R1 1 2 2K TEMP=27
RLOAD 3 6 RTCMOD 4.540 TEMP=85
.MODEL RTCMOD R (TC1=.01 TC2=-.001)
RSEMICOND 2 0 RMOD L=1000u W=1u
.MODEL RMOD R (RSH=1)
```

Symbol

Model Form

```
.MODEL <model name> R [model parameters]
```

Parameters and Options

`(+)` and `(-)` nodes

Polarity definition for a positive voltage across the resistor. The first node is defined as positive. Therefore, the voltage across the component is the first node voltage minus the second node voltage. Positive current flows from the positive node (first node) to the negative node (second node).

`[model name]`

If `[model name]` is omitted, then `[value]` is the resistance in Ohms. If `[model name]` is given then the resistance is determined from the model parameters; see the resistance value formula below.

`[value]`

Positional specification of device parameter R (resistance). Alternately, this can be specified as a parameter, `R=<value>`, or in the (optional) model.

`[device parameters]`

Parameters listed in Table 2.12 may be provided as space separated `<parameter>=<value>` specifications as needed. Any number of parameters may be specified.

Comments

Resistors must have a positive (nonzero) resistance value (R)

Device Parameters

Table 2.12 gives the available device parameters for the resistor.

Parameter	Description	Units	Default
L	Length	m	0
R	Resistance	Ω	1000

Parameter	Description	Units	Default
TEMP	Temperature	°C	27
W	Width	m	1e-05

Table 2.12: Resistor Device Parameters.

Model Parameters

Table 2.13 gives the available model parameters for the resistor.

Parameter	Description	Units	Default
DEFW	Default Instance Width	m	1e-05
NARROW	Narrowing due to side etching	m	0
RSH	Sheet Resistance	Ω	0
TC1	Linear Temperature Coefficient	$°C^{-1}$	0
TC2	Quadratic Temperature Coefficient	$°C^{-2}$	0
TNOM	Parameter Measurement Temperature	°C	27

Table 2.13: Resistor Model Parameters.

Resistor Equations

Resistance Value Formula

If `[model name]` is included, then the resistance is:

$$\mathbf{R} \cdot (1 + \mathbf{TC1} \cdot (T - T_0) + \mathbf{TC2} \cdot (T - T_0)^2)$$

If $\mathbf{L}$ and $\mathbf{W}$ are given, the resistance is:

$$\mathbf{RSH} \frac{[\mathbf{L} - \mathbf{NARROW}]}{[\mathbf{W} - \mathbf{NARROW}]}$$

Diode

General Form	`D<name> <(+) node> <(-) node> <model name> [area value]`
Examples	`DCLAMP 1 0 DMOD` `D2 15 17 SWITCH 1.5`
Symbol	
Model Form	`.MODEL <model name> D [model parameters]`

Parameters and Options	`<(+) node>`
	The anode.
	`<(-) node>`
	The cathode.
	`[area value]`
	Scales IS, ISR, IKF, RS, CJO, and IBV, and has a default value of 1. IBV and BV are both specified as positive values.

Comments	The diode is modeled as an ohmic resistance (`RS/area`) in series with an intrinsic diode. Positive current is current flowing from the anode through the diode to the cathode.

Diode Operating Temperature

Model parameters can be assigned unique measurement temperatures using the **TNOM** model parameter.

Diode level selection

Four distinct implementations of the diode are available. These are selected by using the `LEVEL` model parameter. The default implementation is based on SPICE 3F5, and may be explicitly specified using `LEVEL=1` in the model parameters, but is also selected if no `LEVEL` parameter is specified. The PSpice implementation [2] is obtained by specifying `LEVEL=2`. The third implementation is based on the AIM-SPICE diode model [5] as modified to include radiation effects [6] [7]. The implementation with radiation effects is selected using the `LEVEL=3` model parameter.

The **Xyce** `LEVEL=1` and `LEVEL=2` diodes have a parameter, **IRF**, that allows the user to adjust the reverse current from the basic SPICE implementation. The usual SPICE treatment defines the linear portion of the reverse current in terms of IS which is defined by the forward current characteristics. Data shows that often the reverse current is quite far off when determined in this manner. The parameter **IRF** is a multiplier that can be applied to

adjust the linear portion of the reverse current.

The level 4 diode is really just a "generic p-n junction photocurrent source" device. It is the level 3 diode with the diode equations removed and the photocurrent terms left in place. It is intended for use in extending other devices with p-n junctions to have nominal photocurrent effects. It recognizes all of the model parameters recognized by the level 3 diode, but those unrelated to photocurrent effects are ignored.

Device Parameters

Table 2.14 gives the available device parameters for the diode.

Parameter	Description	Units	Default
AREA	Area scaling value (scales IS, ISR, IKF, RS, CJ0, and IBV)	–	1
IC	Initial voltage drop across device	V	0
LAMBERTW	unknown	logical (T/F)	0
OFF	Initial voltage drop across device set to zero	logical (T/F)	0
TEMP	Device temperature	°C	27

Table 2.14: Diode Device Parameters.

Model Parameters

Table 2.15 gives the available model parameters for the LEVEL=1 and LEVEL=2 diodes.

Parameter	Description	Units	Default
AF	Flicker noise exponent	–	1
BV	Reverse breakdown "knee" voltage	V	1e+99
CJO	Zero-bias p-n depletion capacitance	F	0
EG	Bandgap voltage (barrier height)	eV	1.11
FC	Forward-bias depletion capacitance coefficient	–	0.5
IBV	Reverse breakdown "knee" current	A	0.001
IBVL	Low-level reverse breakdown "knee" current (level 2)	A	0
IKF	High-injection "knee" current (level 2)	A	0
IRF	Reverse current fitting factor	–	1
IS	Saturation current	A	1e-14
ISR	Recombination current parameter (level 2)	A	0
KF	Flicker noise coefficient	–	0

Parameter	Description	Units	Default
M	Grading parameter for p-n junction	–	0.5
N	Emission coefficient	–	1
NBV	Reverse breakdown ideality factor (level 2)	–	1
NBVL	Low-level reverse breakdown ideality factor (level 2)	–	1
NR	Emission coefficient for ISR (level 2)	–	2
RS	Parasitic resistance	Ω	0
TBV1	BV temperature coefficient (linear) (level 2)	$^\circ$C^{-1}	0
TBV2	BV temperature coefficient (quadratic) (level 2)	$^\circ$C^{-2}	0
TIKF	IKF temperature coefficient (linear) (level 2)	$^\circ$C^{-1}	0
TNOM	Nominal device temperature	$^\circ$C	27
TRS1	RS temperature coefficient (linear) (level 2)	$^\circ$C^{-1}	0
TRS2	RS temperature coefficient (quadratic) (level 2)	$^\circ$C^{-2}	0
TT	Transit time	s	0
VJ	Potential for p-n junction	V	1
XTI	IS temperature exponent	–	3

Table 2.15: Diode Model Parameters.

Table 2.16 gives the available model parameters for the LEVEL=3 and LEVEL=4 diodes.

In all cases, voltage parameters in Table 2.16 related to the "radiation voltage" are relative to the electron-hole generation rate (e.g. if PULSEV2 is 4.3 and GRORDER is 26, the generation rate at the top of the pulse is $4.3 \times 10^{26} m^{-3} s^{-1}$). Conversion between radiation dose in rad$/s$ is dependent on the material type, but in the case of silicon a dose of 1rad$/s$ is $4.3 \times 10^{19} m^{-3} s^{-1}$, so specifying **PULSEV1=0**, **PULSEV2=4.3**, **GRORDER=26** along with **FUNCTIONTYPE=1** is equivalent to a square pulse with peak dose rate of 1×10^7rad$/s$.

The level 3 and level 4 diodes support a **FUNCTIONTYPE=7**, allowing a single parameter **PULSEDATA** to specify the radiation dose profile. If used, **PULSEDATA** can be either an expression in curly braces, or the double-quoted name of a file of time, voltage pairs representing the dose. Units of the expression or file entries are the same as those of **PULSEV1**. The **GRORDER** parameter is still used to determine the exponent of the "radiation voltage" as it is for the other function types.

Model parameters	Description	Units	Default
KF	Flicker Noise Coefficient	-	0.0
AF	Flicker Noise Exponent	-	1.0
BV	Reverse Breakdown Knee Voltage	volt	1E99

Model parameters	Description	Units	Default
CJO	Zero-bias p-n Depletion Capacitance	farad	0.0
EG	Activation Energy	eV	1.11
FC	Forward-bias Depletion Capacitance Coefficient	-	0.5
IBV	Reverse Breakdown Knee Current	amp	1E-3
IS	Saturation Current	amp	1E-14
M	p-n Grading Parameter	-	0.5
N	Emission Coefficient	-	1.0
RS	Parasitic Resistance	ohm	0.0
TT	Transit Time	sec	0.0
TNOM	Parameter Measurement Temperature	°C	27.0
VJ	p-n Potential	volt	1.0
XTI	**IS** Temperature Exponent	-	3.0
IKF	High-injection knee current	amp	0.0
ISR	Recombination current	amp	0.0
NR	Emission coefficient for ISR	-	2.0
ISNPP	Is this an n-p-p+ diode?	boolean	0 (false)
ISPNN	Is this an p-n-n+ diode?	boolean	0 (false)
FUNCTIONTYPE	Selects the shape of the radiation pulse. May take the following values: 0 (none), 1 (pulse wave form), 2 (sinusoidal wave form), 3 (exponential wave form), 4 (piecewise linear wave form), 5 (frequency modulated wave form), 6 (linearly ramped radiation), or 7 (take radiation wave form from data file or expression)	-	0 (none)
GRORDER	Order of magnitude of radiation generation rate	-	25
PERMITTIVITY	Dielectric permittivity of the semiconductor	F/m	1.0443E-10
NA	Doping density in p- region	m^{-3}	5E20
NAHI	Doping density in p+ region	m^{-3}	1E24
ND	Doping density in n- region	m^{-3}	3E25
NDHI	Doping density in n+ region	m^{-3}	3E25
NI	Intrinsic concentration	m^{-3}	1.45E16
WN	Width of the n- region	m	2E-6
WNHI	Width of the n+ region	m	1E-6

Model parameters	Description	Units	Default
WP	Width of the n- region	m	5E-5
WPHI	Width of the n+ region	m	1E-5
PULSEV1	Initial value of radiation pulse (FUNCTIONTYPE=1)	volt	0.0
PULSEV2	Maximum value of radiation pulse (FUNCTIONTYPE=1)	volt	4.3
PULSETD	Delay of radiation pulse (FUNCTIONTYPE=1)	sec	0.0
PULSETR	Rise time of radiation pulse (FUNCTIONTYPE=1)	sec	1E-5
PULSETF	Fall time of radiation pulse (FUNCTIONTYPE=1)	sec	1E-5
PULSEPW	Width of radiation pulse (FUNCTIONTYPE=1)	sec	1E-5
PULSEPER	Period of radiation pulse (FUNCTIONTYPE=1)	sec	1E10
SINVO	Initial value of sinusoidal radiation voltage (FUNCTIONTYPE=2)	volt	0.0
SINVA	Amplitude of sinusoidal radiation voltage (FUNCTIONTYPE=2)	volt	0.0
SINFREQ	Frequency of sinusoidal radiation voltage (FUNCTIONTYPE=2)	Hz	1.0
SINTD	Delay of sinusoidal radiation voltage (FUNCTIONTYPE=2)	sec	0.0
SINTHETA	Inverse of time constant for exponential envelope of sinusoidal radiation voltage (FUNCTIONTYPE=2)	sec^{-1}	0.0
EXPV1	Initial value of exponential cusp radiation voltage (FUNCTIONTYPE=3)	volt	0.0
EXPV2	Height of exponential cusp radiation voltage (FUNCTIONTYPE=3)	volt	0.0
EXPTD1	Rise delay time of exponential cusp radiation voltage (FUNCTIONTYPE=3)	sec	0.0
EXPTAU1	Rise time constant of exponential cusp radiation voltage (FUNCTIONTYPE=3)	sec	1e-2
EXPTD2	Fall delay time of exponential cusp radiation voltage (FUNCTIONTYPE=3)	sec	1E10
EXPTAU2	Fall time constant of exponential cusp radiation voltage (FUNCTIONTYPE=3)	sec	1E10

Model parameters	Description	Units	Default
SFFMVO	Offset of single frequency FM curve (FUNCTIONTYPE=4)	volt	0.0
SFFMVA	Amplitude of single frequency FM curve (FUNCTIONTYPE=4)	volt	0.0
SFFMFC	Carrier frequency of single frequency FM curve (FUNCTIONTYPE=4)	Hz	1.0
SFFMMDI	Modulation index of single frequency FM curve (FUNCTIONTYPE=4)	-	0.0
SFFMFS	Signal frequency of single frequency FM curve (FUNCTIONTYPE=4)	Hz	0.0
PWLT1	Time of point 1 of piecewise linear curve (FUNCTIONTYPE=5)	sec	1
PWLT2	Time of point 2 of piecewise linear curve (FUNCTIONTYPE=5)	sec	2
PWLT3	Time of point 3 of piecewise linear curve (FUNCTIONTYPE=5)	sec	3
PWLT4	Time of point 4 of piecewise linear curve (FUNCTIONTYPE=5)	sec	4
PWLT5	Time of point 5 of piecewise linear curve (FUNCTIONTYPE=5)	sec	5
PWLV1	Height of point 1 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
PWLV2	Height of point 2 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
PWLV3	Height of point 3 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
PWLV4	Height of point 4 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
PWLV5	Height of point 5 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
LINET1	Time of point 1 for linear radiation voltage (FUNCTIONTYPE=6)	sec	0
LINEV1	Height of point 1 for linear radiation voltage (FUNCTIONTYPE=6)	volt	0
LINEK	Slope linear radiation voltage (FUNCTIONTYPE=6)	-	0
RAUGN	Auger recombination rate for electrons in p-region	cm^6/s	1.1E-42
RAUGP	Auger recombination rate for holes in n-region	cm^6/s	3E-43

Model parameters	Description	Units	Default
NDN	Diffusion constant of electrons in n-region at low injection	m^2/s	1E-3
NDP	Diffusion constant of holes in n-region at low injection	m^2/s	7E-4
TAUPO	Hole lifetime in n-region at low injection	sec	2e-8
TAUINFP	Hole lifetime in n-region at saturated SRH condition	sec	4E-8
PDN	Diffusion constant of electrons in p-region at low injection	m^2/s	4E-3
PDP	Diffusion constant of holes in p-region at low injection	m^2/s	5E-4
TAUNO	Electron lifetime in p-region at low injection	sec	1e-6
TAUINFN	Electron lifetime in p-region at saturated SRH condition	sec	2e-6
PDNHI	Diffusion constant of electrons in p+-region at low injection	m^2/s	5E-3
PDPHI	Diffusion constant of holes in p+-region at low injection	m^2/s	1E-4
TAUNOHI	Electron lifetime in p+-region at low injection	sec	1e-7
TAUINFNHI	Electron lifetime in p+-region at saturated SRH condition	sec	2E-7
NDNHI	Diffusion constant of electrons in n+-region at low injection	m^2/s	1e-3
NDPHI	Diffusion constant of holes in n+-region at low injection	m^2/s	2e-4
TAUPOHI	Hole lifetime in n+-region at low injection	sec	2e-8
TAUINFPHI	Hole lifetime in n+-region at saturated SRH condition	sec	4e-8

Table 2.16: Diode Level 3 Model Parameters.

Diode Equations

The equations in this section use the following variables:

$$
\begin{aligned}
V_{di} &= \text{voltage across the intrinsic diode only} \\
V_{th} &= k \cdot T/q \text{ (thermal voltage)} \\
k &= \text{Boltzmann's constant} \\
q &= \text{electron charge} \\
T &= \text{analysis temperature (Kelvin)}
\end{aligned}
$$

$$\begin{aligned} T_0 &= \text{nominal temperature (set using } \mathbf{TNOM} \text{ option)} \\ \omega &= \text{Frequency (Hz)} \end{aligned}$$

Other variables are listed above in the diode model parameters.

Level=1

The level 1 diode is based on the Spice3f5 level 1 model.

DC Current (Level=1)

The intrinsic diode current consists of forward and reverse bias regions where

$$I_D = \begin{cases} \mathbf{IS} \cdot \left[\exp\left(\frac{V_{di}}{\mathbf{N}V_{th}}\right) - 1\right], & V_{di} > -3.0 \cdot \mathbf{N}V_{th} \\ -\mathbf{IS} \cdot \mathbf{IRF} \cdot \left[1.0 + \left(\frac{3.0 \cdot \mathbf{N}V_{th}}{V_{di} \cdot q}\right)^3\right], & V_{di} < -3.0 \cdot \mathbf{N}V_{th} \end{cases}$$

$\mathbf{IRF}$ is a **Xyce**-specific parameter that can be used to scale the reverse-biased current to match measured data. It defaults to 1.0, which reduces the model to strict SPICE3F5 compatibility.

When $\mathbf{BV}$ is explicitly given in the model statement, an exponential current model is substituted when $V_{di} < -\mathbf{BV}$.

This equation for I_D is

$$I_D = -\mathbf{IS} \cdot \exp\left(-\frac{BV + V_{di}}{\mathbf{N}V_{th}}\right)$$

Note here that if $\mathbf{IBV}$ is set by the user, then $\mathbf{BV}$ is changed internally to ensure consistency. This is the equation actually used by **Xyce** but the value of $\mathbf{BV}$ is not required to be specified by the user.

Capacitance (Level=1)

The p-n diode capacitance consists of a depletion layer capacitance C_d and a diffusion capacitance C_{dif}. The first is given by

$$C_d = \begin{cases} \mathbf{CJ} \cdot \mathbf{AREA} \left(1 - \frac{V_{di}}{\mathbf{VJ}}\right)^{-\mathbf{M}}, & V_{di} \leq \mathbf{FC} \cdot \mathbf{VJ} \\ \frac{\mathbf{CJ} \cdot \mathbf{AREA}}{\mathbf{F2}} \left(\mathbf{F3} + \mathbf{M}\frac{V_{di}}{\mathbf{VJ}}\right), & V_{di} > \mathbf{FC} \cdot \mathbf{VJ} \end{cases}$$

The diffusion capacitance (sometimes referred to as the transit time capacitance) is

$$C_{dif} = \mathbf{TT}G_d = \mathbf{TT}\frac{dI_D}{dV_{di}}$$

where G_d is the junction conductance.

Temperature Effects (Level=1)

The diode model contains explicit temperature dependencies in the ideal diode current, the generation/recombination current and the breakdown current. Further temperature dependencies are present in the diode model via the saturation current I_S, the depletion layer junction capacitance CJ, the junction potential V_J.

$$
\begin{aligned}
V_t(T) &= \frac{kT}{q} \\
V_{tnom}(T) &= \frac{k\mathbf{TNOM}}{q} \\
E_g(T) &= E_{g0} - \frac{\alpha T^2}{\beta + T} \\
E_{gNOM}(T) &= E_{g0} - \frac{\alpha \mathbf{TNOM}^2}{\mathbf{TNOM} + \beta} \\
arg1(T) &= -\frac{E_g(T)}{2kT} + \frac{E_{g300}}{2kT_0} \\
arg2(T) &= -\frac{E_{gNOM}(T)}{2k\mathbf{TNOM}} + \frac{E_{g300}}{2kT_0} \\
pbfact1(T) &= -2.0 \cdot V_t(T) \left(1.5 \cdot \ln\left(\frac{T}{T_0}\right) + q \cdot arg1(T)\right) \\
pbfact2(T) &= -2.0 \cdot V_{tnom}(T) \left(1.5 \cdot \ln\left(\frac{\mathbf{TNOM}}{T_0}\right) + q \cdot arg2(T)\right) \\
pbo(T) &= (\mathbf{VJ} - pbfact2(T)) \frac{T_0}{\mathbf{TNOM}} \\
V_J(T) &= pbfact1(T) + \frac{T}{T_0} pbo(T) \\
gma_{old}(T) &= \frac{\mathbf{VJ} - pbo(T)}{pbo(T)} \\
gma_{new}(T) &= \frac{V_J(T) - pbo(T)}{pbo(T)} \\
CJ(T) &= \mathbf{CJ0} \frac{1.0 + \mathbf{M}\left(4.0 \times 10^{-4}\left(T - T_0\right) - gma_{new}(T)\right)}{1.0 + \mathbf{M}\left(4.0 \times 10^{-4}\left(\mathbf{TNOM} - T_0\right) - gma_{old}(T)\right)} \\
I_S(T) &= \mathbf{IS} \cdot \exp\left(\left(\frac{T}{\mathbf{TNOM}} - 1.0\right) \cdot \frac{\mathbf{EG}}{\mathbf{N} V_t(T)} + \frac{\mathbf{XTI}}{\mathbf{N}} \cdot \ln\left(\frac{T}{\mathbf{TNOM}}\right)\right)
\end{aligned}
$$

where, for silicon, $\alpha = 7.02 \times 10^{-4}\ eV/K$, $\beta = 1108\ ^\circ K$ and $E_{g0} = 1.16\ eV$.

Level=3

The level 3 diode implementation is based on [5] with radiation effects added [6] [7].

DC Current (Level=3)

Here the I-V nature is modeled using a diffusion current I_D, a generation/recombination current I_{GR} and a breakdown current I_B

$$I = K_{HI} \cdot I_D + I_{GR} - I_B$$

where

$$I_D = \mathbf{IS} \cdot \left[\exp\left(\frac{V_{di}}{\mathbf{N} V_{th}} \right) - 1 \right]$$

and the injection current factor is given by

$$K_{HI} = \begin{cases} \sqrt{\mathbf{IKF}/(\mathbf{IKF} + I_D)}, & \text{for } \mathbf{IKF} > 0 \\ 1, & \text{otherwise} \end{cases}$$

The generation/recombination current is given by

$$I_{GR} = \mathbf{ISR} \left[\left(1 - \frac{V_{di}}{\mathbf{VJ}} \right)^2 + 0.001 \right]^{\mathbf{M}/2} \left[\exp\left(\frac{V_{di}}{\mathbf{NR} V_{th}} \right) - 1 \right]$$

where the grading parameter $\mathbf{M}$ is $1/2$ for an abrupt junction and $1/3$ for a linearly graded junction. Lastly, the breakdown current is calculated using

$$I_B = \mathbf{IBV} \exp\left(-\frac{V_{di} + \mathbf{BV}}{\mathbf{N} V_{th}} \right)$$

Capacitance (Level=3)

The p-n diode capacitance consists of a depletion layer capacitance C_d and a diffusion capacitance C_{dif}. The first is given by

$$C_d = \begin{cases} \mathbf{CJO} \left(1 - \frac{V_{di}}{\mathbf{VJ}} \right)^{-\mathbf{M}}, & V_{di} \leq \mathbf{FC} \cdot \mathbf{VJ} \\ \mathbf{CJO}(1 - \mathbf{FC})^{-(1+\mathbf{M})} \left[1 - \mathbf{FC}(1 + \mathbf{M}) + \mathbf{M} \frac{V_{di}}{\mathbf{VJ}} \right], & V_{di} > \mathbf{FC} \cdot \mathbf{VJ} \end{cases}$$

The diffusion capacitance (sometimes referred to as the transit time capacitance) is

$$C_{dif} = \mathbf{TT} G_d = \mathbf{TT} \frac{dI}{dV_{di}}$$

where G_d is the junction conductance and I is the diode DC current given above.

Temperature Effects (Level=3)

The diode model contains explicit temperature dependencies in the ideal diode current, the generation/recombination current and the breakdown current. Further temperature

dependencies are present in the diode model via the saturation current I_S and the built-in or contact voltage V_{bi}

$$
\begin{aligned}
I_S(T) &= \mathbf{IS} \cdot \left(\frac{T}{T_0}\right)^{\mathbf{XTI/N}} \exp\left[\frac{\mathbf{EG} \cdot (T - T_0)}{\mathbf{N} \cdot qV_{th}T_0}\right] \\
V_{bi}(T) &= \frac{T}{T_0}\mathbf{VJ} - 2V_{th}\ln\left(\frac{T}{T_0}\right)^{1.5} - \frac{1}{q}\left[\frac{T}{T_0}E_{g0} - E_g(T)\right] \\
E_g(T) &= E_{g0} - \frac{\alpha T^2}{\beta + T}
\end{aligned}
$$

where, for silicon, $\alpha = 7.02 \times 10^{-4}\ eV/K$, $\beta = 1108\ ^\circ K$ and $E_{g0} = 1.16\ eV$.

Radiation Effects

The equations used to incorporate radiation effects into the `LEVEL=3` diode are beyond the scope of this manual. Consult [6] [7] for a detailed analysis.

Caveats

The area parameter that can be specified on the instance line scales many of the device model parameters, and is usually used to specify a number of equivalent parallel devices rather than an actual device area. In the original AimSPICE and ChileSPICE implementation this same area parameter was used to scale the photocurrent. Many of the extracted BJT models in use at Sandia were designed to be used with the instance area parameter omitted. Using the radiation aware model with an area of 1.0 results in absurdly high photocurrents, but specifying any other area causes model parameters to be scaled away from the values originally extracted for the real devices.

To address this problem, the **Xyce** implementation of the radiation-aware device has defined a new model parameter, $\mathbf{DEVICEAREA}$, that can be specified in the model statement instead of the instance line. In the **Xyce** implementation, the instance line area is used only to scale the model parameters in a manner consistent with SPICE 3F5, and the $\mathbf{DEVICEAREA}$ parameter is used only to scale the photocurrent. **This is incompatible with ChileSPICE and Aim-SPICE. Xyce will allow real device models to be used in the radiation context by adding the radiation specific parameters and the $\mathbf{DEVICEAREA}$ parameter to the model statement, whereas the other simulators will require that several level 1 model parameters be converted to per-unit-area values before use with the level 3 model.**

For a more thorough description of p-n junction physics, see [9]. For a thorough description of the U.C. Berkeley SPICE models see Reference [11].

Independent Current Source

General Form	`I<name> <(+) node> <(-) node> + [ [DC] <value> ]` `+ [transient specification]`
Examples	`ISLOW 1 22 SIN(0.5 1.0ma 1KHz 1ms)` `IPULSE 1 3 PULSE(-1 1 2ns 2ns 2ns 50ns 100ns)`
Symbol	
Description	Positive current flows from the positive node through the source to the negative node. Both constant DC values and time-dependent values for the source can be specified. One or both of the DC and transient values may be specified.
Parameters and Options	`[transient specification]` There are five predefined time-varying functions for sources: ■ `PULSE(<parameters>)` - pulse waveform ■ `SIN(<parameters>)` - sinusoidal waveform ■ `EXP(<parameters>)` - exponential waveform ■ `PWL(<parameters>)` - piecewise linear waveform ■ `SFFM(<parameters>)` - frequency-modulated waveform

Transient Specifications

This section outlines the available transient specifications. Δt and T_F are the time step size and simulation end-time, respectively.

Pulse

```
PULSE(I1 I2 TD TR TF PW PER)
```

Parameter	Default	Unit
I1 (Initial Value)	N/A	amp
I2 (Pulse Value)	N/A	amp
TD (Delay Time)	0.0	s
TR (Rise Time)	Δt	s
TF (Fall Time)	Δt	s
PW (Pulse Width)	T_F	s
PER (Period)	T_F	s

Sine

```
SIN(I0 IA FREQ TD THETA)
```

Parameter	Default	Unit
I0 (Offset)	N/A	amp
IA (Amplitude)	N/A	amp
FREQ (Frequency)	0.0	s
TD (Delay)	Δt	s
THETA (Attenuation Factor)	Δt	s

The waveform is shaped according to the following equations:

$$I = \begin{cases} I_0, & 0 < t < T_D \\ I_0 + I_A \sin[2\pi \cdot \mathbf{FREQ} \cdot (t - T_D)] \exp[-(t - T_D) \cdot \mathbf{THETA}], & T_D < t < T_F \end{cases}$$

Exponent

```
EXP(I1 I2 TD1 TAU1 TD2 TAU2)
```

Parameter	Default	Unit
I1 (Initial Phase)	N/A	amp
IA (Amplitude)	N/A	amp
TD1 (Rise Delay Time)	0.0	s
TAU1 (Rise Time Constant)	Δt	s
TD2 (Delay Fall Time)	TD1 $+\Delta t$	s
TAU2 (Fall Time Constant)	Δt	s

The waveform is shaped according to the following equations:

$$I = \begin{cases} I_1, & 0 < t < \mathrm{TD1} \\ I_1 + (I_2 - I_1)\{1 - \exp[-(t - \mathrm{TD1})/\mathrm{TAU1}]\}, & \mathrm{TD1} < t < \mathrm{TD2} \\ I_1 + (I_2 - I_1)\{1 - \exp[-(t - \mathrm{TD1})/\mathrm{TAU1}]\} & \\ \quad +(I_1 - I_2)\{1 - \exp[-(t - \mathrm{TD2})/\mathrm{TAU2}]\}, & \mathrm{TD2} < t < T_2 \end{cases}$$

Piecewise Linear

```
PWL  <t0> <i0> [<tn> <in>]*

PWL  FILE "<name>"
```

Parameter	Default	Unit
<tn> (Time at Corner)	s	none
<in> (Current at Corner)	amp	none
<n> (Number of Repetitions)	positive integer, 0, or -1	none

When the FILE option is given, **Xyce** will read the corner points from the file specified in the <name> field. This file should be a plain ASCII text file with time/current pairs. There should be one pair per line, and the time and current values should be separated by whitespace or commas.

Frequency Modulated

```
SFFM (<ioff> <iampl> <fc> <mod> <fm>)
```

Parameter	Default	Unit
<ioff> (Offset Current)	amp	none
<iampl> (Peak Current Amplitude)	amp	none
<fc> (Carrier Frequency)	hertz	1/**TSTOP**
<mod> (Modulation Index)		0
<fm> (Modulation Frequency)	hertz	1/**TSTOP**

The waveform is shaped according to the following equations:

$$V = \mathbf{ioff} + \mathbf{iampl} \cdot \sin(2\pi \cdot \mathbf{fc} \cdot \mathbf{TIME} + \mathrm{mod} \cdot \sin(2\pi \cdot \mathbf{fm} \cdot \mathbf{TIME}))$$

where $\mathbf{TIME}$ is the current simulation time.

Independent Voltage Source

The syntax of this device is exactly the same as for a Independent Current Source. For an Independent Voltage Source, substitute an I for the V on the instance line. The V device generates a voltage, whereas the I device generates a current. For details about the Independent Current Source, see section 2.2.

General Form	`V<name> <(+) node> <(-) node> + [ [DC] <value> ]` `+ [transient specification]`
Examples	`VSLOW 1 22 SIN(0.5 1.0ma 1KHz 1ms)` `VPULSE 1 3 PULSE(-1 1 2ns 2ns 2ns 50ns 100ns)`
Symbol	
Description	Positive current flows from the positive node through the source to the negative node. Both constant DC values and time-dependent values for the source can be specified. One or both of the DC and transient values may be specified.
Parameters and Options	`[transient specification]` There are five predefined time-varying functions for sources: ■ `PULSE(<parameters>)` - pulse waveform ■ `SIN(<parameters>)` - sinusoidal waveform ■ `EXP(<parameters>)` - exponential waveform ■ `PWL(<parameters>)` - piecewise linear waveform ■ `SFFM(<parameters>)` - frequency-modulated waveform

Voltage Controlled Voltage Source

General Form	`E<name> <(+) node> <(-) node> <(+) controlling node>`
	`+ <(-) controlling node> <gain>`
	`E<name> <(+) <node> <(-) node> VALUE = { <expression> }`
	`E<name> <(+) <node> <(-) node> TABLE { <expression> } =`
	`+ < <input value>,<output value> >*`

Examples	`EBUFFER 1 2 10 11 5.0`
	`ESQROOT 5 0 VALUE = {5V*SQRT(V(3,2))}`
	`ET2 2 0 TABLE {V(ANODE,CATHODE)} = (0,0) (30,1)`

Symbol	
Description	In the first form, a specified voltage drop elsewhere in the circuit controls the voltage-source output. The second and third forms using the `VALUE` and `TABLE` keywords, respectively, are used in analog behavioral modeling. These two forms are automatically converted within **Xyce** to its principal ABM device, the `B` nonlinear dependent source device. See the **Xyce** User's Guide for more information on analog behavioral modeling.
Parameters and Options	`(+)` and `(-)` nodes Output nodes. Positive current flows from the `(+)` node through the source to the `(-)` node. `<(+) controlling node>` and `<(-) controlling node>` Node pairs that define a set of controlling voltages. A given node may appear multiple times and the output and controlling nodes may be the same.

Current Controlled Current Source

General Form	`F<name> <(+) node> <(-) node>`
	`+ <controlling V device name> <gain>`
	`F<name> <(+) node> <(-) node> POLY(<value>)`
	`+ <controlling V device name>*`
	`+ < <polynomial coefficient value> >*`

Examples	`FSENSE 1 2 VSENSE 10.0`
	`FAMP 13 0 POLY(1) VIN 0 500`
	`FNONLIN 100 101 POLY(2) VCNTRL1 VCINTRL2 0.0 13.6 0.2 0.005`

Symbol	
Description	In the first form, a specified current elsewhere in the circuit controls the current-source output. The second form using the `POLY` keyword is used in analog behavioral modeling. This form is automatically converted within **Xyce** to its principal ABM device, the `B` nonlinear dependent source device. See the **Xyce** User's Guide for more information on analog behavioral modeling.
Parameters and Options	`(+)` and `(-)` nodes Output nodes. Positive current flows from the `(+)` node through the source to the `(-)` node. `<controlling V device name>` The controlling voltage source which must be an independent voltage source (V device).

Current Controlled Voltage Source

The syntax of this device is exactly the same as for a Current Controlled Current Source. For a Current-Controlled Voltage Source just substitute an H for the F. The H device generates a voltage, whereas the F device generates a current.

General Form	`H<name> <(+) node> <(-) node>`
	`+ <controlling V device name> <gain>`
	`H<name> <(+) node> <(-) node> POLY(<value>)`
	`+ <controlling V device name>*`
	`+ < <polynomial coefficient value> >*`

Examples	`HSENSE 1 2 VSENSE 10.0`
	`HAMP 13 0 POLY(1) VIN 0 500`
	`HNONLIN 100 101 POLY(2) VCNTRL1 VCINTRL2 0.0 13.6 0.2 0.005`

Symbol	

Voltage Controlled Current Source

General Form	`G<name> <(+) node> <(-) node> <(+) controlling node>`
	`+ <(-) controlling node> <transconductance>`
	`G<name> <(+) <node> <(-) node> VALUE = { <expression> }`
	`G<name> <(+) <node> <(-) node> TABLE { <expression> } =`
	`+ < <input value>,<output value> >*`

Examples	`GBUFFER 1 2 10 11 5.0`
	`GPSK 11 6 VALUE = {5MA*SIN(6.28*10kHz*TIME+V(3))}`
	`GA2 2 0 TABLE {V(5)} = (0,0) (1,5) (10,5) (11,0)`

Symbol	
Description	In the first form, a specified voltage drop elsewhere in the circuit controls the current-source output. The second and third forms using the `VALUE` and `TABLE` keywords, respectively, are used in analog behavioral modeling. These two forms are automatically converted within **Xyce** to its principal ABM device, the `B` nonlinear dependent source device. See the **Xyce** User's Guide for more information on analog behavioral modeling.
Parameters and Options	`(+)` and `(-)` nodes Output nodes. Positive current flows from the `(+)` node through the source to the `(-)` node. `<(+) controlling node>` and `<(-) controlling node>` Node pairs that define a set of controlling voltages. A given node may appear multiple times and the output and controlling nodes may be the same.

Nonlinear Dependent Source

General Form	`B<name> <(+) node> <(-) node> V={ABM expression}` `B<name> <(+) node> <(-) node> I={ABM expression}`

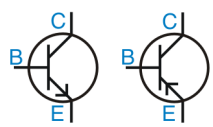
Examples	`B1 2 0 V={sqrt(V(1))}`
	`B2 4 0 V={V(1)*TIME}`
	`B3 4 2 I={I(V1) + V(4,2)/100}`
	`B4 5 0 V={Table {V(5)}=(0,0) (1.0,2.0) (2.0,3.0) (3.0,10.0)}`

Description	The nonlinear dependent source device, also known as the B-source device, is used in analog behavioral modeling (ABM). The `(+)` and `(-)` nodes are the output nodes. Positive current flows from the `(+)` node through the source to the `(-)` node.
Comments	See the "Analog Behavioral Modeling" chapter of the **Xyce** User's Guide for more information on the Bsource device and ABM expressions, and the "Parameters and Expressions" section of the User's Guide for more information on expressions in general. **Note: the braces surrounding all expressions are required.**

Bipolar Junction Transistor (BJT)

General Form	`Q<name> < collector node> <base node> <emitter node>` `+ [substrate node] <model name> [area value]`

Examples	`Q2 10 2 9 PNP1`
	`Q12 10 2 9 NeutPNP DELAY=10ms NEUT=1e13`
	`Q12 14 2 0 1 NPN2 2.0`
	`Q6 VC 4 11 [SUB] LAXPNP`

Symbols	
Model Form	`.MODEL <model name> NPN [model parameters]` `.MODEL <model name> PNP [model parameters]`

Parameters and Options	`[substrate node]`
	Optional and defaults to ground. Since **Xyce** permits alphanumeric node names and because there is no easy way to make a distinction between these and the model names, the name (not a number) used for the substrate node must be enclosed in square brackets `[ ]`. Otherwise, nodes would be interpreted as model names. See the fourth example above.
	`[area value]`
	The relative device area with a default value of 1.

Comments	The BJT is modeled as an intrinsic transistor using ohmic resistances in series with the collector (RC/area), with the base (value varies with current, see BJT equations) and with the emitter (RE/area).For model parameters with optional names, such as VAF and VA (the optional name is in parentheses), either may be used.For model types NPN and PNP, the isolation junction capacitance is connected between the intrinsic-collector and substrate nodes. This is the same as in SPICE and works well for vertical IC transistor structures.

BJT Level selection

Xyce supports five BJT models. The level 1 model is based on the documented standard SPICE 3F5 BJT model, but was coded independently at Sandia. It is mostly based on the classic Gummel-Poon BJT model [8]. The levels 2, 3 and 4 models add effects to the level 1 model. Level 3 adds neutron damage effects to level 1 [9]. Level 2 and 4 are identical and

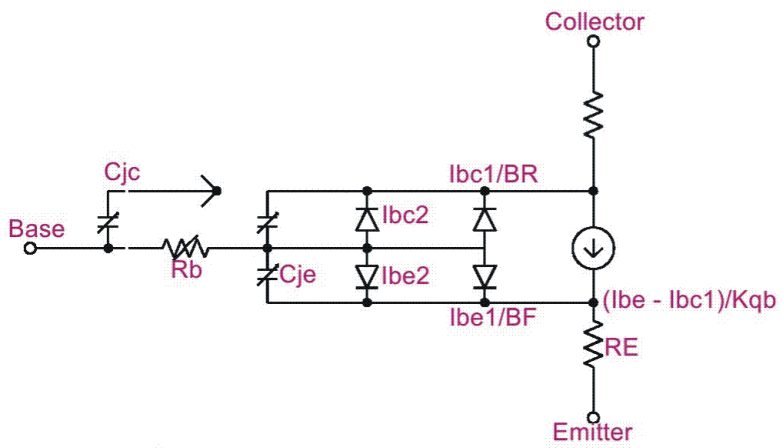


Figure 2.1. BJT model schematic. Adapted from reference [2].

add effects due to ionizing radiation [6] [7]. Level 5 specifies the Deveney-Wrobel neutron-damage model with added photocurrent effects. Specify the model parameter **LEVEL** to select the model.

BJT Operating Temperature

Model parameters may be assigned unique measurement temperatures using the **TNOM** model parameter. See BJT model parameters for more information.

Level=1 Model Parameters

Table 2.17 gives the available model parameters for the level 1 BJT.

Model parameters	Description	Units	Default
BF	Ideal Maximum Forward Beta		100.0
BR	Ideal Maximum Reverse Beta		1.0
CJC	Base-collector Zero-bias p-n Capacitance	farad	0.0
CJE	Base-emitter Zero-bias p-n Capacitance	farad	0.0
CJS	Substrate Zero-bias p-n Capacitance	farad	0.0
EG	Bandgap Voltage (Barrier Height)	eV	1.11
FC	Forward-bias Depletion Capacitor Coefficient		0.5
IKF	Corner for Forward-beta High-current Roll-off	amp	1E99
IKR	Corner for Reverse-beta High-current Roll-off	amp	1E99

Model parameters	Description	Units	Default
IRB	Current at which Rb Falls off by half	amp	0.0
IS	Transport Saturation Current	amp	1E-16
ISC	Base-collector Leakage Saturation Current	amp	0.0
ISE	Base-emitter Leakage Saturation Current	amp	0.0
ITF	Transit Time Dependency on Ic	amp	0.0
KF	Flicker Noise Coefficient		0.0
MJC	Base-collector p-n Grading Factor		0.33
MJE	Base-emitter p-n Grading Factor		0.33
MJS	Substrate p-n Grading Factor		0.0
NC	Base-collector Leakage Emission Coefficient		2.0
NE	Base-emitter Leakage Emission Coefficient		1.5
NF	Forward Current Emission Coefficient		1.0
NK	High Current Rolloff Coefficient		0.5
NR	Reverse Current Emission Coefficient		1.0
PTF	Excess Phase @ $1/(2\pi \cdot \mathrm{TF})$Hz	degree	0.0
RB	Zero-bias (Maximum) Base Resistance	ohm	0.0
RBM	Minimum Base Resistance	ohm	0.0
RC	Collector Ohmic Resistance	ohm	0.0
RE	Emitter Ohmic Resistance	ohm	0.0
TEMPMODEL	Specification to type of parameter interpolation over temperature	string	
TF	Ideal Forward Transit Time	sec	0.0
TR	Ideal Reverse Transit Time	sec	0.0
TNOM	Parameter Measurement Temperature	°C	27.0
VAF	Forward Early Voltage	volt	1E99
VAR	Reverse Early Voltage	volt	1E99
VJC	Base-collector Built-in Potential	volt	0.75
VJE	Base-emitter Built-in Potential	volt	0.75
VJS	Substrate Built-in Potential	volt	0.75
VTF	Transit Time Dependency on $\mathrm{V_{bc}}$	volt	1E99
XCJC	Fraction of **CJC** Connected Internally to **RB**		1.0
XTB	Forward and Reverse Beta Temperature Coefficient		0.0
XTF	Transit Time Bias Dependence Coefficient		0.0

Model parameters	Description	Units	Default

Table 2.17: BJT Model Parameters.

Level=2 and Level=4 Model Parameters

Table 2.18 gives the available model parameters for the levels 2 and 4 radiation-aware BJT. Level 2 and Level 4 are identical.

Model parameters	Description	Units	Default
BF	Ideal Maximum Forward Beta		100.0
BR	Ideal Maximum Reverse Beta		1.0
CJC	Base-collector Zero-bias p-n Capacitance	farad	0.0
CJE	Base-emitter Zero-bias p-n Capacitance	farad	0.0
CJS	Substrate Zero-bias p-n Capacitance	farad	0.0
EG	Bandgap Voltage (Barrier Height)	eV	1.11
FC	Forward-bias Depletion Capacitor Coefficient		0.5
IKF	Corner for Forward-beta High-current Roll-off	amp	1E99
IKR	Corner for Reverse-beta High-current Roll-off	amp	1E99
IRB	Current at which Rb Falls off by half	amp	0.0
IS	Transport Saturation Current	amp	1E-16
ISC	Base-collector Leakage Saturation Current	amp	0.0
ISE	Base-emitter Leakage Saturation Current	amp	0.0
ITF	Transit Time Dependency on Ic	amp	0.0
KF	Flicker Noise Coefficient		0.0
MJC	Base-collector p-n Grading Factor		0.33
MJE	Base-emitter p-n Grading Factor		0.33
MJS	Substrate p-n Grading Factor		0.0
NC	Base-collector Leakage Emission Coefficient		2.0
NE	Base-emitter Leakage Emission Coefficient		1.5
NF	Forward Current Emission Coefficient		1.0
NK	High Current Rolloff Coefficient		0.5
NR	Reverse Current Emission Coefficient		1.0
PTF	Excess Phase @ $1/(2\pi \cdot \mathrm{TF})$Hz	degree	0.0
RB	Zero-bias (Maximum) Base Resistance	ohm	0.0

Model parameters	Description	Units	Default
RBM	Minimum Base Resistance	ohm	0.0
RC	Collector Ohmic Resistance	ohm	0.0
RE	Emitter Ohmic Resistance	ohm	0.0
TEMPMODEL	Specification to type of parameter interpolation over temperature	string	
TF	Ideal Forward Transit Time	sec	0.0
TR	Ideal Reverse Transit Time	sec	0.0
TNOM	Parameter Measurement Temperature	°C	27.0
VAF	Forward Early Voltage	volt	1E99
VAR	Reverse Early Voltage	volt	1E99
VJC	Base-collector Built-in Potential	volt	0.75
VJE	Base-emitter Built-in Potential	volt	0.75
VJS	Substrate Built-in Potential	volt	0.75
VTF	Transit Time Dependency on $\mathrm{V_{bc}}$	volt	1E99
XCJC	Fraction of **CJC** Connected Internally to **RB**		1.0
XTB	Forward and Reverse Beta Temperature Coefficient		0.0
XTF	Transit Time Bias Dependence Coefficient		0.0
BC	Doping density in base	m^{-3}	1E22
BDN	Diffusion constant of electrons in base at low injection	m^2/s	1E-3
BDP	Diffusion constant of holes in base at low injection	m^2/s	2E-4
BTAUINF	Electron lifetime in base at saturated SRH condition	sec	4E-8
BTAU0	Electron lifetime in base at low injection	sec	2E-8
BW	Width of base	m	1E-6
CC	Doping density in collector	m^{-3}	5E20
CCHI	Doping density in n^+-region (used when ISCHILOW=1)	m^{-3}	1E24
CDN	Diffusion constant of electrons in collector at low injection	m^2/s	5E-3
CDNHI	Diffusion constant of electrons in n^+-region at low injection (when ISCHILOW=1)	m^2/s	4E-3
CDP	Diffusion constant of holes in collector at low injection	m^2/s	7E-4

Model parameters	Description	Units	Default
CDPHI	Diffusion constant of holes in n^+-region at low injection (when ISCHILOW=1)	m^2/s	8E-4
CTAUINF	Hole lifetime in collector at saturated SRH condition	sec	2E-6
CTAUINFHI	Hole lifetime in collector in n^+-region at saturated SRH condition (when ISHILO=1)	sec	2E-7
CTAUO	Hole lifetime in collector at low injection	sec	1E-6
CTAUOHI	Hole lifetime in collector in n^+-region at low injection (when ISHILO=1)	sec	1E-7
CW	Width of collector	m	4E-6
CWHI	Width of n^+-region (when ISCHILOW=1)	m	5E-5
DEVICEAREA	Area of device	m^2	1.0
EC	Doping density in emitter	m^{-3}	1E25
EDN	Diffusion constant of electrons in emitter at low injection	m^2/s	3E-3
EDP	Diffusion constant of holes in emitter at low injection	m^2/s	2E-4
ETAUINF	Hole lifetime in emitter at saturated SRH condition	sec	4E-8
ETAUO	Hole lifetime in emitter at low injection	sec	2E-8
EW	Width of emitter	m	2E-6
ISCHILOW	"Is the collector a Hi-Lo structure?" (0=no, 1=yes) *CAUTION: Tor Fjeldly's paper refers to a parameter "ISCHILO", but the code actually references "ISCHILOW"! If "ISCHILO" is used in a netlist then the parameter is ignored and the default value for* ISCHILOW *is used*	-	0 (no)
GRORDER	Order of magnitude of radiation generation rate	-	25
NI	Intrinsic concentration	m^{-3}	1.45E16
PERMITTIVITY	Dielectric permittivity of the semiconductor	F/m	1.0443E-10
RAUGN	Auger recombination rate for electrons in p-region	cm^6/s	1.1E-42
RAUGP	Auger recombination rate for holes in n-region	cm^6/s	3E-43

Model parameters	Description	Units	Default
FUNCTIONTYPE	Selects the shape of the radiation pulse. May take the following values: 0 (none), 1 (pulse wave form), 2 (sinusoidal wave form), 3 (exponential wave form), 4 (piecewise linear wave form), 5 (frequency modulated wave form), 6 (linearly ramped radiation), or 7 (take radiation wave form from data file or expression)	-	0 (none)
PULSEV1	Initial value of radiation pulse (FUNCTIONTYPE=1)	volt	0.0
PULSEV2	Maximum value of radiation pulse (FUNCTIONTYPE=1)	volt	4.3
PULSETD	Delay of radiation pulse (FUNCTIONTYPE=1)	sec	0.0
PULSETR	Rise time of radiation pulse (FUNCTIONTYPE=1)	sec	1E-5
PULSETF	Fall time of radiation pulse (FUNCTIONTYPE=1)	sec	1E-5
PULSEPW	Width of radiation pulse (FUNCTIONTYPE=1)	sec	1E-5
PULSEPER	Period of radiation pulse (FUNCTIONTYPE=1)	sec	1E10
SINVO	Initial value of sinusoidal radiation voltage (FUNCTIONTYPE=2)	volt	0.0
SINVA	Amplitude of sinusoidal radiation voltage (FUNCTIONTYPE=2)	volt	0.0
SINFREQ	Frequency of sinusoidal radiation voltage (FUNCTIONTYPE=2)	Hz	1.0
SINTD	Delay of sinusoidal radiation voltage (FUNCTIONTYPE=2)	sec	0.0
SINTHETA	Inverse of time constant for exponential envelope of sinusoidal radiation voltage (FUNCTIONTYPE=2)	sec^{-1}	0.0
EXPV1	Initial value of exponential cusp radiation voltage (FUNCTIONTYPE=3)	volt	0.0
EXPV2	Height of exponential cusp radiation voltage (FUNCTIONTYPE=3)	volt	0.0
EXPTD1	Rise delay time of exponential cusp radiation voltage (FUNCTIONTYPE=3)	sec	0.0
EXPTAU1	Rise time constant of exponential cusp radiation voltage (FUNCTIONTYPE=3)	sec	1e-2

Model parameters	Description	Units	Default
EXPTD2	Fall delay time of exponential cusp radiation voltage (FUNCTIONTYPE=3)	sec	1E10
EXPTAU2	Fall time constant of exponential cusp radiation voltage (FUNCTIONTYPE=3)	sec	1E10
SFFMVO	Offset of single frequency FM curve (FUNCTIONTYPE=4)	volt	0.0
SFFMVA	Amplitude of single frequency FM curve (FUNCTIONTYPE=4)	volt	0.0
SFFMFC	Carrier frequency of single frequency FM curve (FUNCTIONTYPE=4)	Hz	1.0
SFFMMDI	Modulation index of single frequency FM curve (FUNCTIONTYPE=4)	-	0.0
SFFMFS	Signal frequency of single frequency FM curve (FUNCTIONTYPE=4)	Hz	0.0
PWLT1	Time of point 1 of piecewise linear curve (FUNCTIONTYPE=5)	sec	1
PWLT2	Time of point 2 of piecewise linear curve (FUNCTIONTYPE=5)	sec	2
PWLT3	Time of point 3 of piecewise linear curve (FUNCTIONTYPE=5)	sec	3
PWLT4	Time of point 4 of piecewise linear curve (FUNCTIONTYPE=5)	sec	4
PWLT5	Time of point 5 of piecewise linear curve (FUNCTIONTYPE=5)	sec	5
PWLV1	Height of point 1 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
PWLV2	Height of point 2 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
PWLV3	Height of point 3 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
PWLV4	Height of point 4 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
PWLV5	Height of point 5 of piecewise linear curve (FUNCTIONTYPE=5)	volt	0
LINET1	Time of point 1 for linear radiation voltage (FUNCTIONTYPE=6)	sec	0
LINEV1	Height of point 1 for linear radiation voltage (FUNCTIONTYPE=6)	volt	0
LINEK	Slope linear radiation voltage (FUNCTIONTYPE=6)	-	0

Model parameters	Description	Units	Default
PULSEDATA	Expression or filename of (T,V) pairs to use instead of internal radiation source (FUNCTIONTYPE=7) (filename must be in double quotation marks, e.g. PULSEDATA="pulse.dat", expression must be in braces)	-	-

Table 2.18: Level 2 and Level 4 BJT Model Parameters.

Level=3 Model Parameters

Table 2.19 gives the available model parameters for the level 3 transient neutron radiation-aware BJT. See [9] for a description of the model.

Model parameters	Description	Units	Default
FLUENCE	Neutron fluence (DC, not yet implemented)	cm^{-2}	0.0
A1	Neutron radiation model parameter at low injection		1E-14
A2	Neutron radiation model parameter at high injection		1E-14
B1	Neutron radiation model parameter at low injection		-0.26
B2	Neutron radiation model parameter at high injection		-0.26
GAMMA	Neutron radiation model adjustable smoothing parameter		1.0
TAU_ANNEAL	Annealing parameter tau		0.0
ALPHA_ANNEAL	Annealing parameter alpha		1.0
PULSEDATA	Input pulse expression. Flux may be specified with an expression, or with an input file as in levels 2 and 4.	-	-

Table 2.19: Level 3 BJT Model Parameters.

Level=3 Model Parameters

Table 2.19 gives the available model parameters for the level 3 transient neutron radiation aware BJT. In addition, all of the basic BJT (level 1) model parameters are applicable. Detailed descriptions of the level 3 parameters are contained in an unpublished reference which is available upon request. The model itself is similar to the one described in [9].

The PULSEDATA parameter is used to specify the pulse affecting the device. This can be specified either as an expression or as input from a file as in level 2 and 4. In the

expression method, the flux is simply specified as a time dependent function. An example would be a pulse of flux 1e12 starting at time=100ns and continuing for 10ns. This would be specified with:

```
PULSEDATA = {IF(TIME>1E-7, IF(TIME <1.1E-7, 1E12, 0), 0)}
```

Level=5 Model Parameters

Details of the level 5 BJT model are not in the scope of this document. This model will be documented in detail in a separate guide.

The level 5 BJT is based on the level 4 with some important differences. The base resistance model is different from the one traditionally used in Gummel-Poon models, and does not depend on **RB**, **RBM**, and **IRB**. If you specify these parameters they will be ignored and a warning will be emitted on the console output. The parameters that define the base resistance model are instead **RBMIN**, **RBS**, **RBINT**, and **IRBMAX**.

All other parameters of the level 4 (and level 2) BJT are carried over exactly to the level 5 BJT, and so are listed in Table 2.18. The additional parameters that define the neutron-damage effects and base-resistance model are listed in Table 2.20.

Model parameters	Description	Units	Default
ISEFCOEF	Coefficient of expression defining fully annealed post-neutron value of Ise	A	0
ISEFCONST	Constant term of expression defining fully annealed post-neutron value of Ise	A	0
ISEFEXP	Exponent in expression defining fully annealed post-neutron value of Ise		1
ISNNCOEF	Coefficient of expression defining post-neutron excess base current	A	0
ISNNCONST	Constant term of expression defining post-neutron excess base current	A	0
ISNNEXP	Exponent in expression defining post-neutron excess base current		1
NEN	Emission coefficient of base recombination current		0
NN	Emission coefficient of post-neutron excess base current		0
RBMIN	Minimum value of base resistance	Ohm	0
RBS	Slope of base resistive voltage equation on log plot		1
RBINT	Y intercept of base resistive voltage equation on log plot	Ohm	0

Model parameters	Description	Units	Default
IRBMAX	Current offset in resistance expression	A	0

Table 2.20: Level 5 BJT Model Parameters (excluding those in common with levels 2 and 4).

Additional Level=5 Parameters

In addition to the parameters that are specified in the .MODEL statement, the level 5 BJT takes two additional parameters specified on the device line itself.

DELAY specifies the time at which the neutron damage occurs. **NEUT** specifies the magnitude of the neutron burst.

Specification of radiation dose for levels 2, 4 and 5 BJT

In all cases, voltage parameters in Table 2.18 related to the "radiation voltage" are relative to the electron-hole generation rate (e.g. if PULSEV2 is 4.3 and GRORDER is 26, the generation rate at the top of the pulse is $4.3 \times 10^{26} m^{-3} s^{-1}$). Conversion between radiation dose in rad$/s$ is dependent on the material type, but in the case of silicon a dose of 1rad$/s$ is $4.3 \times 10^{19} m^{-3} s^{-1}$, so specifying **PULSEV1=0**, **PULSEV2=4.3**, **GRORDER=26** along with **FUNCTIONTYPE=1** is equivalent to a square pulse with a peak dose rate of 1×10^{7}rad$/s$.

Both the level 2 and level 4 support a **FUNCTIONTYPE=7**, allowing a single parameter **PULSEDATA** to specify the radiation dose profile. If used, **PULSEDATA** can be either an expression in curly braces, or the double-quoted name of a file of time, voltage pairs representing the dose. Units of the expression or file entries are the same as those of **PULSEV1**. The **GRORDER** parameter is still used to determine the exponent of the "radiation voltage" as it is for the other function types.

BJT Equations

The BJT implementation within **Xyce** is based on [1]. The equations in this section describe an NPN transistor. For the PNP device, reverse the signs of all voltages and currents. The equations use the following variables:

V_{be} = intrinsic base-intrinsic emitter voltage
V_{bc} = intrinsic base-intrinsic collector voltage
V_{bs} = intrinsic base-substrate voltage
V_{bw} = intrinsic base-extrinsic collector voltage (quasi-saturation only)
V_{bx} = extrinsic base-intrinsic collector voltage
V_{ce} = intrinsic collector-intrinsic emitter voltage
V_{js} = (NPN) intrinsic collector-substrate voltage
= (PNP) intrinsic substrate-collector voltage

$$
\begin{aligned}
V_t &= kT/q \text{ (thermal voltage)} \\
V_{th} &= \text{threshold voltage} \\
k &= \text{Boltzmann's constant} \\
q &= \text{electron charge} \\
T &= \text{analysis temperature (K)} \\
T_0 &= \text{nominal temperature (set using } \mathbf{TNOM} \text{ option)}
\end{aligned}
$$

Other variables are listed above in BJT Model Parameters.

DC Current

The BJT model is based on the Gummel and Poon model [10] where the different terminal currents are written

$$
\begin{aligned}
I_b &= -I_{be} - I_{bc} + I_{re} + I_{rc} + S\frac{dQ_b}{dt} \\
I_e &= -I_{cc} - I_{be} + I_{re} + S\frac{dQ_{dife}}{dt} + C_{de}\frac{dV_{be}}{dt} \\
I_c &= -I_{cc} - I_{bc} + I_{rc} + S\frac{dQ_{difc}}{dt} + C_{dc}\frac{dV_{bc}}{dt}
\end{aligned}
$$

Here, Q_{dife} and Q_{difc} are the hole charges per unit area in the base affiliated with the electrons introduced across the emitter-base and collector-base junctions, respectively. Also, Q_{be} and Q_{bc} are donations to the hole charge of the base affiliated with the differences in the depletion regions of the emitter-base and collector-base junctions, respectively. Lastly, S is the cross-sectional area of the device. The intermediate currents used are defined as

$$
\begin{aligned}
-I_{be} &= \frac{\mathbf{IS}}{\mathbf{BF}}\left[\exp\left(\frac{V_{be}}{\mathbf{NF}V_{th}}\right) - 1\right] \\
-I_{cc} &= \frac{Q_{bo}}{Q_b}\mathbf{IS}\left[\exp\left(\frac{V_{be}}{\mathbf{NF}V_{th}}\right) - \exp\left(\frac{V_{bc}}{\mathbf{NF}V_{th}}\right)\right] \\
-I_{bc} &= \frac{\mathbf{IS}}{\mathbf{BR}}\left[\exp\left(\frac{V_{bc}}{\mathbf{NE}V_{th}}\right) - 1\right] \\
I_{re} &= \mathbf{ISE}\left[\exp\left(\frac{V_{be}}{\mathbf{NE}V_{th}}\right) - 1\right] \\
I_{rc} &= \mathbf{ISC}\left[\exp\left(\frac{V_{bc}}{\mathbf{NC}V_{th}}\right) - 1\right]
\end{aligned}
$$

where the last two terms are the generation/recombination currents related to the emitter and collector junctions, respectively. The charge Q_b is the majority carrier charge in the base at large injection levels and is a key difference in the Gummel-Poon model over the earlier Ebers-Moll model.

Capacitance Terms

The p-n diode capacitance consists of a depletion layer capacitance C_d and a diffusion capacitance C_{dif}. The first is given by

$$C_d = \begin{cases} \mathbf{CJO}\left(1 - \frac{V_{di}}{\mathbf{VJ}}\right)^{-\mathbf{M}} & V_{di} \leq \mathbf{FC} \cdot \mathbf{VJ} \\ \mathbf{CJO}\,(1 - \mathbf{FC})^{-(1+\mathbf{M})}\left[1 - \mathbf{FC}(1+\mathbf{M}) + \mathbf{M}\frac{V_{di}}{\mathbf{VJ}}\right] & V_{di} > \mathbf{FC} \cdot \mathbf{VJ} \end{cases}$$

The diffusion capacitance (sometimes referred to as the transit time capacitance) is

$$C_{dif} = \mathbf{TT}G_d = \mathbf{TT}\frac{dI}{dV_{di}}$$

where G_d is the junction conductance and I is the diode DC current given above.

Temperature Effects

Spice temperature effects are default, but all levels of the BJT have a more advanced temparature compensation available. By specifying TEMPMODEL=QUADRATIC in the netlist, parameters can be interpolated quadratically between measured values extracted from data. In the BJT, IS and ISE are interpolated logarithmically because they can change over an order of magnitude or more for temperature ranges of interest. See Section 5.3 of the User's Guide for more details on how to include quadratic temperature effects.

Radiation Effects

The equations for the radiation effects are beyond the scope of this manual. See [6] [7] for details.

Caveats

The area parameter that can be specified on the instance line scales many of the device model parameters, and is usually used to specify a number of equivalent parallel devices rather than an actual device area. In the original AimSPICE and ChileSPICE implementation this same area parameter was used to scale the photocurrent. Many of the extracted BJT models in use at Sandia were designed to be used with the instance area parameter omitted. Using the radiation aware model with an area of 1.0 results in absurdly high photocurrents, but specifying any other area causes model parameters to be scaled away from the values originally extracted for the real devices.

To address this problem, the **Xyce** implementation of the radiation-aware device has defined a new model parameter, $\mathbf{DEVICEAREA}$, that can be specified in the model statement instead of the instance line. In the **Xyce** implementation, the instance line area is used only to scale the model parameters in a manner consistent with SPICE 3F5, and the $\mathbf{DEVICEAREA}$ parameter is used only to scale the photocurrent. **This is incompatible with early versions of ChileSPICE and with the Aim-SPICE implementation. Xyce**

will allow real device models to be used in the radiation context by adding the radiation specific parameters and the DEVICEAREA parameter to the model statement, whereas the other simulators will require that several level 1 model parameters be converted to per-unit-area values before use with the level 2 model.

In releases prior to **Xyce** Release 3.0, the level 2 BJT was based on an original implementation of the radiation aware BJT in AIM-Spice. Numerous numerical problems were found in that implementation, and a new level 4 BJT was written, based on the native **Xyce** BJT implementation. In **Xyce** Release 3.0, the original AIM-Spice implementation was removed. The level 2 and Level 4 are now identical, with level 2 being provided merely for backward compatibility of netlists.

While the level 4 BJT handles the photocurrent differently than the original AIM-Spice level 2, we observed late in release testing for version 2.1 of **Xyce** that there are still some cases where enabling current crowding (IRB nonzero) leads to convergence failures. This will result in netlists failing with “Timestep too small” errors. This will be corrected in a future version. If such problems are observed, try setting IRB to zero, and forward your netlist to the **Xyce** development team to help us track down the issue.

For further information on BJT models, see [10]. For a thorough description of the U.C. Berkeley SPICE models see Reference [11].

Junction Field-Effect Transistor (JFET)

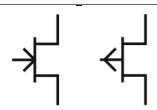
General Form

```
J<name> <drain node> <gate node> <source node> <model name>
+ [area value] [device parameters]
```

Examples

```
JIN 100 1 0 JFAST
J13 22 14 23 JNOM 2.0
J1 1 2 0 2N5114
```

Symbols



Model Form

```
.MODEL <model name> NJF [model parameters]
.MODEL <model name> PJF [model parameters]
```

Parameters and Options

`<drain node>`

Node connected to drain.

`<gate node>`

Node connected to gate.

`<source node>`

Node connected to source.

`<source node>`

Name of model defined in .MODEL line.

`[area value]`

The `JFET` is modeled as an intrinsic FET using an ohmic resistance (`RD/area`) in series with the drain and another ohmic resistance (`RS/area`) in series with the source. `area` is an area factor with a default of `1`.

`[device parameters]`

Parameters listed in Table 2.21 may be provided as space separated `<parameter>=<value>` specifications as needed. Any number of parameters may be specified.

Comments	The JFET was first proposed and analyzed by Shockley. The SPICE- compatible JFET model is an approximation to the Shockley analysis that employs an adjustable parameter B. Both the Shockley formulation and the SPICE approximation are available in Xyce.

Device Parameters

Table 2.21 gives the available device parameters for the JFET.

Parameter	Description	Units	Default
AREA	device area	m^2	1
TEMP	Device temperature	°C	27

Table 2.21: JFET Device Parameters.

Model Parameters

Table 2.22 gives the available model parameters for the JFET.

Parameter	Description	Units	Default
AF	Flicker noise exponent	–	1
B	Doping tail parameter (level 1)	V^{-1}	1
BETA	Transconductance parameter	A/V^2	0.0001
CGD	Zero-bias gate-drain junction capacitance	F	0
CGS	Zero-bias gate-source junction capacitance	F	0
DELTA	Saturation voltage parrameter (level 2)	V	0
FC	Coefficient for forward-bias depletion capacitance	F	0.5
IS	Gate junction saturation current	A	1e-14
KF	Flicker noise coefficient	–	0.05
LAMBDA	Channel length modulation	V^{-1}	0
PB	Gate junction potential	V	1
RD	Drain ohmic resistance	Ω	0
RS	Source ohmic resistance	Ω	0
TEMPMODEL	Specification to type of parameter interpolation over temperature (see User Guide section 5.3	–	NONE
THETA	Mobility modulation parameter (level 2)	V^{-1}	0

Parameter	Description	Units	Default
TNOM	Nominal device temperature	°C	27
VTO	Threshold voltage	V	-2

Table 2.22: JFET Model Parameters.

JFET Level selection

Xyce supports two JFET models. LEVEL=1, the default, is the SPICE 3f5 treatment. This model employs a doping profile parameter B. When B=1, the original SPICE square law is exactly implemented, and when B=0.6 the model is close to that of Shockley.

When LEVEL=2 is selected, the Shockley model is used with some additional physics effects: channel length modulation and the effect of gate electric field on mobility. An additional parameter, DELTA, is added to the LEVEL 2 model that allows the user to adjust the saturation voltage.

Metal-Semiconductor FET (MESFET)

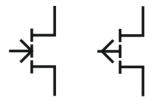
General Form

```
Z<name> < drain node> <gate node> <source node> <model name>
+ [area value] [device parameters]
```

Examples

```
Z1 2 3 0 MESMOD AREA=1.4
Z1 7 2 3 ZM1
```

Symbols



Model Form

```
.MODEL <model name> NMF [model parameters]
.MODEL <model name> PMF [model parameters]
```

Parameters and Options

`<drain node>`

Node connected to drain.

`<gate node>`

Node connected to gate.

`<source node>`

Node connected to source.

`<source node>`

Name of model defined in .MODEL line.

`[area value]`

The `MESFET` is modeled as an intrinsic FET using an ohmic resistance (`RD/area`) in series with the drain and another ohmic resistance (`RS/area`) in series with the source. `area` is an area factor with a default of `1`.

`[device parameters]`

Parameters listed in Table 2.23 may be provided as space separated `<parameter>=<value>` specifications as needed. Any number of parameters may be specified.

Comments

Although MESFETs can be made of Si, such devices are not as common as GaAs MESFETS. And since the mobility of electrons is much higher than holes in GaAs, nearly all commercial devices are n-type MESFETS.

Device Parameters

Table 2.23 gives the available device parameters for the MESFET.

Parameter	Description	Units	Default
AREA	device area	m^2	1
TEMP	Device temperature	°C	27

Table 2.23: MESFET Device Parameters.

Model Parameters

Table 2.24 gives the available model parameters for the MESFET.

Parameter	Description	Units	Default
AF	Flicker noise exponent	–	1
ALPHA	Saturation voltage parameter	V^{-1}	2
B	Doping tail parameter (level 1)	V^{-1}	0.3
BETA	Transconductance parameter	A/V^2	0.0025
CGD	Zero-bias gate-drain junction capacitance	F	0
CGS	Zero-bias gate-source junction capacitance	F	0
FC	Coefficient for forward-bias depletion capacitance	F	0.5
IS	Gate junction saturation current	A	1e-14
KF	Flicker noise coefficient	–	0.05
LAMBDA	Channel length modulation	V^{-1}	0
PB	Gate junction potential	V	1
RD	Drain ohmic resistance	Ω	0
RS	Source ohmic resistance	Ω	0
TEMPMODEL	Specification to type of parameter interpolation over temperature (see User Guide section 5.3	–	NONE
TNOM	Nominal device temperature	°C	27
VTO	Threshold voltage	V	0

Table 2.24: MESFET Model Parameters.

MESFET Level selection

Xyce supports two MESFET models. LEVEL=1, the default, is the SPICE 3f5 treatment. This model employs a doping profile parameter B. When B=1, the original SPICE square law is exactly implemented, and when B=0.6 the model is close to that of Shockley.

When LEVEL=2 is selected, the Shockley model is used with some additional physics effects: channel length modulation and the effect of gate electric field on mobility. An additional parameter, DELTA, is added to the LEVEL 2 model that allows the user to adjust the saturation voltage.

MOS Field Effect Transistor (MOSFET)

General Form

```
M<name> <drain node> <gate node> <source node>
+ <bulk/substrate node> <model name>
+ [L=<value>] [W=<value>]
+ [AD=<value>] [AS=<value>]
+ [PD=<value>] [PS=<value>]
+ [NRD=<value>] [NRS=<value>]
+ [M=<value] [IC=<value, ...>]
```

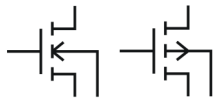
Special Form (BSIMSOI)

```
M<name> <drain node> <gate node> <source node>
+ <substrate node (E)>
+ [<External body contact (P)>]
+ [<internal body contact (B)>]
+ [<temperature node (T)>]
+ <model name>
+ [L=<value>] [W=<value>]
+ [AD=<value>] [AS=<value>]
+ [PD=<value>] [PS=<value>]
+ [NRD=<value>] [NRS=<value>] [NRB=<value>]
+ [BJTOFF=<value>]
+ [IC=<val>,<val>,<val>,<val>,<val>]
+ [RTH0=<val>] [CTH0=<val>]
+ [NBC=<val>] [NSEG=<val>] [PDBCP=<val>] [PSBCP=<val>]
+ [AGBCP=<val>] [AEBCP=<val>] [VBSUSR=<val>] [TNODEOUT]
+ [FRBODY=<val>] [M=<value]
```

Examples

```
M5 4 12 3 0 PNOM L=20u W=10u
M3 5 13 10 0 PSTRONG
M6 7 13 10 0 PSTRONG M=2
M8 10 12 100 100 NWEAK L=30u W=20u
+ AD=288p AS=288p PD=60u PS=60u NRD=14 NRS=24
```

Symbols



Model Form

```
.MODEL <model name> NMOS [model parameters]
.MODEL <model name> PMOS [model parameters]
```

Parameters and Options	`L` and `W`
	The MOSFET channel length and width that are decreased to get the actual channel length and width. They may be given in the device `.MODEL` or `.OPTIONS` statements. The value in the device statement overrides the value in the model statement, which overrides the value in the `.OPTIONS` statement. Defaults for `L` and `W` may be set in the `.OPTIONS` statement. If `L` or `W` values are not given, their default value is 100 u.
	`AD` and `AS`
	The drain and source diffusion areas. Defaults for `AD` and `AS` can be set in the `.OPTIONS` statement. If `AD` or `AS` defaults are not set, their default value is 0.
	`PD` and `PS`
	The drain and source diffusion perimeters. Their default value is 0.

Parameters and Options (cont.)

`NRD`, `NRS`

Multipliers (in units of squares) that can be multiplied by `RSH` to yield the parasitic (ohmic) resistances of the drain (`RD`) and source (`RS`), respectively. `NRD`, `NRS` default to 0.

Consider a square sheet of resistive material. Analysis shows that the resistance between two parallel edges of such a sheet depends upon its composition and thickness, but is independent of its size as long as it is square. In other words, the resistance will be the same whether the square's edge is 2 mm, 2 cm, or 2 m. For this reason, the sheet resistance of such a layer, abbreviated `RSH`, has units of ohms per square.

`M`

If specified, the value is used as a number of parallel MOSFETs to be simulated. For example, if `M`=2 is specified, we simulate two identical mosfets connected to the same nodes in parallel.

`IC`

The BSIM3 (model level 9) and BSIMSOI (model level 10) allow one to specify the initial voltage difference across nodes of the device during the DC operating point calculation. For the BSIM3 the syntax is `IC=` V_{ds}, V_{gs}, V_{bs} where V_{ds} is the voltage difference between the drain and source, V_{gs} is the voltage difference between the gate and source and V_{bs} is the voltage difference between the body and source. The BSIMSOI device's initial condition syntax is `IC=` $V_{ds}, V_{gs}, V_{bs}, V_{es}, V_{ps}$ where the two extra terms are the voltage difference between the substrate and source, and the external body and source nodes respectively. Note that for any of these lists of voltage differences, fewer than the full number of options may be specified. For example, `IC=5.0` specifies an initial condition on V_{ds} but does not specifiy any initial conditions on the other nodes. Therefore, one cannot specify V_{gs} without specifying V_{ds}, etc. It is illegal to specify initial conditions on any nodes that are tied together. Xyce attemps to catch such errors, but complex circuits may stymie this error trap.

BSIMSOI-specific Options

There are a large number of extra instance parameters and optional nodes available for the BSIMSOI (level 10) MOSFET.

`substrate node`

The fourth node of the BSIMSOI device is always the substrate node, which is referred to as the `E` node.

`external body contact node`

If given, the fifth node is the external body contact node, `P`. It is connected to the internal body node through a body tie resistor. If `P` is not given, the internal body node is not accessible from the netlist and floats.

If there are only five nodes specified and `T`NODEOUT is also specified, the fifth node is the temperature node instead.

`internal body contact node`

If given, the sixth node is the internal body contact node, `B`. It is connected to the external body node through a body tie resistor. If `B` is not given and `P` is given, the internal body node is not accessible from the netlist, but is still tied to the external body contact through the tie resistance.

If there are only six nodes specified and `T`NODEOUT is also specified, the sixth node is the temperature node instead.

`temperature node`

If the parameter `T`NODEOUT is specified, the final node (fifth, sixth, or seventh) is interpreted as a temperature node. The temperature node is intended for thermal coupling simulation.

`BJTOFF`

Turns off the parasitic BJT currents.

`IC`

The `I`C parameter allows specification of the five junction initial conditions, VDS, VGS, CBS, VES and VPS. VPS is ignored in a four-terminal device.

BSIMSOI-specific Options (cont.)	`RTH0`
	Thermal resistance per unit width. Taken from model card if not given.
	`CTH0`
	Thermal capacitance per unit width. Taken from model card if not given.
	`NBC`
	Number of body contact isolation edge.
	`NSEG`
	Number of segments for channel width partitioning.
	`PDBCP`
	Parasitic perimeter length for body contact at drain side.
	`PSBCP`
	Parasitic perimeter length for body contact at source side.
	`AGBCP`
	Parasitic gate-to-body overlap area for body contact.
	`AEBCP`
	Parasitic body-to-substrate overlap area for body contact.
	`VBSUSR`
	Optional initial value of VBS specified by user for use in transient analysis. (currently unused in Xyce).
	`FRBODY`
	Layout-dependent body resistance coefficient.

Comments	The simulator provides three MOSFET device models, which differ in the formulation of the I-V characteristic. The `LEVEL` parameter selects among different models as shown below.

MOSFET Operating Temperature

Model parameters may be assigned unique measurement temperatures using the **TNOM** model parameter. See the MOSFET model parameters for more information.

Model Parameters

Table 2.25 gives the available model parameters for the MOSFET.

All MOSFET models

The parameters shared by all MOSFET model levels are principally parasitic element values (e.g., series resistance, overlap capacitance, etc.).

Model levels 1, and 3

The DC behaviors of the level 1 and 3 MOSFET models are defined by the parameters $\mathbf{VTO}$, $\mathbf{KP}$, $\mathbf{LAMBDA}$, $\mathbf{PHI}$, and $\mathbf{GAMMA}$. The simulator calculates these if the process parameters (e.g., $\mathbf{TOX}$, and $\mathbf{NSUB}$) are specified, but these are always overridden by any user-defined values. The $\mathbf{VTO}$ value is positive (negative) for modeling the enhancement mode and negative (positive) for the depletion mode of N-channel (P-channel) devices.

For MOSFETs, the capacitance model enforces charge conservation, influencing just the Level 1 and 3 models.

Effective device parameter lengths and widths are calculated as follows:

$$P_i = P_0 + P_L/L_e + P_W/W_e$$

where

$$\begin{array}{rcl} L_e & = & \text{effective length} \quad = \quad \mathbf{L} - (2 \cdot \mathbf{LD}) \\ W_e & = & \text{effective width} \quad = \quad \mathbf{W} - (2 \cdot \mathbf{WD}) \end{array}$$

See `.MODEL` (model definition) for more information.

Model level 9 (BSIM3 version 3.2.2)

The University of California, Berkeley BSIM3 model is a physical-based model with a large number of dependencies on essential dimensional and processing parameters. It incorporates the key effects that are critical in modeling deep-submicrometer MOSFETs. These include threshold voltage reduction, nonuniform doping, mobility reduction due to the vertical field, bulk charge effect, carrier velocity saturation, drain-induced barrier lowering (DIBL), channel length modulation (CLM), hot-carrier-induced output resistance reduction, subthreshold conduction, source/drain parasitic resistance, substrate current induced body effect (SCBE) and drain voltage reduction in LDD structure.

The BSIM3 Version 3.2.2 model is a deep submicron MOSFET model with several major enhancements (over earlier versions). These include a single I-V formula used to define the current and output conductance for operating regions, improved narrow width device modeling, a superior capacitance model with improved short and narrow geometry models, a new relaxation-time model to better transient modeling and enhanced model fitting of

assorted W/L ratios using a single parameter set. This version preserves the large number of integrated dependencies on dimensional and processing parameters of the Version 2 model. For further information, see Reference [12].

Additional notes

1. If any of the following BSIM3 3.2.2 model parameters are not specified, they are computed via the following:

   If $\mathbf{VTHO}$ is not specified, then:

$$\mathbf{VTHO} = \mathbf{VFB} + \phi_s \mathbf{K1}\sqrt{\phi_s}$$

   where:

$$\mathbf{VFB} = -1.0$$

   If $\mathbf{VTHO}$ is given, then:

$$\begin{aligned}
\mathbf{VFB} &= \mathbf{VTHO} - \phi_s + \mathbf{K1}\sqrt{phi_s} \\
\mathbf{VBX} &= \phi_s - \frac{q \cdot \mathbf{NCH} \cdot \mathbf{XT}^2}{2\varepsilon_{si}} \\
\mathbf{CF} &= \left(\frac{2\varepsilon_{ox}}{\pi}\right) \ln\left(1 + \frac{1}{4 \times 10^7 \cdot \mathbf{TOX}}\right)
\end{aligned}$$

   where:

$$E_g(T) = \text{the energy bandgap at temperature } T = 1.16 - \frac{T^2}{7.02 \times 10^4 (T + 1108)}$$

2. If $\mathbf{K1}$ and $\mathbf{K2}$ are not given then they are computed via the following:

$$\begin{aligned}
\mathbf{K1} &= \mathbf{GAMMA2} - 2 \cdot \mathbf{K2}\sqrt{\phi_s - \mathbf{VBM}} \\
\mathbf{K2} &= \frac{(\mathbf{GAMMA1} - \mathbf{GAMMA2})(\sqrt{\phi_s - \mathbf{VBX}} - \sqrt{\phi_s})}{2\sqrt{\phi_s}(\sqrt{\phi_s - \mathbf{VBM}} - \sqrt{\phi_s}) + \mathbf{VBM}}
\end{aligned}$$

   where:

$$\begin{aligned}
\phi_s &= 2V_t \ln\left(\frac{\mathbf{NCH}}{n_i}\right) \\
V_t &= kT/q \\
n_i &= 1.45 \times 10^{10} \left(\frac{T}{300.15}\right)^{1.5} \exp\left(21.5565981 - \frac{E_g(T)}{2V_t}\right)
\end{aligned}$$

3. If $\mathbf{NCH}$ is not specified and $\mathbf{GAMMA1}$ is, then:

$$\mathbf{NCH} = \frac{\mathbf{GAMMA1^2} \times \mathbf{COX^2}}{2q\varepsilon_{si}}$$

If $\mathbf{GAMMA1}$ and $\mathbf{NCH}$ *are not* specified, then $\mathbf{NCH}$ defaults to $1.7 \times 10^{23}\ m^{-3}$ and $\mathbf{GAMMA1}$ is computed using $\mathbf{NCH}$:

$$\mathbf{GAMMA1} = \frac{\sqrt{2q\varepsilon_{si} \cdot \mathbf{NCH}}}{\mathbf{COX}}$$

If $\mathbf{GAMMA2}$ is not specified, then:

$$\mathbf{GAMMA2} = \frac{\sqrt{2q\varepsilon_{si} \cdot \mathbf{NSUB}}}{\mathbf{COX}}$$

4. If $\mathbf{CGSO}$ is not specified and $\mathbf{DLC} > 0$, then:

$$\mathbf{CGSO} = \begin{cases} 0, & ((\mathbf{DLC} \cdot \mathbf{COX}) - \mathbf{CGSL}) < 0 \\ 0.6 \cdot \mathbf{XJ} \cdot \mathbf{COX}, & ((\mathbf{DLC} \cdot \mathbf{COX}) - \mathbf{CGSL}) \geq 0 \end{cases}$$

5. If $\mathbf{CGDO}$ is not specified and $\mathbf{DLC} > 0$, then:

$$\mathbf{CGDO} = \begin{cases} 0, & ((\mathbf{DLC} \cdot \mathbf{COX}) - \mathbf{CGSL}) < 0 \\ 0.6 \cdot \mathbf{XJ} \cdot \mathbf{COX}, & ((\mathbf{DLC} \cdot \mathbf{COX}) - \mathbf{CGSL}) \geq 0 \end{cases}$$

Model level 10 (BSIMSOI version 3.2)

The BSIMSOI is an international standard model for SOI (silicon on insulator) circuit design and is formulated on top of the BSIM3v3 framework. A detailed description can be found in the BSIMSOI 3.1 Users' Manual [13] and the BSIMSOI 3.2 release notes [14].

This version (v3.2) of the BSIMSOI includes three depletion models; the partially depleted BSIMSOI PD (soiMod=0), the fully depleted BSIMSOI FD (soiMod=2), and the unified SOI model (soiMod=1).

BSIMPD is the Partial-Depletion (PD) mode of the BSIMSOI. A typical PD SOI MOSFET is formed on a thin SOI film which is layered on top of a buried oxide. BSIMPD has the following features and enhancements:

- Real floating body simulation of both I-V and C-V. The body potential is determined by the balance of all body current components.
- An improved parasitic bipolar current model. This includes enhancements in the various diode leakage components, second order effects (high-level injection and Early effect), diffusion charge equation, and temperature dependence of the diode juncion capacitance.
- An improved impact-ionization current model. The contribution from BJT current is also modeled by the parameter Fbjtii.
- A gate-to-body tunneling current model, which is important to thin-oxide SOI technologies.

- Enhancements in the threshold voltage and bulk charge formulation of the high positive body bias regime.
- Instance parameters (Pdbcp, Psbcp, Agbcp, Aebcp, Nbc) are provided to model the parasitics of devices with various body-contact and isolation structures.
- An external body node (the 6th node) and other improvements are introduced to facilitate the modeling of distributed body resistance.
- Self heating. An external temperature node (the 7th node) is supported to facilitate the simulation of thermal coupling among neighboring devices.
- A unique SOI low frequency noise model, including a new excess noise resulting from the floating body effect.
- Width dependence of the body effect is modeled by parameters (K1,K1w1,K1w2).
- Improved history dependence of the body charges with two new parameters (Fbody, DLCB).
- An instance parameter Vbsusr is provided for users to set the transient initial condition of the body potential.
- The new charge-thickness capacitance model introduced in BSIM3v3.2, capMod=3, is included.

The following table gives the parameters for the MOSFET, levels 1 through 10.

Model parameters	Description	Units	Default
	All Levels		
AF	Flicker Noise Exponent		1.0
CBD	Zero-bias Bulk-drain p-n Capacitance	farad (F)	0.0
CBS	Zero-bias Bulk-source p-n Capacitance	F	0.0
CGBO	Gate-bulk Overlap Capacitance/Channel Length	F	0.0
CGDO	Gate-drain Overlap Capacitance/Channel Width	F	0.0
CGSO	Gate-source Overlap Capacitance/Channel Width	F	0.0
CJ	Bulk p-n Zero-bias Bottom Capacitance/Area	F/m^2	0.0
CJSW	Bulk p-n Zero-bias Sidewall Capacitance/Area	F/m^2	0.0
FC	Bulk p-n Forward-bias Capacitance Coefficient		0.5
IS	Bulk p-n Saturation Current	amp	1E-14

Model parameters	Description	Units	Default
JS	Bulk p-n Saturation Current/Area	$\mathrm{amp/m^2}$	0.0
KF	Flicker Noise Coefficient		0.0
L	Channel Length	m	**DEFL**
LEVEL	Model Index		**1**
MJ	Bulk p-n Bottom Grading Coefficient		0.5
MJSW	Bulk p-n Sidewall Grading Coefficient		0.33
PB	Bulk p-n Bottom Potential	volt	0.8
RSH	Drain, Source Diffusion Sheet Resistance	ohm	0.0
TT	Bulk p-n Transit Time	second (s)	0.0
TNOM	Parameter Measurement Temperature	°C	27.0
W	Channel Width	m	**DEFW**
	Levels 1and 3		
DELTA	Width Effect on Threshold		0.0
ETA	Static Feedback (Level 3)		0.0
GAMMA	Bulk Threshold Parameter	$\mathrm{volt\ (V)^{1/2}}$	
KP	Transconductance Coefficient	$\mathrm{amp/V^2}$	2.0E-5
KAPPA	Saturation Field Factor (Level 3)		0.2
LAMBDA	Channel-length Modulation (Levels 1)	$\mathrm{V^{-1}}$	0.0
LD	Lateral Diffusion (Length)	m	0.0
NFS	Fast Surface State Density	$\mathrm{cm^{-2}}$	0.0
NSS	Surface State Density	$\mathrm{cm^{-2}}$	
NSUB	Substrate Doping Density	$\mathrm{cm^{-3}}$	0.0
PHI	Surface Potential	V	0.6
RD	Drain Ohmic Resistance	ohm	0.0
RS	Source Ohmic Resistance	ohm	0.0
THETA	Mobility Modulation (Level 3)	$\mathrm{V^{-1}}$	0.0
TOX	Oxide Thickness	m	
TPG	Gate Material Type: $+1$ = opposite of substrate -1 = same as substrate 0 = aluminum		+1
UTRA	(Not Used) Mobility Degradation Transverse Field Coefficient		0.0
UO	Surface Mobility	$\mathrm{cm^{-2}/(V \cdot s)}$	600

Model parameters	Description	Units	Default
VMAX	Maximum Drift Velocity	m/s	0.0
VTO	Zero-bias Threshold Voltage	V	0.0
WD	Lateral Diffusion (Width)	m	0.0
XJ	Metallurgical Junction Depth (Level 3)	m	0.0
XQC	Fraction of Channel Charge Attributed to Drain		1.0
Level 9: Control Parameters			
CAPMOD	Flag for the Short-channel Capacitance Model		2.0
MOBMOD	Mobility Model Selector		1
NOIMOD	Flag for Noise Model		1
NQSMOD	Flag for NQS Model		0
PARAMCHK	Flag for Model Parameter Checking		0
Level 9: Capacitance Parameters			
CF	Fringing Field Capacitance	F/m	
CKAPPA	Coefficient for Lightly Doped Region Overlap Capacitance Fringing Field Capacitance	F/m	0.6
CLC	Constant Term for the Short-Channel Model	m	0.1E-6
CLE	Exponential Term for the Short-Channel Model		0.6
CGBO	Gate-bulk Overlap Capacitance per Unit Channel Length	F/m	0.0
CGDL	Light-doped Drain-gate Region Overlap Capacitance	F/m	0.0
Level 9: Capacitance Parameters (cont.)			
CGDO	Non-LDD Region Drain-gate Overlap Capacitance per Unit Channel Length	F/m	
CGSL	Light-doped Source-gate Region Overlap Capacitance	F/m	0.0
CGSO	Non-LDD Region Source-gate Overlap Capacitance per Unit Channel Length	F/m	
CJ	Bottom Junction Capacitance per Unit Area	F/m^2	5.0E-4
CJSW	Source/Drain Side Junction Capacitance per Unit Periphery	F/m	5.0E-10
CJSWG	Source/Drain Gate Sidewall Junction Capacitance per Unit Width	F/m	**CJSW**
DLC	Length Offset Fitting Parameter from C-V	m	**LINT**

Model parameters	Description	Units	Default
DWC	Width Offset Fitting Parameter from C-V	m	**WINT**
MJ	Bottom Junction Capacitance Grading Coefficient		0.5
MJSW	Source/Drain Side Junction Capacitance Grading Coefficient		0.33
MJSWG	Source/Drain Gate Sidewall Junction Capacitance Grading Coefficient		**MJSW**
PB	Bottom Built-in Potential	V	1.0
PBSW	Source/Drain Side Junction Built-in Potential	V	1.0
PBSWG	Source/Drain Gate Sidewall Junction Built-in Potential	V	**PBSW**
VFBCV	Flat-band Voltage Parameter (for **CAPMOD** = 0 only)	V	-1.0
XPART	Charge Partitioning Rate Flag		0.0
Level 9: Bin Description Parameters			
BINUNIT	Bin Unit Scale Selector		1.0
LMAX	Maximum Channel Length	m	1.0
LMIN	Minimum Channel Length	m	0.0
WMAX	Maximum Channel Width	m	1.0
WMIN	Minimum Channel Width	m	0.0
Level 9: DC Parameters			
A0	Bulk Charge Effect Coefficient for Channel Length		1.0
A1	First Non-saturation Effect Parameter	V^{-1}	0.0
A2	Second Non-saturation Factor		1.0
AGS	Gate-bias Coefficient of Abulk	V^{-1}	0.0
ALPHA0	First Parameter of Impact-ionization Current	m/V	0.0
B0	Bulk Charge Effect Coefficient for Channel Width	m	0.0
B1	Bulk Charge Effect Width Offset	m	0.0
BETA0	Second Parameter of Impact-ionization Current	V	30.0
CDSC	Drain/Source to Channel Coupling Capacitance	F/m^2	2.4E-4
CDSCB	Body-bias Sensitivity of **CDSC**	F/Vm^2	0.0
CDSCD	Drain-bias Sensitivity of **CDSC**	F/Vm^2	0.0

Model parameters	Description	Units	Default
CIT	Interface Trap Capacitance	F/m^2	0.0
DELTA	Effective **Vds** Parameter	V	0.01
DROUT	L-dependence Coefficient of the **DIBL** Correction Parameter in **Rout**		0.56
DSUB	**DIBL** Coefficient Exponent in Subthreshold Region		**DROUT**
DVT0	First Coefficient of Short-channel Effect on Threshold Voltage		2.2
DVT0W	First Coefficient of Narrow-width Effect on Threshold Voltage for Small-channel Length	m^{-1}	0.0
DVT1	Second Coefficient of Short-channel Effect on Threshold Voltage		0.53
DVT2	Body-bias Coefficient of Short-channel Effect on Threshold Voltage	V^{-1}	-0.032
DVTW1	Second Coefficient of Narrow-channel Effect on Threshold Voltage for Small Channel Length	m^{-1}	5.3E6
DVTW2	Body-bias Coefficient of Narrow-width Effect for Small Channel Length	V^{-1}	-0.032
DWB	Coefficient of Substrate Body Bias Dependence of **Weff**	$m/V^{1/2}$	0.0
DWG	Coefficient of Gate Dependence of **Weff**	m/V	0.0
ETA0	**DIBL** Coefficient in Subthreshold Region		0.08
ETAB	Body-bias Coefficient for the Subthreshold **DIBL** Effect	V^{-1}	-0.07
JS	Source-drain Junction Saturation Current per Unit Area	amp/m^2	1.0E-4
JSW	Sidewall Saturation Current per Unit Length	amp/m	0.0
K1	First-order Body Effect Coefficient	$V^{1/2}$	0.5
K2	Second-order Body Effect Coefficient		0.0
K3	Narrow Width Coefficient		80.0
K3B	Body Effect Coefficient of **K3**	V^{-1}	0.0
KETA	Body-bias Coefficient of Bulk Charge Effect	V^{-1}	-0.047
LINT	Length Offset Fitting Parameter from I-V Without Bias	m	0.0
NFACTOR	Subthreshold Swing Factor		1.0
NGATE	Poly Gate Doping Concentration	cm^{-3}	0.0

Model parameters	Description	Units	Default
NLX	Lateral Non-uniform Doping Parameter	m	1.74E-7
PCLM	Channel Length Modulation Parameter		1.3
PDIBLC1	First Output Resistance **DIBL** Effect Correction Parameter		0.39
PDIBLC2	Second Output Resistance **DIBL** Effect Correction Parameter		0.0086
PDIBLCB	Body Effect Coefficient of **DIBL** Correction Parameter	V^{-1}	0.0
PRWB	Body Effect Coefficient of **RDSW**	$V^{-1/2}$	0.0
PRWG	Gate-bias Effect Coefficient of **RDSW**	V^{-1}	0.0
PSCBE1	First Substrate Current Body Effect Parameter	V/m	4.24E8
PSCBE2	Second Substrate Current Body Effect Parameter	V/m	1.0E-5
PVAG	Gate Dependence of Early Voltage		0.0
RDSW	Parasitic Resistance per Unit Width	ohm-μm^{WR}	0.0
RSH	Source-drain Sheet Resistance	ohm/ square?	0.0
UO	Mobility at Temp = **TNOM** **NMOS** **PMOS**	$cm^2/V \cdot s$	670.0 250.0
UA	First-order Mobility Degradation Coefficient	m/V	2.25E-9
UB	Second-order Mobility Degradation Coefficient	$(m/V)^2$	5.87E-19
UC	Body Effect of Mobility Degradation Coefficient **MOBMOD** = 1 **MOBMOD** = 3	m/V^2 $1/V$	-4.65E-11 -0.046
VBM	Maximum Applied Body-bias in Threshold Voltage Calculation	V	-3.0
VOFF	Offset Voltage in the Subthreshold Region at Large W and L	V	-0.08
VSAT	Saturation Velocity at Temp = **TNOM**	m/s	8.0E4
VTH0	Threshold Voltage at **Vbs** = 0 for Large **L**	V	0.7 (**NMOS**) -0.7 (**PMOS**)
W0	Narrow-width Parameter	m	2.5E-6
WINT	Width-offset Fitting Parameter from I-V Without Bias	m	0.0
WR	Width-offset from Weff for **Rds** Calculation		1.0
Level 9: Flicker Noise Parameters			
AF	Frequency Exponent		1.0

Model parameters	Description	Units	Default
EF	Flicker Exponent		1.0
EM	Saturation Field	$\mathrm{V/m}$	4.1E7
KF	Flicker Noise Parameter		0.0
NOIA	Noise Parameter A **NMOS** **PMOS**		1.0E20 9.9E18
NOIB	Noise Parameter B **NMOS** **PMOS**		5.0E4 2.4E3
NOIC	Noise Parameter C **NMOS** **PMOS**		-1.4E-12 1.4E-12
Level 9: NQS Parameter			
ELM	Elmore Constant of the Channel		5.0
Level 9: Process Parameters			
GAMMA1	Body Effect Coefficient Near the Surface	$\mathrm{V}^{1/2}$	
GAMMA2	Body Effect Coefficient in the Bulk	$\mathrm{V}^{1/2}$	
NCH	Channel Doping Concentration	cm^{-3}	1.7E17
NSUB	Substrate Doping Concentration	cm^{-3}	6.0E16
TOX	Gate-oxide Thickness	m	1.5E-8
VBX	**Vbs** at Which the Depletion Region = **XT**	V	
XJ	Junction Depth	m	1.5E-7
XT	Doping Depth	m	1.55E-7
Level 9: Temperature Parameters			
AT	Temperature Coefficient for Saturation Velocity	$\mathrm{m/s}$	3.3E4
KT1	Temperature Coefficient for Threshold Voltage	V	-0.11
KT1L	Channel Length Dependence of the Temperature Coefficient for Threshold Voltage	$\mathrm{V \cdot m}$	0.0
KT2	Body-bias Coefficient of Threshold Voltage Temperature Effect		0.022
NJ	Emission Coefficient of Junction		1.0
PRT	Temperature Coefficient for **RDSW**	$\mathrm{ohm\text{-}\mu m}$	0.0
TNOM	Temperature at which Parameters are Extracted	$^\circ\mathrm{C}$	27.0
UA1	Temperature Coefficient for **UA**	$\mathrm{m/V}$	4.31E-9
UB1	Temperature Coefficient for **UB**	$(\mathrm{m/V})^2$	-7.61E-18
UC1	Temperature Coefficient for **UC** **MOBMOD** = 1 or 2 **MOBMOD** = 3	$\mathrm{m/V^2}$ $1/\mathrm{V}$	-5.6E-11 -0.056

Model parameters	Description	Units	Default
UTE	Mobility Temperature Exponent		-1.5
XT1	Junction Current Temperature Exponent Coefficient		3.0
Level 9: W and L Parameters			
LL	Coefficient of Length Dependence for Length Offset	m^{LLN}	0.0
LLN	Power of Length Dependence for Length Offset		1.0
LW	Coefficient of Width Dependence for Length Offset	m^{LWN}	0.0
LWL	Coefficient of Length and Width Cross Term for Length Offset	$m^{LWN+LLN}$	0.0
LWN	Power of Width Dependence for Length Offset		1.0
WL	Coefficient of Length Dependence for Width Offset	m^{WLN}	0.0
WW	Coefficient of Width Dependence for Width Offset	m^{WWN}	0.0
WWL	Coefficient of Length and Width Cross Term for Width Offset	$m^{WWN+WLN}$	0.0
WWN	Power of Width Dependence of Width Offset		1.0

Table 2.25: MOSFET Model Parameters.

Model parameters	Description	Units	Default
Level 10: Built-in Potential Lowering (ΔV_{bi}) Parameters			
SOIMOD	SOI model selector. SOIMOD=0 BSIMPD SOIMOD=1 unified model for PD & FD SOIMOD=2 ideal FD SOIMOD=3 auto selection by BSIMSOI	-	0
VBSA	Offset voltage due to non-idealities	V	0
VBSOPD	Upper bound of built-in potential lowering for BSIMPD operation	V	0.0
VBSOFD	Lowering bound of built-in potential lowering for ideal FD operation	V	0.5
FNOIMOD	Flicker noise model selector	-	1
TNOIMOD	Thermal noise model selector	-	0
NTNOI	Noise factor for short-channel devices for TNOIMOD=0 only	-	1.0

Model parameters	Description	Units	Default
TNOIA	Coefficient of channel-lenght dependence of total channel thermal noise	-	1.5
TNOIB	Channel-length dependence parameter for channel thermal noise partitioning	-	3.5
RNOIA	Thermal noise parameter	-	0.577
RNOIB	Thermal noise parameter	-	0.37
NOFF	CV parameter for $V_{gsteff,cv}$	-	1.0
NOFFFD	Smoothing parameter in FD module	-	1
VOFFFD	Smoothing parameter in FD module	V	0
K1B	First backgate body effect parameter	-	1
K2B	Second backgate body effect parameter for short channel effect	-	0
DK2B	Third backgate body effect parameter for short channel effect	-	0
DVBD0	First short channel effect parameter in FD module	-	0
DVBD1	Second short channel effect parameter in FD module	-	0
MOINFD	Gate bias dependence coefficient of surface potential in FD module	-	1e3
Level 10: Model Control Parameters			
SHMOD	Flag for self-heating 0: no self-heating, 1: self-heating	-	0
MOBMOD	Mobility model selector	-	1
CAPMOD	Flag for the short channel capacitance model	-	2 note[1]
NOIMOD	Flag for Noise model	-	1
Level 10: Process Parameters			
TSI	Silicon film thickness	m	1e-7
TBOX	Buried oxide thickness	m	3e-7
TOX	Gate oxide thickness	m	1e-8
TOXM	Gate oxide thickness used in extraction	m	TOX
XJ	S/D junction depth	m	TSI[2]
NCH	Channel doping concentration	$1/cm^3$	1.7e17

[1] BSIMSOI supports CAPMOD=2 and 3 only. CAPMOD=0 and 1 are not supported.

[2] In modern SOI technology, source/drain extension or LDD are commonly used. As a result, the source/drain junction depth (XJ) can be different from the silicon film thickness (TSI). By default, if XJ is not given, it is set to TSI. XJ is not allowed to be greater than TSI.

Model parameters	Description	Units	Default
NSUB	Substrate doping concentration	$1/cm^3$	6e16 note[3]
NGATE	poly gate doping concentration	$1/cm^3$	0
	Level 10: DC Parameters		
VTH0	Threshold voltage @Vbs=0 for long and wide device	-	0.7
K1	First order body effect coefficient $V^{1/2}$	0.6	
K1W1	First body effect width dependent parameter	m	0
K1W2	Second body effect width dependent parameter	m	0
K2	Second order body effect coefficient	-	0
K3	Narrow width coefficient	-	0
K3B	Body effect coefficient of k3	1/V	0
KB1	Backgate body charge coefficient	-	1
W0	Narrow width parameter	m	0
NLX	Lateral non-uniform doping parameter	m	1.74e-7
DVT0	first coefficient of short-channel effect on Vth	-	2.2
DVT1	Second coefficient of short-channel effect on Vth	-	0.53
DVT2	Body-bias coefficient of short-channel effect on Vth	1/V	-0.032
DVT0W	first coefficient of narrow width effect on Vth for small channel length	-	0
DVT1W	Second coefficient of narrow width effect on Vth for small channel length	-	5.3e6
DVT2W	Body-bias coefficient of narrow width effect on Vth for small channel length	1/V	-0.032
U0	Mobility at Temp = Tnom NMOSFET PMOSFET	$cm^2/(V-sec)$	670 / 250
UA	First-order mobility degradation coefficient	m/V	2.25e-9
UB	Second-order mobility degradation coefficient	$(m/V)^2$	5.9e-19
UC	Body-effect of mobility degradation coefficient	1/V	-.0465

[3]BSIMSOI refers substrate to the silicon below buried oxide, not the well region in BSIM3. It is used to calculate backgate flatband voltage (V_{fbb}) and parameters related to source/drain diffusion bottom capacitance (VSDTH, VSDFB, CSDMIN). Positive NSUB means the same type of doping as the body and negative nsub means opposite type of doping.

Model parameters	Description	Units	Default
VSAT	Saturation velocity at Temp=Tnom	m/sec	8e4
A0	Bulk charge effect coefficient for channel length	-	1.0
AGS	Gate bias coefficient of Abulk	1/V	0.0
B0	Bulk charge effect coefficient for channel width	m	0.0
B1	Bulk charge effect width offset	m	0.0
KETA	Body-bias coefficient of bulk charge effect	V^{-1}	0
KETAS	Surface potential adjustment for bulk charge effect	V	0
A1	First non-saturation effect parameter	1/V	0.0
A2	Second non-saturation effect parameter	0	1.0
RDSW	Parasitic resistance per unit width	$\Omega - \mu m^{Wr}$	100
PRWB	Body effect coefficient of Rdsw	1/V	0
PRWG	Gate bias effect coefficient of Rdsw	$(1/V)^{1/2}$	0
WR	Width offset from Weff for Rds calculation	-	1
NFACTOR	Subthreshold swing factor	-	1
WINT	Width offset fitting parameter from I-V without bias	m	0.0
LINT	Length offset fitting parameter from I-V without bias	m	0.0
DWG	Coefficient of Weff s gate dependence	m/V	0.0
DWB	Coefficient of Weff s substrate body bias dependence	$(m/V)^{1/2}$	0.0
DWBC	Width offset for body contact isolation edge	m	0.0
VOFF	Offset voltage in the subthreshold region for large W and L	V	-0.08
ETA0	DIBL coefficient in subthreshold region	-	0.08
ETAB	Body-bias coefficient for the subthreshold DIBL effect	1/V	-0.07
DSUB	DIBL coefficient exponent	-	0.56
CIT	Interface trap capacitance	F/m2	0.0
CDSC	Drain/Source to channel coupling capacitance	F/m^2	2.4e-4
CDSCB	Body-bias sensitivty of Cdsc	F/m^2	0
CDSCD	Drain-bias sensitivty of Cdsc	F/m^2	0
PCLM	Channel length modulation parameter	-	1.3

Model parameters	Description	Units	Default
PDIBL1	First output resistance DIBL effect correction parameter	-	.39
PDIBL2	Second output resistance DIBL effect correction parameter	-	0.086
DROUT	L dependence coefficient of the DIBL correction parameter in Rout	-	0.56
PVAG	Gate dependence of Early voltage	-	0.0
DELTA	Effective Vds parameter	-	0.01
ALPHA0	The first parameter of impact ionization current	m/V	0.0
FBJTII	Fraction of bipolar current affecting the impact ionization	-	0.0
BETA0	First Vds dependent parameter of impact ionization current	V^{-1}	0
BETA1	Second Vds dependent parameter of impact ionization current	-	0
BETA2	Third Vds dependent parameter of impact ionization current	V	0.1
VDSATII0	Nominal drain saturation voltage at threshold for impact ionization current	V	0.9
TII	Temperature dependent parameter for impact ionization current	-	0
LII	Channel length dependent parameter at threshold for impact ionization current	-	0
ESATII	Saturation channel electric field for impact ionization current	V/m	1e7
SII0	First Vgs dependent parameter for impact ionization current	V^{-1}	0.5
SII1	Second Vgs dependent parameter for impact ionization current	V^{-1}	0.1
SII2	Third Vgs dependent parameter for impact ionization current	-	0
SIID	Vds dependent parameter of drain saturation voltage for impact ionization current	V^{-1}	0
AGIDL	GIDL constant	Ω^{-1}	0.0
BGIDL	GIDL exponential coefficient	V/m	0.0
NGIDL	GIDL Vds enhancement coefficient	V	1.2
NTUN	Reverse tunneling non-ideality factor	-	10.0

Model parameters	Description	Units	Default
NDIO	Diode non-ideality factor	-	1.0
NRECFO	Recombination non-ideality factor at forward bias	-	2.0
NRECRO	Recombination non-ideality factor at reversed bias	-	10
ISBJT	BJT injection saturation current	A/m^2	1e-6
ISDIF	Body to source/drain injection saturation current	A/m^2	1e-7
ISREC	Recombination in depletion saturation current	A/m^2	1e-5
ISTUN	Reverse tunneling saturation current	A/m^2	0.0
LN	Electron/hole diffusion length	m	2e-6
VRECO	Voltage dependent parameter for recombination current	V	0
VTUNO	Voltage dependent parameter for tunneling current	V	0
NBJT	Power coefficient of channel length dependency for bipolar current	-	1
LBJTO	Reference channel length for bipolar current	m	0.20e-6
VABJT	Early voltage for bipolar current	V	10
AELY	Channel length dependency of early voltage for bipolar current	V/m	0
AHLI	High level injection parameter for bipolar current	-	0
RBODY	Intrinsic body contact sheet resistance	ohm/square	0.0
RBSH	Extrinsic body contact sheet resistance	ohm/square	0.0
RSH	Source drain sheet resistance in ohm per square	ohm/square	0.0
RHALO	Body halo sheet resistance	ohm/m	1e15
Level 10: Gate-to-body tunneling parameters			
IGMOD	Gate current model selector	-	0
TOXQM	Oxide thickness for Igb calculation	m	TOX
NTOX	Power term of gate current	-	1
TOXREF	Target oxide thickness	m	2.5e-9
EBG	Effective bandgap in gate current calculation	V	1.2

Model parameters	Description	Units	Default
ALPHAGB1	First Vox dependent parameter for gate current in inversion	1/V	.35
BETAGB1	Second Vox dependent parameter for gate current in inversion	$1/V^2$	.03
VGB1	Third Vox dependent parameter for gate current in inversion	V	300
VEVB	Vaux parameter for valence band electron tunneling	-	0.075
ALPHAGB2	First Vox dependent parameter for gate current in accumulation	1/V	.43
BETAGB2	Second Vox dependent parameter for gate current in accumulation	$1/V^2$	.05
VGB2	ThirdVox dependent parameter for gate current in accumulation	V	17
VECB	Vaux parameter for conduction band electron tunneling	-	.026
Level 10: AC and Capacitance Parameters			
XPART	Charge partitioning rate flag	-	0
CGSO	Non LDD region source-gate overlap capacitance per channel length	F/m	calculated[4]
CGDO	Non LDD region drain-gate overlap capacitance per channel length	F/m	calculated[5]
CGEO	Gate substrate overlap capacitance per unit channel length	F/m	0.0
CJSWG	Source/Drain (gate side) sidewall junction capacitance per unit width (normalized to 100nm Tsi)	F/m^2	1e-10
PBSWG	Source/Drain (gate side) sidewall junction capacitance buit in potential	V	.7
MJSWG	Source/Drain (gate side) sidewall junction capacitance grading coefficient	V	0.5
TT	Diffusion capacitance transit time coefficient	second	1e-12
NDIF	Power coefficient of channel length dependency for diffusion capacitance	-	-1

[4] If CGSO is not given then it is calculated using:
if DLC is given and is greater 0 then, CGSO $=$ p1 $=$ DLC $\cdot$ cox $-$ cgs1.
if the previously calculated CGSO < 0, then CGSO = 0
else CGSO $=$ 0.6 $\cdot$ TSI $\cdot$ cox.

[5] CGDO is calculated in a way similar to CSDO

Model parameters	Description	Units	Default
LDIFO	Channel-length dependency coefficient of diffusion cap.	-	1
VSDFB	Source/drain bottom diffusion capacitance flatband voltage	V	calculated[6]
VSDTH	Source/drain bottom diffusion capacitance threshold voltage	V	calculated[7]
CSDMIN	Source/drain bottom diffusion minimum capacitance	V	calculated[8]
ASD	Source/drain bottom diffusion smoothing parameter	-	0.3
CSDESW	Source/drain sidewall fringing capacitance per unit length	F/m	0.0
CGSL	Light doped source-gate region overlap capacitance	F/m	0.0
CGDL	Light doped drain-gate region overlap capacitance	F/m	0.0
CKAPPA	Coefficient for lightly doped region overlap capacitance fringing field capacitance	F/m	0.6
CF	Gate to source/drain fringing field capacitance	F/m	calculated[9]
CLC	Constant term for the short channel model	m	0.1e-7
CLE	Exponential term for the short channel model	none	0.0
DLC	Length offset fitting parameter for gate charge	m	LINT
DLCB	Length offset fitting parameter for body charge	m	0
DLBG	Length offset fitting parameter for backgate charge	m	0.0
DWC	Width offset fitting parameter from C-V	m	WINT
DELVT	Threshold voltage adjust for C-V	V	0.0
FBODY	Scaling factor for body charge	-	1.0

[6] If NSUB is positive, $\mathtt{VSDFB} = -\frac{\mathtt{kT}}{\mathtt{q}} \log\left(\frac{10^{20}\mathtt{NSUB}}{\mathtt{n_i}\cdot\mathtt{n_i}}\right) - 0.3$ else $\mathtt{VSDFB} = -\frac{\mathtt{kT}}{\mathtt{q}} \log\left(\frac{10^{20}}{\mathtt{NSUB}}\right) + 0.3$.

[7] If NSUB is positive, $\phi_{sd} = 2\frac{kT}{q}\log\left(\frac{\mathtt{NSUB}}{n_i}\right)$, $\gamma_{sd} = \frac{5.753\times10^{-12}\sqrt{\mathtt{NSUB}}}{C_{box}}$, $\mathtt{VSDTH} = \mathtt{VSDFB} + \phi_{\mathtt{sd}} + \gamma_{\mathtt{sd}}\sqrt{\phi_{\mathtt{sd}}}$ else, $\phi_{sd} = 2\frac{kT}{q}\log\left(-\frac{\mathtt{NSUB}}{n_i}\right)$, $\gamma_{sd} = \frac{5.753\times10^{-12}\sqrt{-\mathtt{NSUB}}}{C_{box}}$, $\mathtt{VSDTH} = \mathtt{VSDFB} - \phi_{\mathtt{sd}} - \gamma_{\mathtt{sd}}\sqrt{\phi_{\mathtt{sd}}}$.

[8] $X_{sddep} = \sqrt{\frac{2\epsilon_{si}\phi_{sd}}{q|\mathtt{NSUB}10^6|}}$, $C_{sddep} = \frac{\epsilon_{si}}{X_{sddep}}$, $\mathtt{CSDMIN} = \frac{\mathtt{C_{sddep}C_{box}}}{\mathtt{C_{sddep}+C_{box}}}$.

[9] if CF is not given, then it is calculated using $\mathtt{CF} = \frac{2\epsilon_{\mathtt{OX}}}{\pi}\ln\left(1 + \frac{4\times10^{-7}}{\mathtt{T_{OX}}}\right)$.

Model parameters	Description	Units	Default
ACDE	Exponential coefficient for charge thickness in capMod=3 for accumulation and depletion regions.	m/V	1.0
MOIN	Coefficient for the gate-bias dependent surface potential.	$V^{1/2}$	15.0
Level 10: Temperature Parameters			
TNOM	Temperature at which parameters are expected	$^{\circ}C$ RF Model Parameters	27
UTE	Mobility temperature exponent	none	-1.5
KT1	Temperature coefficient for threshold voltage	V	-0.11
KT11	Channel length dependence of the temperature coefficient for threshold voltage	V*m	0.0
KT2	Body-bias coefficient of the Vth temperature effect	none	0.022
UA1	Temperature coefficient for UA m/V 4.31e-9 - Ub2 ub1 Temperature coefficient for Ub	$(m/V)^2$	-7.61e-18
UC1	Temperature coefficient for UC	1/V	-.056 note[10]
AT	Temperature coefficient for saturation velocity	m/sec	3.3e4
TCJSWG	Temperature coefficient of CJSWG	1/K	0
TPBSWG	Temperature coefficient of PBSWG	V/K	0
CTHO	Normalized thermal capacity	$(W * sec)/(m^{\circ}C)$	1e-5
PRT	Temperature coefficient for RDSW	$\Omega - \mu m$	0
RTHO	Normalized thermal resistance	$m^{\circ}C/W$	0
NTRECF	Temperature coefficient for NRECF	-	0
NTRECR	Temperature coefficient for NRECR	-	0
XBJT	Power dependence of j_{bjt} on temperature	-	1
XDIF	Power dependence of j_{dif} on temperature	-	XBJT
XREC	XREC Power dependence of j_{rec} on temperature	-	1
XTUN	Power dependence of j_{tun} on temperature	-	0

[10] For MOBMOD = 1 and 2, the unit is m/V^2. Default is -5.6e-11. For MOBMOD = 3, unit is 1/V and default is -0.056.

Model parameters	Description	Units	Default
WTHO	Minimum width for thermal resistance calculation	m	0
	Level 10: RF Model Parameters		
RGATEMOD	Gate resistance model selector RGATEMOD = 0 No gate resistance RGATEMOD = 1 Constant gate resistance RGATEMOD = 2 Rii model with variable resistance RGATEMOD = 3 Rii model with two nodes	-	0
RSHG	Gate sheet resistance	-	0.1
XRCRG1	Parameter for distributed channel resistance effect for intrinsic input resistance	-	12.0
XRCRG2	Parameter to account for the excess channel diffusion resistance for intrinsic input resistance	-	1.0
NGCON	Number of gate contacts	-	1
XGW	Distance from the gate contact to the channel edge	m	0.0
XGL	Offset of the gate length due to variations in patterning	m	0.0

Table 2.26: BSIMSOI Model Parameters

Model level 18 (VDMOS)

The vertical double-diffused power MOSFET model is based on the uniform charge control model (UCCM) developed at Rensselaer Polytechnic Institute [5]. The VDMOS current-voltage characteristics are described by a single, continuous analytical expression for all regimes of operation. The physics-based model includes effects such as velocity saturation in the channel, drain induced barrier lowering, finite output conductance in saturation, the quasi-saturation effect through a bias dependent drain parasitic resistance, effects of bulk charge, and bias dependent low-field mobility. An important feature of the implementation is the utilization of a single continuous expression for the drain current, which is valid below and above threshold, effectively removing discontinuities and improving convergence properties.

Model level 19 (VDMOS_RAD)

This model adds total dose radiation effects to the basic VDMOS with dynamic radiation effects and annealing taken into account. The approach taken is described in [15]. Gamma radiation leads to the generation of electron-hole pairs both in the semiconductor parts and in the oxide of MOS devices. Electrons created in the oxide quickly escape into the semiconductor, while the holes get trapped creating a positive charge in the oxide. The radia-

tion also results in the build-up of traps in the semiconductor-oxide interface. The primary effects of the trapped oxide and interface charge are a shift of the MOSFET threshold voltage and a reduction of the carrier mobility in the channel. Since details of these radiation mechanisms vary with device type, radiation history, operating conditions and annealing procedures, the model is generalized in such a way that the user can input alternative dependencies of the interface charge density on the radiation dose. Five functional forms are embedded in the model that can be selected by the user to match experimental data.

Model level 20 (VDMOS_TF)

The VDMOS contains a parasitic drain-source diode. Gamma radiation can induce photocurrents in the p-n junction of this diode. The level 20 Mosfet model is similar to the level 18 Mosfet except that photocurrents in the drain-source parasitic diode are included in level 20. The photocurrents are modeled in the same way as in the level 3 and level 4 diode models. The photocurrent is represented by a current source in parallel with the p-n junction. This current source includes prompt photocurrent associated with the generation of electron-hole pairs in the depletion region and delayed photocurrent associated with the build-up and discharge of carriers in the quasi-neutral regions surrounding the junction. For a description of how to specify the radiation pulse form, refer to the writeup for the level 3 diode.

The following tables give parameters for the level 18 MOSFET.

Parameter	Description	Units	Default
AD	Drain diffusion area	m^2	0
AS	Source diffusion area	m^2	0
L	Channel length	m	0.0001
M	Multiplier for M devices connected in parallel	–	1
NRD	Multiplier for RSH to yield parasitic resistance of drain	squares	0
NRS	Multiplier for RSH to yield parasitic resistance of source	squares	0
PD	Drain diffusion perimeter	m	0
PS	Source diffusion perimeter	m	0
TEMP	Device temperature	°C	27
W	Channel width	m	0.0001

Table 2.27: Power MOSFET Device Parameters.

Parameter	Description	Units	Default
ALPHA	Parameter accounting for the threshold dependence on the channel potential	–	1.05
CBD	Zero-bias bulk-drain p-n capacitance	F	0
CBS	Zero-bias bulk-source p-n capacitance	F	0

Parameter	Description	Units	Default
CGBO	Gate-bulk overlap capacitance/channel length	F/m	0
CGDO	Gate-drain overlap capacitance/channel width	F/m	0
CGSO	Gate-source overlap capacitance/channel width	F/m	0
CJ	Bulk p-n zero-bias bottom capacitance/area	F/m^2	0
CJSW	Bulk p-n zero-bias sidewall capacitance/area	F/m^2	0
CV	Charge model storage selector	–	1
CVE	Meyer-like capacitor model selector	–	1
D1AF	Drain-source diode flicker noise exponent	–	1
D1BV	Drain-source diode reverse breakdown voltage	V	1e+99
D1CJO	Drain-source diode junction capacitance	F	0
D1EG	Drain-source diode activation energy	eV	1.11
D1FC	Drain-source diode forward bias depletion capacitance	–	0.5
D1IBV	Drain-source diode current at breakdown voltage	A	0.001
D1IKF	Drain-source diode high injection knee currrent	A	0
D1IS	Drain-Source diode saturation current	A	1e-14
D1ISR	Drain-source diode recombination saturation current	A	0
D1KF	Drain-source diode flicker noise coefficient	–	0
D1M	Drain-source diode grading coefficient	–	0.5
D1N	Drain-source diode emission coefficient	–	1
D1NR	Drain-source diode recombination emission coefficient	–	2
D1RS	Drain-source diode ohmic resistance	Ω	0
D1TNOM	Drain-source diode nominal temperature	°C	300.15
D1TT	Drain-source diode transit time	s	0
D1VJ	Drain-source diode junction potential	V	1
D1XTI	Drain-source diode sat. current temperature exponent	–	3
DELTA	Transition width parameter	–	5
DRIFTPARAMA	Drift region resistance intercept parameter	Ω	0.08
DRIFTPARAMB	Drift region resistance slope parameter	unknown	0.013
ETA	Subthreshold ideality factor	–	1.32
FC	Coefficient for forward-bias depletion capacitance formula	–	0.5
FPE	Charge partitioning scheme selector	–	1
GAMMAL0	Body effect constant in front of linear term	–	0
GAMMAS0	Body effect constant in front of square root term	$V^{-1/2}$	0.5

Parameter	Description	Units	Default
IS	Bulk p-n saturation current	A	1e-14
JS	Bulk p-n saturation current density	A/m^2	0
LO	Gate length of nominal device	m	0.0001
LAMBDA	Output conductance parameter	V^{-1}	0.048
LD	Lateral diffusion length	m	0
LGAMMAL	Sensitivity of gL on device length	–	0
LGAMMAS	Sensitivity of gS on device length	V$^{-1/2}$	0
M	Knee shape parameter	–	4
MCV	Transition width parameter used by the charge partitioning scheme	–	10
MJ	Bulk p-n bottom grading coefficient	–	0.5
MJSW	Bulk p-n sidewall grading coefficient	–	0.5
NSS	Surface state density	cm^{-2}	0
NSUB	Substrate doping density	cm^{-3}	0
PB	Bulk p-n bottom potential	V	0.8
PHI	Surface potential	V	0.6
RD	Drain ohmic resistance	Ω	0
RDSSHUNT	Drain-source shunt resistance	Ω	0
RG	Gate ohmic resistance	Ω	0
RS	Source ohmic resistance	Ω	0
RSH	Drain, source diffusion sheet resistance	Ω	0
SIGMAO	DIBL parameter	–	0.048
TEMPMODEL	Specification to type of parameter interpolation over temperature (see User Guide section 5.3	–	NONE
THETA	Mobility degradation parameter	m/V	0
TNOM	Nominal device temperature	°C	27
TOX	Gate oxide thickness	m	1e-07
TPG	Gate material type (-1 = same as substrate, 0 = aluminum, 1 = opposite of substrate	–	1
UO	Surface mobility	1/(Vcm^{2}s)	280
VFB	Flat band voltage	V	1e-12
VMAX	Maximum drift velocity for carriers	m/s	40000
VSIGMA	DIBL parameter	V	0.2
VSIGMAT	DIBL parameter	V	1.7
VTO	Zero-bias threshold voltage	V	0

Parameter	Description	Units	Default
W0	Gate width of nominal device	m	0.0001
WGAMMAL	Sensitivity of gL on device width	–	0
WGAMMAS	Sensitivity of gS on device width	$V^{-1/2}$	0
XJ	Metallurgical junction depth	m	0
XQC	Charge partitioning factor	–	0.6

Table 2.28: Power MOSFET Model Parameters.

The following tables give parameters for the level 19 MOSFET.

Parameter	Description	Units	Default
AD	Drain diffusion area	m^2	0
AS	Source diffusion area	m^2	0
DOSE	Radiation total dose (ignored in transient)	rads	0
DOSERATE_COEFF0	Initial dose rate level if type = PULSE	rads/sec	0
DOSERATE_COEFF1	Maximum dose rate level if type = PULSE	rads/sec	0
DOSERATE_COEFF2	Delay time of start of radiation pulse if type = PULSE	s	0
DOSERATE_COEFF3	Rise time of radiation pulse if type = PULSE	s	0
DOSERATE_COEFF4	Fall time of radiation pulse if type = PULSE	s	0
DOSERATE_COEFF5	Width of radiation pulse if type = PULSE	s	0
DOSERATE_COEFF6	Period of radiation pulse if type = PULSE	s	0
DOSERATE_ORDER	Order of doserate functional form	–	0
DOSERATE_TYPE	Doserate function type	–	
L	Channel length	m	0.0001
M	Multiplier for M devices connected in parallel	–	1
NRD	Multiplier for RSH to yield parasitic resistance of drain	squares	0
NRS	Multiplier for RSH to yield parasitic resistance of source	squares	0
PD	Drain diffusion perimeter	m	0
PS	Source diffusion perimeter	m	0

Parameter	Description	Units	Default
PULSEDATA	Expression (in braces) or filename (in quotes "") of (Time, Value) pairs to use instead of internal radiation source (functiontype = 7)	–	0
TEMP	Device temperature	°C	27
W	Channel width	m	0.0001

Table 2.29: Total Dose Effects Power MOSFET Device Parameters.

Parameter	Description	Units	Default
ALPHA	Parameter accounting for the threshold dependence on the channel potential	–	1.05
ALPHANINT	Mobility coefficient for interface-trapped charge density	cm^2	2.8e-12
ALPHANOXT	Mobility coefficient for oxide-trapped charge density	cm^2	1.2e-12
ANNEALALPHA	Annealing factor alpha	–	1
ANNEALTAU	Annealing time constant	s	1
CBD	Zero-bias bulk-drain p-n capacitance	F	0
CBS	Zero-bias bulk-source p-n capacitance	F	0
CGBO	Gate-bulk overlap capacitance/channel length	F/m	0
CGDO	Gate-drain overlap capacitance/channel width	F/m	0
CGSO	Gate-source overlap capacitance/channel width	F/m	0
CJ	Bulk p-n zero-bias bottom capacitance/area	F/m^2	0
CJSW	Bulk p-n zero-bias sidewall capacitance/area	F/m^2	0
CV	Charge model storage selector	–	1
CVE	Meyer-like capacitor model selector	–	1
D1AF	Drain-source diode flicker noise exponent	–	1
D1BV	Drain-source diode reverse breakdown voltage	V	1e+99
D1CJO	Drain-source diode junction capacitance	F	0
D1EG	Drain-source diode activation energy	eV	1.11
D1FC	Drain-source diode forward bias depletion capacitance	–	0.5
D1IBV	Drain-source diode current at breakdown voltage	A	0.001
D1IKF	Drain-source diode high injection knee currrent	A	0
D1IS	Drain-Source diode saturation current	A	1e-14
D1ISR	Drain-source diode recombination saturation current	A	0
D1KF	Drain-source diode flicker noise coefficient	–	0
D1M	Drain-source diode grading coefficient	–	0.5

Parameter	Description	Units	Default
D1N	Drain-source diode emission coefficient	–	1
D1NR	Drain-source diode recombination emission coefficient	–	2
D1RS	Drain-source diode ohmic resistance	Ω	0
D1TNOM	Drain-source diode nominal temperature	°C	300.15
D1TT	Drain-source diode transit time	s	0
D1VJ	Drain-source diode junction potential	V	1
D1XTI	Drain-source diode sat. current temperature exponent	–	3
DELTA	Transition width parameter	–	5
DRIFTPARAMA	Drift region resistance intercept parameter	Ω	0.08
DRIFTPARAMB	Drift region resistance slope parameter	unknown	0.013
ETA	Subthreshold ideality factor	–	1.32
FC	Coefficient for forward-bias depletion capacitance formula	–	0.5
FPE	Charge partitioning scheme selector	–	1
GAMMAL0	Body effect constant in front of linear term	–	0
GAMMAS0	Body effect constant in front of square root term	$V^{-1/2}$	0.5
IS	Bulk p-n saturation current	A	1e-14
JS	Bulk p-n saturation current density	A/m^2	0
L0	Gate length of nominal device	m	0.0001
LAMBDA	Output conductance parameter	V^{-1}	0.048
LD	Lateral diffusion length	m	0
LGAMMAL	Sensitivity of gL on device length	–	0
LGAMMAS	Sensitivity of gS on device length	$V^{-1/2}$	0
M	Knee shape parameter	–	4
MCV	Transition width parameter used by the charge partitioning scheme	–	10
MJ	Bulk p-n bottom grading coefficient	–	0.5
MJSW	Bulk p-n sidewall grading coefficient	–	0.5
NIT_COEFF0	Coefficient in function for radiation-induced oxide trap states	–	0
NIT_COEFF1	Coefficient in function for radiation-induced oxide trap states	–	0
NIT_COEFF2	Coefficient in function for radiation-induced oxide trap states	–	0
NIT_COEFF3	Coefficient in function for radiation-induced oxide trap states	–	0

Parameter	Description	Units	Default
NIT_COEFF4	Coefficient in function for radiation-induced oxide trap states	–	0
NIT_COEFF5	Coefficient in function for radiation-induced oxide trap states	–	0
NIT_COEFF6	Coefficient in function for radiation-induced oxide trap states	–	0
NIT_ORDER	Order of function type for radiation-induced oxide trap states	–	4
NIT_TYPE	Function type for radiation-induced oxide trap states	–	
NSS	Surface state density	cm^{-2}	0
NSUB	Substrate doping density	cm^{-3}	0
PB	Bulk p-n bottom potential	V	0.8
PHI	Surface potential	V	0.6
RD	Drain ohmic resistance	Ω	0
RDSSHUNT	Drain-source shunt resistance	Ω	0
RG	Gate ohmic resistance	Ω	0
RS	Source ohmic resistance	Ω	0
RSH	Drain, source diffusion sheet resistance	Ω	0
SIGMA0	DIBL parameter	–	0.048
TEMPMODEL	Specification to type of parameter interpolation over temperature (see User Guide section 5.3	–	NONE
THETA	Mobility degradation parameter	m/V	0
TNOM	Nominal device temperature	°C	27
TOX	Gate oxide thickness	m	1e-07
TPG	Gate material type (-1 = same as substrate, 0 = aluminum, 1 = opposite of substrate	–	1
U0	Surface mobility	$1/(Vcm^2s)$	280
VFB	Flat band voltage	V	1e-12
VMAX	Maximum drift velocity for carriers	m/s	40000
VSIGMA	DIBL parameter	V	0.2
VSIGMAT	DIBL parameter	V	1.7
VTO	Zero-bias threshold voltage	V	0
VTO_COEFF0	Coefficient in function for dose-dependent threshold voltage	–	0
VTO_COEFF1	Coefficient in function for dose-dependent threshold voltage	–	0

Parameter	Description	Units	Default
VTO_COEFF2	Coefficient in function for dose-dependent threshold voltage	–	0
VTO_COEFF3	Coefficient in function for dose-dependent threshold voltage	–	0
VTO_COEFF4	Coefficient in function for dose-dependent threshold voltage	–	0
VTO_COEFF5	Coefficient in function for dose-dependent threshold voltage	–	0
VTO_COEFF6	Coefficient in function for dose-dependent threshold voltage	–	0
VTO_ORDER	Order of threshold voltage function type	–	1
VTO_TYPE	Function type for dose-dependent threshold voltage	–	
W0	Gate width of nominal device	m	0.0001
WGAMMAL	Sensitivity of gL on device width	–	0
WGAMMAS	Sensitivity of gS on device width	$V^{-1/2}$	0
XJ	Metallurgical junction depth	m	0
XQC	Charge partitioning factor	–	0.6

Table 2.30: Total Dose Effects Power MOSFET Model Parameters.

The following tables give parameters for the level 20 MOSFET.

Parameter	Description	Units	Default
AD	Drain diffusion area	m^2	0
AS	Source diffusion area	m^2	0
L	Channel length	m	0.0001
M	Multiplier for M devices connected in parallel	–	1
NRD	Multiplier for RSH to yield parasitic resistance of drain	squares	0
NRS	Multiplier for RSH to yield parasitic resistance of source	squares	0
PD	Drain diffusion perimeter	m	0
PS	Source diffusion perimeter	m	0
TEMP	Device temperature	°C	27
W	Channel width	m	0.0001

Table 2.31: Transient Photocurrent Effects Power Mosfet Device Parameters.

Parameter	Description	Units	Default
ALPHA	Parameter accounting for the threshold dependence on the channel potential	–	1.05
CBD	Zero-bias bulk-drain p-n capacitance	F	0
CBS	Zero-bias bulk-source p-n capacitance	F	0
CGBO	Gate-bulk overlap capacitance/channel length	F/m	0
CGDO	Gate-drain overlap capacitance/channel width	F/m	0
CGSO	Gate-source overlap capacitance/channel width	F/m	0
CJ	Bulk p-n zero-bias bottom capacitance/area	F/m^2	0
CJSW	Bulk p-n zero-bias sidewall capacitance/area	F/m^2	0
CV	Charge model storage selector	–	1
CVE	Meyer-like capacitor model selector	–	1
D1AF	Drain-source diode flicker noise exponent	–	1
D1BV	Drain-source diode reverse breakdown voltage	V	1e+99
D1CJO	Drain-source diode junction capacitance	F	0
D1EG	Drain-source diode activation energy	eV	1.11
D1FC	Drain-source diode forward bias depletion capacitance	–	0.5
D1IBV	Drain-source diode current at breakdown voltage	A	0.001
D1IKF	Drain-source diode high injection knee currrent	A	0
D1IS	Drain-Source diode saturation current	A	1e-14
D1ISR	Drain-source diode recombination saturation current	A	0
D1KF	Drain-source diode flicker noise coefficient	–	0
D1M	Drain-source diode grading coefficient	–	0.5
D1N	Drain-source diode emission coefficient	–	1
D1NR	Drain-source diode recombination emission coefficient	–	2
D1RS	Drain-source diode ohmic resistance	Ω	0
D1TNOM	Drain-source diode nominal temperature	°C	300.15
D1TT	Drain-source diode transit time	s	0
D1VJ	Drain-source diode junction potential	V	1
D1XTI	Drain-source diode sat. current temperature exponent	–	3
DELTA	Transition width parameter	–	5
DEVICEAREA		m^2	1
DRIFTPARAMA	Drift region resistance intercept parameter	Ω	0.08
DRIFTPARAMB	Drift region resistance slope parameter	unknown	0.013
ETA	Subthreshold ideality factor	–	1.32

Parameter	Description	Units	Default
EXPTAU1	Rise time constant of exponential cusp radiation source (functiontype = 3)	s	0.01
EXPTAU2	Fall time constant of exponential cusp radiation source (functiontype = 3)	s	1e+10
EXPTD1	Rise delay time of exponential cusp radiation source (functiontype = 3)	s	0
EXPTD2	Fall delay time of exponential cusp radiation source (functiontype = 3)	s	1e+10
EXPV1	Initial value of exponential cusp radiation source (functiontype = 3)	–	0
EXPV2	Height of exponential cusp radiation source (functiontype = 3)	–	0
FC	Coefficient for forward-bias depletion capacitance formula	–	0.5
FPE	Charge partitioning scheme selector	–	1
FUNCTIONTYPE	Internal function type for pulse (1-6) or user defined (7)	–	0
GAMMAL0	Body effect constant in front of linear term	–	0
GAMMAS0	Body effect constant in front of square root term	$V^{-1/2}$	0.5
GRORDER	Order of magnitude of radiation generation rate	–	25
IS	Bulk p-n saturation current	A	1e-14
ISNPP	This a n-p-p+ diode	logical (T/F)	False
ISPNN	This is a p-n-n+ diode	logical (T/F)	False
JS	Bulk p-n saturation current density	A/m^2	0
L0	Gate length of nominal device	m	0.0001
LAMBDA	Output conductance parameter	V^{-1}	0.048
LD	Lateral diffusion length	m	0
LGAMMAL	Sensitivity of gL on device length	–	0
LGAMMAS	Sensitivity of gS on device length	$V^{-1/2}$	0
LINEK	Slope of point 1 of linear radiation source (functiontype = 6)	s^{-1}	0
LINET1	Time of point 1 of linear radiation source (functiontype = 6)	s	0
LINEV1	Value of point 1 of linear radiation source (functiontype = 6)	–	0
M	Knee shape parameter	–	4

Parameter	Description	Units	Default
MCV	Transition width parameter used by the charge partitioning scheme	–	10
MJ	Bulk p-n bottom grading coefficient	–	0.5
MJSW	Bulk p-n sidewall grading coefficient	–	0.5
NA	Doping density in the p- region	m^{-3}	5e+20
NAHI	Doping density in the p+ region	m^{-3}	1e+24
ND	Doping density in the n- region	m^{-3}	3e+25
NDHI	Doping density in the n+ region	m^{-3}	3e+25
NDN	Diffusion constant of electrons in n-region at low injection	m^2/s	0.001
NDNHI	Diffusion constant of electrons in n+-region at low injection	m^2/s	0.001
NDP	Diffusion constant of holes in n-region at low injection	m^2/s	0.0007
NDPHI	Diffusion constant of holes in n+-region at low injection	m^2/s	0.0002
NI	Intrinsic concentration	m^{-3}	1.45e+16
NSS	Surface state density	cm^{-2}	0
NSUB	Substrate doping density	cm^{-3}	0
PB	Bulk p-n bottom potential	V	0.8
PDN	Diffusion constant of electrons in p-region at low injection	m^2/s	0.004
PDNHI	Diffusion constant of electrons in p+-region at low injection	m^2/s	0.005
PDP	Diffusion constant of holes in p-region at low injection	m^2/s	0.0005
PDPHI	Diffusion constant of holes in p+-region at low injection	m^2/s	0.0001
PERMITTIVITY	Dielectric permittivity of the semiconductor	F/m	1.0433e-10
PHI	Surface potential	V	0.6
PULSEDATA	Expression (in braces) or filename (in quotes ””) of (Time, Value) pairs to use instead of internal radiation source (functiontype = 7)	–	0
PULSEPER	Period of radiation pulse (functiontype = 1)	s	1e+10
PULSEPW	Width of radiation pulse (functiontype = 1)	s	1e-05
PULSETD	Time delay of radiation pulse (functiontype = 1)	s	0
PULSETF	Fall time of radiation pulse (functiontype = 1)	s	1e-05
PULSETR	Rise time of radiation pulse (functiontype = 1)	s	1e-05
PULSEV1	Initial value of radiation pulse (functiontype = 1)	–	0
PULSEV2	Maximum value of radiation pulse (functiontype = 1)	–	4.3

Parameter	Description	Units	Default
PWLT1	Time of point 1 of piecewise linear curve radiation source (functiontype = 5)	s	1
PWLT2	Time of point 2 of piecewise linear curve radiation source (functiontype = 5)	s	2
PWLT3	Time of point 3 of piecewise linear curve radiation source (functiontype = 5)	s	3
PWLT4	Time of point 4 of piecewise linear curve radiation source (functiontype = 5)	s	4
PWLT5	Time of point 5 of piecewise linear curve radiation source (functiontype = 5)	s	5
PWLV1	Value of point 1 of piecewise linear curve radiation source (functiontype = 5)	–	0
PWLV2	Value of point 2 of piecewise linear curve radiation source (functiontype = 5)	–	0
PWLV3	Value of point 3 of piecewise linear curve radiation source (functiontype = 5)	–	0
PWLV4	Value of point 4 of piecewise linear curve radiation source (functiontype = 5)	–	0
PWLV5	Value of point 5 of piecewise linear curve radiation source (functiontype = 5)	–	0
RAUGN	Auger recombination rate for electrons in p-region	cm^6/s	1.1e-42
RAUGP	Auger recombination rate for holes in n-region	cm^6/s	3e-43
RD	Drain ohmic resistance	Ω	0
RDSSHUNT	Drain-source shunt resistance	Ω	0
RG	Gate ohmic resistance	Ω	0
RS	Source ohmic resistance	Ω	0
RSH	Drain, source diffusion sheet resistance	Ω	0
SFFMFC	Carrier frequency of single frequency FM radiation source (functiontype = 4)	Hz	1
SFFMFS	Signal frequency of single frequency FM radiation source (functiontype = 4)	Hz	0
SFFMMDI	Modulation index of single frequency FM radiation source (functiontype = 4)	–	0
SFFMVA	Amplitude of single frequency FM radiation source (functiontype = 4)	–	0
SFFMVO	Offset of single frequency FM radiation source (functiontype = 4)	–	0
SIGMA0	DIBL parameter	–	0.048

Parameter	Description	Units	Default
SINFREQ	Frequency of sinusoidal radiation source (functiontype = 2)	Hz	1
SINTD	Delay of sinusoidal radiation source (functiontype = 2)	s	0
SINTHETA	Inverse of time constant for exponential envelope of sinusoidal radiation source (functiontype = 2)	s^{-1}	0
SINVA	Amplitude of sinusoidal radiation source (functiontype = 2)	–	0
SINVO	Offset of sinusoidal radiation source (functiontype = 2)	–	0
TAUINFN	Electron lifetime in p-region at saturated SRH condition	s	2e-06
TAUINFNHI	Electron lifetime in p+-region at saturated SRH condition	s	2e-07
TAUINFP	Hole lifetime in n-region at saturated SRH condition	s	4e-08
TAUINFPHI	Hole lifetime in n+-region at saturated SRH condition	s	4e-08
TAUNO	Electron lifetime in p-region at low injection	s	1e-06
TAUNOHI	Electron lifetime in p+-region at low injection	s	1e-07
TAUPO	Hole lifetime in n-region at low injection	s	2e-08
TAUPOHI	Hole lifetime in N+-region at low injection	s	2e-08
TEMPMODEL	Specification to type of parameter interpolation over temperature (see User Guide section 5.3	–	NONE
THETA	Mobility degradation parameter	m/V	0
TNOM	Nominal device temperature	°C	27
TOX	Gate oxide thickness	m	1e-07
TPG	Gate material type (-1 = same as substrate, 0 = aluminum, 1 = opposite of substrate	–	1
UO	Surface mobility	$1/(Vcm^2s)$	280
VFB	Flat band voltage	V	1e-12
VMAX	Maximum drift velocity for carriers	m/s	40000
VSIGMA	DIBL parameter	V	0.2
VSIGMAT	DIBL parameter	V	1.7
VTO	Zero-bias threshold voltage	V	0
WO	Gate width of nominal device	m	0.0001
WGAMMAL	Sensitivity of gL on device width	–	0
WGAMMAS	Sensitivity of gS on device width	$V^{-1/2}$	0
WN	Width of the n- region	m	2e-06
WNHI	Width of the n+ region	m	1e-06
WP	Width of the p- region	m	5e-05
WPHI	Width of the p+ region	m	1e-05

Parameter	Description	Units	Default
XJ	Metallurgical junction depth	m	0
XQC	Charge partitioning factor	–	0.6

Table 2.32: Transient Photocurrent Effects Power Mosfet Model Parameters.

Quadratic Temperature Compensation

Spice temperature effects are default, but MOSFET levels 18, 19 and 20 have a more advanced temparature compensation available. By specifying TEMPMODEL=QUADRATIC in the netlist, parameters can be interpolated quadratically between measured values extracted from data. See Section 5.3 of the User's Guide for more details.

MOSFET Equations

The following equations define an N-channel MOSFET. The P-channel devices use a reverse the sign for all voltages and currents. The equations use the following variables:

$$
\begin{aligned}
V_{bs} &= \text{intrinsic substrate-intrinsic source voltage} \\
V_{bd} &= \text{intrinsic substrate-intrinsic drain voltage} \\
V_{ds} &= \text{intrinsic drain-substrate source voltage} \\
V_{dsat} &= \text{saturation voltage} \\
V_{gs} &= \text{intrinsic gate-intrinsic source voltage} \\
V_{gd} &= \text{intrinsic gate-intrinsic drain voltage} \\
V_t &= kT/q \text{ (thermal voltage)} \\
V_{th} &= \text{threshold voltage} \\
C_{ox} &= \text{the gate oxide capacitance per unit area} \\
f &= \text{noise frequency} \\
k &= \text{Boltzmann's constant} \\
q &= \text{electron charge} \\
Leff &= \text{effective channel length} \\
Weff &= \text{effective channel width} \\
T &= \text{analysis temperature } (^\circ K) \\
T_0 &= \text{nominal temperature (set using TNOM option)}
\end{aligned}
$$

Other variables are listed in the BJT Model Parameters Table 2.17.

All Levels

$$
\begin{aligned}
I_g &= \text{gate current} = 0 \\
I_b &= \text{bulk current} = I_{bs} + I_{bd} \\
\text{where} & \\
I_{bs} &= \text{bulk-source leakage current} = I_{ss}\left(e^{V_{bs}/(N-V_t)} - 1\right) \\
I_{ds} &= \text{bulk-drain leakage current} = I_{ds}\left(e^{V_{bd}/(N-V_t)} - 1\right) \\
\text{where} & \\
\textit{if} & \\
& \mathbf{JS} = 0, \text{ or } \mathbf{AS} = 0 \text{ or } \mathbf{AD} = 0 \\
\textit{then} & \\
& I_{ss} = \mathbf{IS} \\
& I_{ds} = \mathbf{IS} \\
\textit{else} & \\
& I_{ss} = \mathrm{AS} \times \mathbf{JS} + \mathrm{PS} \times \mathbf{JSSW} \\
& I_{ds} = \mathrm{AD} \times \mathbf{JS} + \mathrm{PD} \times \mathbf{JSSW} \\
& I_d = \text{drain current} = I_{drain} - I_{bd} \\
& I_s = \text{source current} = -I_{drain} - I_{bs}
\end{aligned}
$$

Level 1: Idrain

Normal Mode: $V_{ds} > 0$

Case 1

For cutoff region: $V_{gs} - V_{to} < 0$

$$I_{drain} = 0$$

Case 2

For linear region: $V_{ds} < V_{gs} - V_{to}$

$$I_{drain} = (W/L)(\mathbf{KP}/2)(1 + \mathbf{LAMBDA} \times V_{ds})V_{ds}(2(V_{gs} - V_{to}) - V_{ds})$$

Case 3

For saturation region: $0 \leq V_{gs} - V_{to} \leq V_{ds}$

$$I_{drain} = (W/L)(\mathbf{KP}/2)(1 + \mathbf{LAMBDA} \cdot V_{ds})(V_{gs} - V_{to})^2$$

where

$$V_{to} = \mathbf{VTO} + \mathbf{GAMMA} \cdot \left((\mathbf{PHI} - V_{bs})^{1/2}\right)^{1/2}$$

Inverted Mode: $V_{ds} < 0$

Here, simply switch the source and drain in the normal mode equations given above.

Level 3: Idrain

See Reference [16] below for detailed information.

Capacitance

Level 1 and 3
C_{bs} = bulk-source capacitance = area cap. + sidewall cap. + transit time cap.
C_{bd} = bulk-drain capacitance = area cap. + sidewall cap. + transit time cap.

where

$$
\begin{aligned}
&\textit{if} \\
&\qquad \mathbf{CBS} = 0 \text{ and } \mathbf{CBD} = 0 \\
&\textit{then} \\
&\qquad C_{bs} = \mathrm{AS} \cdot \mathbf{CJ} \cdot C_{bsj} + \mathrm{PS} \cdot \mathbf{CJSW} \cdot C_{bss} + \mathbf{TT} \cdot G_{bs} \\
&\qquad C_{bd} = \mathrm{AD} \cdot \mathbf{CJ} \cdot C_{bdj} + \mathrm{PD} \cdot \mathbf{CJSW} \cdot C_{bds} + \mathbf{TT} \cdot G_{ds} \\
&\textit{else} \\
&\qquad C_{bs} = \mathrm{CBS} \cdot C_{bsj} + \mathrm{PS} \cdot \mathbf{CJSW} \cdot C_{bss} + \mathbf{TT} \cdot G_{bs} \\
&\qquad C_{bd} = \mathrm{CBD} \cdot C_{bdj} + \mathrm{PD} \cdot \mathbf{CJSW} \cdot C_{bds} + \mathbf{TT} \cdot G_{ds} \\
&\textit{where} \\
&\qquad G_{bs} = \text{DC bulk-source conductance} = dI_{bs}/dV_{bs} \\
&\qquad G_{bd} = \text{DC bulk-drain conductance} = dI_{bd}/dV_{bd}
\end{aligned}
$$

$$
\begin{aligned}
&\textit{if} \\
&\qquad V_{bs} \leq \mathbf{FC} \cdot \mathbf{PB} \\
&\textit{then} \\
&\qquad C_{bsj} = (1 - V_{bs}/\mathbf{PB})^{-\mathbf{MJ}} \\
&\qquad C_{bss} = (1 - V_{bs}/\mathbf{PBSW})^{-\mathbf{MJSW}} \\
&\textit{if} \\
&\qquad V_{bs} > \mathbf{FC} \cdot \mathbf{PB} \\
&\textit{then} \\
&\qquad C_{bsj} = (1 - \mathbf{FC})^{-(1+\mathbf{MJ})}(1 - \mathbf{FC}(1 + \mathbf{MJ}) + \mathbf{MJ} \cdot V_{bs}/\mathbf{PB}) \\
&\qquad C_{bss} = (1 - \mathbf{FC})^{-(1+\mathbf{MJSW})}(1 - \mathbf{FC}(1 + \mathbf{MJSW}) + \mathbf{MJSW} \cdot V_{bs}/\mathbf{PBSW}) \\
&\textit{if} \\
&\qquad V_{bd} \leq \mathbf{FC} \cdot \mathbf{PB} \\
&\textit{then} \\
&\qquad C_{bdj} = (1 - V_{bd}/\mathbf{PB})^{-\mathbf{MJ}} \\
&\qquad C_{bds} = (1 - V_{bd}/\mathbf{PBSW})^{-\mathbf{MJSW}} \\
&\textit{if} \\
&\qquad V_{bd} > \mathbf{FC} \cdot \mathbf{PB} \\
&\textit{then} \\
&\qquad C_{bdj} = (1 - \mathbf{FC})^{-(1+\mathbf{MJ})}(1 - \mathbf{FC}(1 + \mathbf{MJ}) + \mathbf{MJ} \cdot V_{bd}/\mathbf{PB}) \\
&\qquad C_{bds} = (1 - \mathbf{FC})^{-(1+\mathbf{MJSW})}(1 - \mathbf{FC}(1 + \mathbf{MJSW}))
\end{aligned}
$$

$$
\begin{aligned}
&C_{gs} = \text{gate-source overlap capacitance} = \mathbf{CGSO} \cdot \mathbf{W} \\
&C_{gd} = \text{gate-drain overlap capacitance} = \mathbf{CGDO} \cdot \mathbf{W} \\
&C_{gb} = \text{gate-bulk overlap capacitance} = \mathbf{CGBO} \cdot \mathbf{L}
\end{aligned}
$$

Temperature Effects

All Levels

$$\mathbf{IS}(T) = \mathbf{IS} \cdot \exp\left(E_g(T_0) \cdot T/T_0 - E_g(T)\right)/V_t$$
$$\mathbf{JS}(T) = \mathbf{JS} \cdot \exp\left(E_g(T_0) \cdot T/T_0 - E_g(T)\right)/V_t$$
$$\mathbf{JSSW}(T) = \mathbf{JSSW} \cdot \exp\left(E_g(T_0) \cdot T/T_0 - E_g(T)\right)/V_t$$
$$\mathbf{PB}(T) = \mathbf{PB} \cdot T/T_0 - 3V_t \ln(T/T_0) - E_g(T_0) \cdot T/T_0 + E_g T$$
$$\mathbf{PBSW}(T) = \mathbf{PBSW} \cdot T/T_0 - 3V_t \ln(T/T_0) - E_g(T_0) \cdot T/T_0 + E_g T$$
$$\mathbf{PHI}(T) = \mathbf{PHI} \cdot T/T_0 - 3V_t \ln(T/T_0) - E_g(T_0) \cdot T/T_0 + E_g T$$

where

$$E_g(T) = \text{silicon bandgap energy} = 1.16 - 0.000702T^2/(T + 1108)$$
$$\mathbf{CBD}(T) = \mathbf{CBD} \cdot (1 + \mathbf{MJ} \cdot (0.0004(T - T_0) + (1 - \mathbf{PB}(T)/\mathbf{PB})))$$
$$\mathbf{CBS}(T) = \mathbf{CBS} \cdot (1 + \mathbf{MJ} \cdot (0.0004(T - T_0) + (1 - \mathbf{PB}(T)/\mathbf{PB})))$$
$$\mathbf{CJ}(T) = \mathbf{CJ} \cdot (1 + \mathbf{MJ} \cdot (0.0004(T - T_0) + (1 - \mathbf{PB}(T)/\mathbf{PB})))$$
$$\mathbf{CJSW}(T) = \mathbf{CJSW} \cdot (1 + \mathbf{MJSW} \cdot (0.0004(T - T_0) + (1 - \mathbf{PB}(T)/\mathbf{PB})))$$
$$\mathbf{KP}(T) = \mathbf{KP} \cdot (T/T_0)^{-3/2}$$
$$\mathbf{UO}(T) = \mathbf{UO} \cdot (T/T_0)^{-3/2}$$
$$\mathbf{MUS}(T) = \mathbf{MUS} \cdot (T/T_0)^{-3/2}$$
$$\mathbf{MUZ}(T) = \mathbf{MUZ} \cdot (T/T_0)^{-3/2}$$
$$\mathbf{X3MS}(T) = \mathbf{X3MS} \cdot (T/T_0)^{-3/2}$$

For a thorough description of MOSFET models see [17, 16, 18, 19, 20, 11, 12, 21, 22, 23].

For complete documentation of the BSIM3 model, see the users' manual for the BSIM3, available for download at http://www-device.eecs.berkeley.edu/ bsim3/get.html. **Xyce** implements Version 3.2.2 of the BSIM3, you will have to get the documentation from the FTP archive on the Berkeley site.

For complete documentation of the BSIMSOI model, see the users' manual for the BSIMSOI, available for download at http://www-device.eecs.berkeley.edu/ bsimsoi/. **Xyce** implements Version 3.2 of the BSIMSOI, you will have to get the documentation from the FTP archive on the Berkeley site..

Voltage- or Current-controlled Switch

General Form

```
S<name> <(+) switch node> <(-) switch node>
+ <(+) control node> <(-) control node>
+ <model name> [ON] [OFF]

W<name> <(+) switch node> <(-) switch node>
+ <control node voltage source>
+ <model name> [ON] [OFF]
```

Examples

```
S1 21 23 12 10 SMOD1
SSET 15 10 1 13 SRELAY
W1 1 2 VCLOCK SWITCHMOD1
W2 3 0 VRAMP SM1 ON
```

Model Form

```
.MODEL <model name> VSWITCH [model parameters]
.MODEL <model name> ISWITCH [model parameters]
```

Description

The voltage- or current-controlled switch is a particular type of controlled resistor. This model is designed to help reduce numerical issues. See Special considerations below.

The resistance between the <(+) switch node> and the <(-) switch node> is dependent on either the voltage between the <(+) control node> and the <(-) control node> or the current through the control node voltage source. The resistance changes in a continuous manner between the RON and ROFF model parameters.

No resistance is inserted between the control nodes. It is up to the user to make sure that these nodes are not floating.

Comments

Even though evaluating the switch model is computationally inexpensive, for transient analysis, **Xyce** steps through the transition section using small time-steps in order to calculate the waveform accurately. Thus, a circuit with many switch transitions can result in lengthy run times.

The ON and OFF parameters are used to specify the initial state of the switch at the first step of the operating point calculation; this does not force the switch to be in that state, it only gives the operating point solver an initial state to work with. If it is known that the switch should be in a particular state in the operating point it could help convergence to specify one of these keywords.

Model Parameters

Table 2.33 gives the available model parameters for the voltage- or current-controlled switch.

Model parameters	Description	Units	Default
ROFF	Off Resistance	ohm	1.0×10^6
RON	On Resistance	ohm	1.0
VOFF	Control Voltage for Off State	volt	0.0
VON	Control Voltage for 0n State	volt	1.0
IOFF	Control Currrent for Off State	amp	0.0
ION	Control Current for 0n State	amp	1×10^{-3}
OFF	Control for Off State		
ON	Control for 0n State		

Table 2.33. Controlled Switch Model Parameters.

Special Considerations

- Due to numerical limitations, **Xyce** can only manage a dynamic range of approximately 12 decades. Thus, it is recommended the user limit the ratio $\mathbf{ROFF/RON}$ to less than 10^{12}.
- Furthermore, it is a good idea to limit the narrowness of the transition region. This is because in the transition region, the switch has gain and the narrower the region, the higher the gain and the more potential for numerical problems. The smallest value allowed for $\|\mathbf{VON} - \mathbf{VOFF}\|$ or $\|\mathbf{ION} - \mathbf{IOFF}\|$ is 1×10^{-12}.

Controlled switch equations

The equations in this section use the following variables:

R_s	$=$	switch resistance		
V_c	$=$	voltage across control nodes		
I_c	$=$	current through control node voltage source		
L_m	$=$	log-mean of resistor values	$=$	$\ln\left(\sqrt{\mathbf{RON} \cdot \mathbf{ROFF}}\right)$
L_r	$=$	log - ratio of resistor values	$=$	$\ln\left(\mathbf{RON}/\mathbf{ROFF}\right)$
V_d	$=$	difference of control voltages	$=$	$\mathbf{VON} - \mathbf{VOFF}$
I_d	$=$	difference of control currents	$=$	$\mathbf{ION} - \mathbf{IOFF}$

Switch Resistance

To compute the switch resistance, **Xyce** first calculates the "switch state" S as $S = (V_c - \mathbf{VOFF})/V_d$ or $S = (I_c - \mathbf{IOFF})/I_d$. The switch resistance is then:

$$R_s = \begin{cases} \mathbf{RON}, & S \geq 1.0 \\ \mathbf{ROFF}, & S \leq 0.0 \\ \exp\left(L_m + 0.75L_r(2S-1) - 0.25L_r(2S-1)^3\right), & 0 < S < 1 \end{cases}$$

Generic Switch

General Form

```
SW<name> <(+) switch node> <(-) switch node>
+ <model name> [ON] [OFF] <control = { expression }>
```

Examples

```
SW 1 2 SWI OFF CONTROL={I(VMON)}
SW 1 2 SWV OFF CONTROL={V(3)-V(4)}
SW 1 2 SW OFF CONTROL={if(time>0.001,1,0)}
```

Model Form

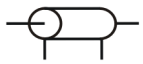
```
.MODEL <model name> VSWITCH [model parameters]
.MODEL <model name> ISWITCH [model parameters]
.MODEL <model name> SWITCH [model parameters]
```

Description

The generic switch is similar to the voltage- or current-controlled switch except that the control variable is anything that can be writen as an expression. The examples show how a voltage- or current-controlled switch can be implemented with the generic switch. Also shown is a relay that turns on when a certain time is reached. Model parameters are given in Table 2.33.

Lossless (Ideal) Transmission Line

General Form	`T<name> <A port (+) node> <A port (-) node>`
	`+ <B port (+) node> <B port (-) node> [model name]`
	`+ Z0=<value> [TD=<value>] [F=<value> [NL=<value>]]`

Examples	`Tline inp inn outp outn Z0=50 TD=1us` `Tline2 inp inn outp outn Z0=50 F=1meg NL=1.0`
Symbol	
Description	The lossless transmission line device is a two port (`A` and `B`), bi-directional delay line. The `(+)` and `(-)` nodes define the polarity of a positive voltage at a port.
Comments	`Z0` is the characteristic impedance. The transmission line's length is specified by either `TD` (a delay in seconds) or by `F` and `NL` (a frequency and relative wavelength at `F`). `NL` defaults to 0.25 (`F` is the quarter-wave frequency). If `F` is given, the time delay is computed as $\frac{NL}{F}$. While both `TD` and `F` are optional, at least one of them must be given.

Model Parameters

Table 2.34 gives the available model parameters for the lossless transmission line.

Model parameters	Description	Units	Default
`Z0`	Characteristic impedance	ohm	-
`TD`	Transmission delay	second	-
`F`	Frequency for **NL**	Hz	-
`NL`	Relative wavelength	-	0.25

Table 2.34. Lossless (Ideal) Transmission Line Parameters.

Behavioral Digital Devices

General Form	Y<type> <name> [low output node] [high output node] [input reference node] <input node(s)> <output node(s)> <model name> [device parameters]
Examples	YAND in1 in2 out DMOD IC=1 YNOT in out DMOD YNOR vlo vhi vref in1 in2 out DDEF .MODEL DMOD DIG (VLO=0.5 VHI=2.0 VREF=0 DELAY=20ns) .MODEL DDEF DIG
Model Form	.MODEL <model name> DIG [model parameters]

Parameters and Options

`<type>`

Type of digital device. Supported devices are: NOT, AND, NAND, OR, NOR, XOR, NXOR, and ADD. All have two input nodes and one output node, except NOT, which has only one input node and 1 output and ADD which has 3 input and two output.

`<name>`

Name of the device instance.

`[low output node]`

Dominant node to be connected to the output node(s) to establish low output state. This node is connected to the output by a resistor and capacitor in parallel, whose values are set by the model. If specified by the model, this node can be omitted and a fixed voltage is used instead.

`[high output node]`

Dominant node to be connected to the output node(s) to establish high output state. This node is connected to the output by a resistor and capacitor in parallel, whose values are set by the model. If specified by the model, this node can be omitted and a fixed voltage is used instead.

`[input reference node]`

This node is connected to the input node by a resistor and capacitor in parallel, whose values are set by the model. Determination if the input state is based on the voltge drop between the input node and this node. If specified by the model, this node can be omitted and a fixed voltage is used instead.

`<input and output nodes>`

Nodes that connect to the circuit.

`<model name>`

Name of the model defined in a .MODEL line.

`[device parameters]`

Parameter listed in Table 2.35 may be provided as `<parameter>=<value>` specifications as needed. For devices with more than one output, multiple output initial states may be provided as a comma separated list (e.g. IC=T,F).

Device Parameters

Table 2.35 gives the available device parameters for the behavioral digital devices.

Parameter	Description	Units	Default
IC	Vector of initial values for output(s)	logical (T/F)	False

Table 2.35: Behavioral Digital Device Parameters.

Model Parameters

Table 2.36 gives the available model parameters for the behavioral digital devices.

Parameter	Description	Units	Default
CHI	Capacitance between output node and high reference	F	1e-06
CLO	Capacitance between output node and low reference	F	1e-06
CLOAD	Capacitance between input node and input reference	F	1e-06
DELAY	Delay time of device	s	1e-08
RLOAD	Resistance between input node and input reference	Ω	1000
S0RHI	Low state resitance between output node and high reference	Ω	100
S0RLO	Low state resistance between output node and low reference	Ω	100
S0TSW	Switching time transition to low state	s	1e-08
S0VHI	Maximum voltage to switch to low state	V	1.7
S0VLO	Minimum voltage to switch to low state	V	-1.5
S1RHI	High state resistance between output node and high reference	Ω	100
S1RLO	High state resistance between output node and low reference	Ω	100
S1TSW	Switching time transition to high state	s	1e-08
S1VHI	Maximum voltage to switch to high state	V	7
S1VLO	Minimum voltage to switch to high state	V	0.9
VHI	Internal high state supply voltage	V	0
VLO	Internal low state supply voltage	V	0
VREF	Internal reference voltage for inputs	V	0

Table 2.36: Behavioral Digital Model Parameters.

Model Description

The input interface model consists of the input node connected with a resistor and capacitor in parallel to the input reference node. The values of these are: RLOAD and CLOAD. If

the model parameter VREF is specified, then the input reference node is not given, and an internal node of fixed voltage, VREF, is used instead.

The logical state of any input node is determined by comparing the voltage relative to the reference to the range for the low and high state. The range for the low state is S0VLO to S0VHI. Similarly, the range for the high state is S1VLO to S1VHI. The state of the input node will remain fixed as longs as the voltage stays within the range for the current state. Only when it goes outside the range will transition to the other state be considered.

The output interface model is more complex than the input model, but shares the same basic configuration of a resistor and capacitor in parallel to simulate loading. For the output case, there are such connections to two nodes, the low output node and the high output node. Either or both of these can be omitted it the VLO and/or VHI model parameters are specified. Specifying either of these causes a fixed voltage node to be used in place of an externally connected node, like in the input case.

The capacitance to the high node is specified by CHI, and the capacitance to the low node is CLO. The resistors in parallel with these capacitors are variable, and have values that depend on the state. In the low state (S0), the resistance values are: S0RLO and S0RHI. In the high state (S1),the resistance values are: S1RLO and S1RHI. Transition to the high state occurs exponentially over a time of S1TSW, and to the low state S0TSW.

Delay of the device is given by the model parameter DELAY.

Subcircuit

A subcircuit can be introduced into the circuit netlist using the specified nodes to substitute for the argument nodes in the definition. It provides a building block of circuitry to be defined a single time and subsequently used multiple times in the overall circuit netlists.

General Form	`X<name> [node]* <subcircuit name> [PARAMS: [<name> = <value>]*]`

Examples	`X12 100 101 200 201 DIFFAMP`
	`XBUFF 13 15 UNITAMP`
	`XFOLLOW IN OUT VCC VEE OUT OPAMP`
	`XFELT 1 2 FILTER PARAMS: CENTER=200kHz`
	`XNANDI 25 28 7 MYPWR MYGND PARAMS: IO_LEVEL=2`

Parameters and Options	`<subcircuit name>`
	The name of the subcircuit's definition.
	`PARAMS:`
	Passed into subcircuits as arguments and into expressions inside the subcircuit.

Comments	There must be an equal number of nodes in the subcircuit call and in its definition. Subcircuit references may be nested to any level. However, the nesting cannot be circular. For example, if subcircuit `A`'s definition includes a call to subcircuit `B`, then subcircuit `B`'s definition cannot include a call to subcircuit `A`.

2.3 TCAD Devices

Semiconductor device simulation, which is based on a coupled set of partial differential equations (PDE's) is supported in **Xyce**. Such devices can be invoked from the circuit netlist, in a similar manner to traditional SPICE-style analog devices. One dimensional and two dimensional devices are supported, with the dimensionality determined by the device model level.

General Form, 1D:	`Z<name> <node> <node> [model name]`
	`[na=<value>] [nd=<value>] [nx=<value>] [area=<value>]`
	`[graded=<value>] [wj=<value>] [l=<value>] [w=<value>]`
	`[tecplotlevel=<value>] [sgplotlevel=<value>]`
	`[gnuplotlevel=<value>] [node=<tabular data>]`
	`[region=<tabular data>] [bulkmaterial=<string>]`
	`[temp=<value>]`

General Form, 2D:	`Z<name> <node> <node> [node][node] [model name]`
	`[na=<value>] [nd=<value>] [meshfile=<filename.msh>]`
	`[nx=<value>][ny=<value>] [l=<value>][w=<value>]`
	`[type=<string> [node=<tabular data>]`
	`[region=<tabular data>] [x0=<value>] [cyl=<value>]`
	`[tecplotlevel=<value>] [sgplotlevel=<value>]`
	`[gnuplotlevel=<value>] [txtdatalevel=<value>]`
	`[ph.a1=<value>] [ph.type=<string>]`
	`[ph.tstart=<value>] [ph.tstop=<value>] [photogen=<value>]`
	`[ph.td=<value>] [ph.tr=<value>]`
	`[ph.tf=<value>] [ph.pw=<value>] [ph.per=<value>]`
	`[bulkmaterial=<string>] [temp=<value>]`

Comments:	Most of the PDE parameters are specified on the instance level. At this point the model statement is only used for specifying if the device is 1D or 2D, via the level parameter. Both the 1D and the 2D devices can construct evenly spaced meshes, internally. The 2D device also has the option of reading in an unstructured mesh from an external mesh file. The electrode tabular data specification is explained in detail in table 2.41 Similarly, the doping region tabular data specification is explained in detail in table 2.39.

TCAD Device Parameters

Most TCAD device parameters are specified on the instance level.

Instance parameters	Description	Units	Default	Device Type
	All Levels			
`name`	The instance name must start with a Z.	-	-	1D, 2D
`node`	Minimum of 2 connecting circuit nodes. The 2D device may have as many as 4 nodes, while the 1D device can only have 2. The node parameter is a tabular parameter, which specifies all the electrode attributes. See table 2.41 for a list.	-	-	1D, 2D
`region`	Specifies doping regions. Like the node parameter, this is a tabular parameter, containing several attributes.. See table 2.39 for a list.	-	-	1D, 2D
`area`	Cross sectional area of the device.	-	1.0	1D, 2D
`tecplotlevel`	Setting for Tecplot output: 0 - no Tecplot files 1 - Tecplot files, each output in a separate file. 2 - Tecplot file, each output appended to a single file. Tecplot files will have the `.dat` suffix, and the prefix will be the name of the device instance	-	1	1D, 2D
`sgplotlevel`	Flag for sgplot output. 0 - no sgplot files. 1 - sgplot files. sgplot is a plotting program that comes as part of the SG Framework [24]. sgplot files will have the *.res suffix, and the prefix will be the name of the device instance	-	0	1D, 2D
`gnuplotlevel`	Flag for gnuplot output. 0 - no gnuplot files. 1 - gnuplot files. gnuplot is an open source plotting program that is usually installed on Linux systems. gnuplot files will have the *Gnu.dat suffix, and the prefix will be the name of the device instance.	-	0	1D, 2D

Instance parameters	Description	Units	Default	Device Type
`txtdatalevel`	Flag for volume-averaged text output. 0 - no text files. 1 - text files. txtdataplot files will have the *.txt suffix, and the prefix will be the name of the device instance.	-	0	2D
`bulkmaterial`	Material of bulk material.	-	si	1D, 2D
`mobmodel`	mobility model.	-	carr	1D, 2D
`type`	P-type or N-type - this is only relevant if using the default dopings	-	PNP	1D, 2D
`temp`	Temperature	K	300.15	1D, 2D
`nx`	Number of mesh points, x-direction.	-	11	1D, 2D
`l, w`	Device length and width. These parameters mean the same thing for the 1D device.	-	1.0e-3	1D,2D
`graded`	Flag for graded junction vs. abrupt junction. (1=graded, 0=abrupt)	-	0	1D
`wj`	Junction width.	-	1.0e-4	1D
Level 2 (2D) only				
`ny`	Number of mesh points, y-direction. Similar to nx (see above).	-	11	2D
`meshfile`	This is a required field for a 2D simulation. If the user specifies `meshfile = internal.mesh`, then **Xyce** will create a cartesian mesh. If the user specifies anything else (for example `meshfile = diode.msh`), **Xyce** will attempt to read in an external mesh file (in the example, named `diode.msh`) which is in the format of the SG Framework [24].	-	-	2D

Instance parameters	Description	Units	Default	Device Type
x0	This is the scaling factor for length. The code will do all of its scaling internally, so it is generally not necessary to specify it manually. This is provided primarily for testing purposes.	-	max length of device	2D
Photogeneration terms (2D only)				
ph.a1	Photocurrent source magnitude.	$cm^{-3}s^{-1}$	0.0	2D
ph.tstart	Starting time	seconds	0.0	2D
ph.tstop	Ending time	seconds	1.0e+100	2D
photogen	This is an on/off flag. Setting to 1 turns on photogeneration terms	-	0	2D
ph.type	Uniform is the only available type.	-	UNIFORM	2D
ph.td	Delay time	seconds	0.0	2D
ph.tr	Rise time	seconds	0.0	2D
ph.tf	Fall time	seconds	0.0	2D
ph.pw	Pulse width	seconds	0.0	2D
ph.per	Period length	seconds	0.0	2D

Table 2.37: PDE Device Instance Parameters.

There is only one TCAD device model parameter, the level.

Model parameters	Description	Units	Default
LEVEL	The level determines if this is a 1D or a 2D device. 1=1D, 2=2D.	-	1

Table 2.38. TCAD Device Model Parameters.

Instance parameters	Description	Units	Default	Device Type
	All Levels			
`function`	functional form of doping region. Options are uniform, gaussian, and step.		1D,2D	uniform
`type`	Ntype of Ptype		1D,2D	ntype
`nmax`	Maximum value of impurity concentration.	cm^{-3}	1D,2D	1.0e15
`nmin`	Minimum value of impurity concentration.	cm^{-3}	1D,2D	1.0e15
`xloc`	Peak location	cm	1D,2D	0.0
`xwidth`	Distance from nmax to nmin, if applicable. This is only applicable for the function=gaussian case.		1D,2D	1.0e-3
`flatx`	This parameter determines if we're doing a half gaussian or a full gaussian. See table 2.40	-	1D,2D	0
	Level 2 (2D) only			
`yloc`	Same as xloc, but for the y-direction.	cm	2D	0.0
`ywidth`	Same as xwidth, but for the y-direction.	cm	2D	1.0e-3
`flaty`	Same as flatx, but for the y-direction.	-	2D	0

Table 2.39: PDE Device Doping Region Parameters. These correspond to the region instance parameter.

flatx or flaty value	Description	1D Cross Section
0	Gaussian on both sides of the peak (`xloc`) location.	
+1	Gaussian if `x>xloc`, flat (constant at the peak value) if `x<xloc`.	
-1	Gaussian if `x<xloc`, flat (constant at the peak value) if `x>xloc`.	

Table 2.40: Description of the flatx, flaty doping parameters

Electrode parameters	Description	Units	Default
	Level 2 (2D) only		
`name`	Electrode name	-	anode
`bc`	Carrier Density Boundary condition type (dirichlet or neumann)	-	dirichlet
`start`	Starting location	cm	0.0
`end`	Ending location	cm	0.0
`side`	Side specification (top, bottom, left or right)	-	top
`material`	Contact material		neutral
`oxidebndryflag`	Oxide layer boolean	-	false (0)
`oxthick`	Oxide thickness	cm	0.0
`oxcharge`	Oxide charge	C	0.0

Table 2.41: PDE Device Electrode Parameters.

Physical Models

This section contains information about physical models used in **Xyce** for TCAD devices. This includes various mobility models, expressions for calculating the effective mass for electrons and holes, an expression for intrinsic carrier concentration as a function of temperature, expressions which describe contacts to metal as well as contacts to metal-oxide-semiconductor devices.

Material Models and Parameters

This section describes some of the basic material properties that are available in **Xyce**. Described here are the models for effective mass, intrinsic carrier concentration, and the bandgap. This information is needed for the more complex models described in the mobility section (section 2.3) and the boundary condition section (section 2.3).

Effective Mass

Xyce includes functions which return the effective mass of electrons and holes for a number of semiconductor materials.

Electron Effective Mass

The electron effective mass is calculated as

$$m_{de} = (m_l^* m_t^{*2})^{1/3} \tag{2.1}$$

where m_l and m_t are the effective masses along the longitudinal and transverse directions of the ellipsoidal energy surface.

Hole Effective Mass

The hole effective mass is calculated as

$$m_{dh} = (m_{lh}^{*3/2} + m_{hh}^{*3/2})^{2/3} \tag{2.2}$$

where m_{lh} and m_{hh} are the ”light” and ”heavy” hole masses, respectively.

Intrinsic Carrier Concentration

The intrinsic carrier concentration in a semiconductor is obtained from the ”np” product

$$np = n_i^2 = N_C N_V exp(-E_g/kT) \tag{2.3}$$

or

$$n_i = \sqrt{N_C N_V} e^{-E_g/2kT} \tag{2.4}$$

The expression used in **Xyce** to calculate the intrinsic carrier concentration comes from this and is given by

$$n_i = 4.9 \times 10^{15} (\frac{m_{de} m_{dh}}{m_0^2})^{3/4} M_c^{1/2} T^{3/2} e^{-E_g/2kT} \tag{2.5}$$

where M_c is the number of equivalent minima in the conduction band for the semiconductor, m_{de} is the density-of-state effective mass for electrons, m_{dh} is the density-of-state effective mass for holes, and m_0 is the free-electron mass.

Semiconductor	Symbol	$M_c^{1/2}$	n_i at room temperature
Silicon	si	$\sqrt{6.00}$	$1.25x10^{10}$
Germanium	ge	2.00	$2.5x10^{13}$
Galium Arsenide	gaas	1.00	$2.0x10^{6}$

Table 2.42: Intrinsic Carrier Concentration Parameters

Bandgap

The bandgap is a material and temperature-dependent quantity. The bandgap model for semiconductor materials, is based on Thurmond [25]. This model is given by:

$$E_g = E_{g0} - A * \left(\frac{T^{2.0}}{T + T_{off}} \right) \tag{2.6}$$

where E_g is the bandgap (eV) and T is the temperature (K). A, E_{g0}, and T_{off} are all material-dependent constants. Insulating materials, such as silicon dioxide, are assumed to have constant bandgaps, so their bandgaps are given by:

$$E_g = E_{g0} \tag{2.7}$$

where E_{g0} is a material-dependent constant. The values for the material-dependent constants used by equations 2.6 and 2.7 are given in Table 2.43.

Material	Symbol	E_{g0} (eV)	A	T_{off} (K)
Silicon	si	1.17	4.73e-4	636.0
Germanium	ge	0.7437	4.774e-4	235.0

Material	Symbol	E_{g0} (eV)	A	T_{off} (K)
Galium Arsenide	gaas	1.519	5.405e-4	204.0
Silicon Dioxide	sio2	9.00	NA	NA
Silicon Nitride	wdi	4.7	NA	NA
Sapphire	cu	4.7	NA	NA

Table 2.43: Bandgap constants

Mobility Models

A number of mobility models are included in **Xyce**. The analytic, arora, and carrier-carrier scattering models are considered to be low-field mobility models. The Lombardi surface mobility model is a transverse-field dependent model which also incorporates the mobility of the bulk silicon.

Analytic Mobility

This is a concentration- and temperature-dependent empirical mobility model, based on the work of Caughey and Thomas [26], which combines the effects of lattice scattering and ionized impurity scattering. The equation for the mobility of electrons is:

$$\mu_{0n} = \mu_{nmin} + \frac{\mu_{nmax}(\frac{T}{T_{ref}})^{nun} - \mu_{nmin}}{1 + (\frac{T}{T_{ref}})^{xin}(N_{total}/N_n^{ref})^{\alpha_n}} \tag{2.8}$$

and the equation for the mobility of holes is:

$$\mu_{0p} = \mu_{pmin} + \frac{\mu_{pmax}(\frac{T}{T_{ref}})^{nup} - \mu_{pmin}}{1 + (\frac{T}{T_{ref}})^{xip}(N_{total}/N_p^{ref})^{\alpha_p}} \tag{2.9}$$

where N_{total} is the local total impurity concentration (in $\#/cm^3$), T_{ref} is a reference temperature (300.15K), and T is the temperature (in degrees K). The parameters N_n^{ref} and N_p^{ref} are reference values for the doping concentration. The analytic mobility model can be selected by using the statement ”mobmodel=analytic” in the netlist.

The parameters for the analytic mobility model are given in Table 3.

Parameter	Silicon	GaAs
μ_{nmin}	55.24	0.0
μ_{nmax}	1429.23	8500.0
N_n^{ref}	1.072e17	1.69e17
nun	-2.3	-1.0
xin	-3.8	0.0
α_n	0.73	0.436
μ_{pmin}	49.70	0.0
μ_{pmax}	479.37	400.0
N_p^{ref}	1.606e17	2.75e17
nup	-2.2	-2.1
xip	-3.7	0.0
α_p	0.70	0.395

Table 2.44: Analytic Mobility Parameters

Arora Mobility

This mobility model is also an analytic model which depends on impurity concentration and temperature. It comes from the work of Arora, *et al.* [27] and is based on both experimental data and the modified Brooks-Herring theory of mobility. The equation for the mobility of electrons is:

$$\mu_{0n} = \mu_{n1}(\frac{T}{T_{ref}})^{exn1} + \frac{\mu_{n2}(\frac{T}{T_{ref}})^{exn2}}{1 + (\frac{N_{total}}{Cn(\frac{T}{T_{ref}})^{exn3}})^{\alpha_n}} \tag{2.10}$$

and the equation for the mobility of holes is:

$$\mu_{0p} = \mu_{p1}(\frac{T}{T_{ref}})^{exp1} + \frac{\mu_{p2}(\frac{T}{T_{ref}})^{exp2}}{1 + (\frac{N_{total}}{Cp(\frac{T}{T_{ref}})^{exp3}})^{\alpha_p}} \tag{2.11}$$

where

$$\alpha_n = An(\frac{T}{T_{ref}})^{exn4} \tag{2.12}$$

and

$$\alpha_p = Ap(\frac{T}{T_{ref}})^{exp4} \tag{2.13}$$

The Arora mobility model can be selected by including the statement ”mobmodel=arora” in the netlist. The parameters for the arora mobility model are given in Table 4.

Parameter	Silicon	GaAs
μ_{n1}	88.0	8.5e3
μ_{n2}	1252.0	0.0
Cn	1.26e17	1.26e17
An	0.88	0.0
exn1	-0.57	-0.57
exn2	-2.33	0.0
exn3	2.4	0.0
exn4	-0.146	0.0
μ_{p1}	54.3	4e2
μ_{p2}	407.0	0.0
Cp	2.35e17	2.35e17
Ap	0.88	0.0
exp1	-0.57	0.0
exp2	-2.23	0.0
exp3	2.4	0.0
exp4	-0.146	0.0

Table 2.45: Arora Mobility Parameters

Carrier-Carrier Scattering Mobility

This mobility model is based on the work of Dorkel and Leturq [28]. It incorporates carrier-carrier scattering effects, which are important when high concentrations of electrons and holes are present in the device. This model also takes lattice scattering and ionized impurity scattering into account. One important difference between the carrier-carrier scattering mobility model and the two previous mobility models (analytic and arora models) is that the carrier-carrier scattering mobility model depends upon the actual carrier concentrations in the device. This model is important for modeling breakdown as well as various radiation effects, which often result in very high carrier densities.

The expressions for the carrier-carrier model are as follows:

$$\mu_L = \mu_{L0}(\frac{T}{T_{ref}})^{-\alpha} \tag{2.14}$$

where μ_L is the lattice mobility, which has to do with scattering due to acoustic phonons.

$$\mu_I = \frac{AT^{3/2}}{N}[ln(1+\frac{BT^2}{N}) - \frac{BT^2}{N+BT^2}]^{-1} \tag{2.15}$$

where μ_I is the impurity mobility which is related to the interactions between the carriers and the ionized impurities.

$$\mu_{ccs} = \frac{2\times 10^{17}T^{3/2}}{\sqrt{pn}}[ln(1+8.28\times 10^8 T^2(pn)^{-1/3})]^{-1} \tag{2.16}$$

where μ_{ccs} is the carrier-carrier scattering mobility, which is very important when both types of carriers are at high concentration.

$$X = \sqrt{\frac{6\mu_L(\mu_I+\mu_{ccs})}{\mu_I\mu_{ccs}}} \tag{2.17}$$

is an intermediate term and

$$\mu = \mu_L[\frac{1.025}{1+(X/1.68)^{1.43}} - 0.025] \tag{2.18}$$

is the carrier mobility. The carrier-carrier scattering mobility can be selected by including the statement ”mobmobel=carr” in the netlist. The parameters for the carrier-carrier mobility model are given in Table 5.

Parameter	Carrier	Silicon	GaAs
Al	e^-	1430.0	8.50e3
Bl	e^-	-2.2	0.0
Ai	e^-	4.61e17	4.61e17
Bi	e^-	1.52e15	1.52e15
Al	h^+	495.0	4.0e2
Bl	h^+	-2.2	0.0
Ai	h^+	1.00e17	1.00e17
Bi	h^+	6.25e14	6.25e14

Table 2.46: Carrier-Carrier Mobility Parameters

Lombardi Surface Mobility Model

This mobility model combines expressions for mobility at the semiconductor-oxide interface and in bulk silicon. It is based on the work of Lombardi *et al.* [29]. The overall mobility is found using Mathiessen's rule:

$$\frac{1}{\mu} = \frac{1}{\mu_{ac}} + \frac{1}{\mu_b} + \frac{1}{\mu_{sr}} \tag{2.19}$$

where μ_{ac} is the carrier mobility due to scattering with surface acoustic phonons, μ_b is the carrier mobility in bulk silicon, and μ_{sr} is the carrier mobility limited by surface roughness scattering.

The Lombardi model is a more physics-based surface mobility model. It is a semi-empirical model for carrier mobility, and the expressions for the individual scattering mechanisms were extracted from experimental data taken in appropriate experimental conditions.

The expressions used in this model are given below:

$$\mu_{ac,n} = \frac{bn}{E_\perp} + \frac{cnN^{exn4}}{T(E_\perp)^{1/3}} \tag{2.20}$$

is the expression for electron mobility for acoustic phonon scattering,

$$\mu_{ac,p} = \frac{bp}{E_\perp} + \frac{cpN^{exp4}}{T(E_\perp)^{1/3}} \tag{2.21}$$

is the expression for hole mobility for acoustic phonon scattering,

$$\mu_{b,n} = \mu_{n0} + \frac{\mu_{max,n} - \mu_{n0}}{1 + (N/crn)^{exn1}} - \frac{\mu_{n1}}{1 + (csn/N)^{exn2}} \tag{2.22}$$

is the expression for bulk mobility for electrons, where

$$\mu_{max,n} = \mu_{n2}(\frac{T}{T_{ref}})^{-exn3} \tag{2.23}$$

and

$$\mu_{b,p} = \mu_{p0}exp(-pc/N) + \frac{\mu_{max,p}}{1 + (N/crp)^{exp1}} - \frac{\mu_{p1}}{1 + (csp/N)^{exp2}} \tag{2.24}$$

is the expression for bulk mobility for holes, where

$$\mu_{max,p} = \mu_{p2}(\frac{T}{T_{ref}})^{-exp3} \tag{2.25}$$

The expression for electrons for surface roughness scattering is

$$\mu_{sr,n} = (\frac{dn}{E_{\perp}^{exn8}}) \tag{2.26}$$

and the expression for holes for surface roughness scattering is

$$\mu_{sr,p} = (\frac{dp}{E_{\perp}^{exp8}}) \tag{2.27}$$

The parameters for the lombardi surface mobility model are given in Table 6.

Parameter	Silicon	GaAs
μ_{n0}	52.2	0.0
μ_{n1}	43.4	0.0
μ_{n2}	1417.0	1e6
crn	9.68e16	9.68e16
csn	3.43e20	0.0
bn	4.75e7	1e10
cn	1.74e5	0.0
dn	5.82e14	1e6
exn1	0.680	0.0
exn2	2.0	0.0
exn3	2.5	0.0
exn4	0.125	0.0
exn8	2.0	0.0
μ_{p0}	44.9	0.0
μ_{p1}	29.0	0.0
μ_{p2}	470.5	1.0
crp	2.23e17	2.23e17
csp	6.1e20	0.0
bp	9.93e6	1e10
cp	8.84e5	0.0
dp	2.05e14	1e6
exp1	0.719	0.0
exp2	2.0	0.0
exp3	2.2	0.0
exp4	0.0317	0.0
exp8	2.0	0.0
pc	9.23e16	0.0

Table 2.47: Lombardi Surface Mobility Parameters

Edge Mobilities

Mobility values are calculated along the edge connecting two nodes. In the case of the analytic, arora, and surface mobility models, the edge mobilities are calculated by taking the average of the mobilities at the two nodes. Then, the mobility along the edge connecting nodes 1 and 2 is:

$$\mu_{edge} = (\mu[1] + \mu[2])/2.0 \tag{2.28}$$

In the case of the carrier-carrier scattering mobility, the edge mobilities were calculated differently. The electron and hole concentrations were first calculated at the midpoint of the edge using a ”product” average and then these values of ”n” and ”p” were used in the function to calculate the mobility at the midpoint of the edge. For example, if n[1] and n[2] are the electron concentrations at nodes 1 and 2, the electron concentration along the edge is given by:

$$n_{edge} = \sqrt{n[1] * n[2]} \tag{2.29}$$

Subsequently, the mobility at the midpoint of an edge is found by using the values of electron and hole concentration at the midpoint of the edge when calling the function which returns the mobility, calcMob().

$$\mu_{n,edge}^{carrier} = f(n_{edge}) \tag{2.30}$$

This method makes more sense, especially when the electron and hole concentrations vary by several orders of magnitude. Then it approximates taking the average of the logarithms.

Boundary Conditions for Electrode Contacts

This section describes various boundary conditions that need to be applied to the semiconductor boundary. **Xyce** is predominantly an analog circuit simulator, and the TCAD (PDE-based) device modeling that has been implemented in **Xyce** takes external circuit information as input. This input consists of voltages and currents which are applied as boundary conditions to the semiconductor domain.

The physical connection from the circuit to the device generally includes a variety of materials, including metals and oxides. Electrical differences between the semiconductor and the contact material can result in a potential barrier that must be included in the imposed voltage boundary condition.

There are three general types of contacts between the circuit and the TCAD device which are currently handled by **Xyce**. The first is the ”neutral” contact, in which it is simply assumed that the electrode material does not impose any addition potential barrier to that of the Fermi level differences in the semiconductor. The second is the Schottky contact, in which the electrode is a specified metal, and a potential barrier is imposed to account for the workfunction difference between the metal and the semiconductor. The last type of contact is the metal-oxide-semiconductor contact, in which the workfunction difference, and the voltage drop across the oxide must be accounted for.

Neutral Contacts

A neutral contact refers to the case in which the contact is made to the semiconductor itself, and barrier heights due to material differences are not considered. This is the simplest type of contact in **Xyce**, and problems which use this type of contact are generally easier to solve, compared with other types of contacts. In this case, the boundary is given by

$$V_{bc} = V_{ckt} + V_{bi} \tag{2.31}$$

where V_{ckt} is the potential applied by the circuit and V_{bi} is the "built-in" potential of the semiconductor. For a p-type substrate, the built-in potential is given by

$$V_{bi} = -\frac{kT}{q} ln(\frac{N_A}{n_i}) \tag{2.32}$$

and for an n-type substrate, the built-in potential is given by

$$V_{bi} = \frac{kT}{q} ln(\frac{N_D}{n_i}) \tag{2.33}$$

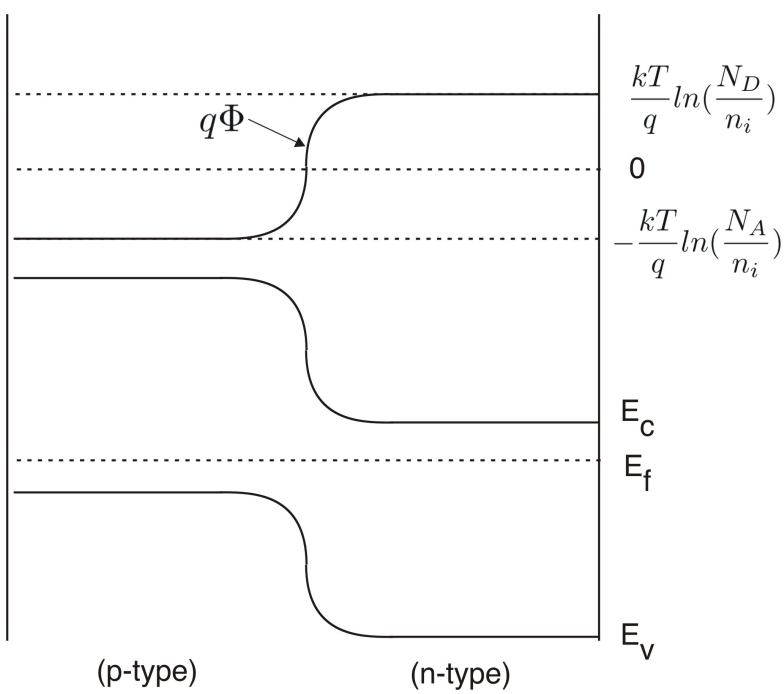


Figure 2.2. Neutral Contacts.

V_{bi} represents the extent of the energy band bending due to the doping of a device. While most of the dramatic changes will happen away from the contact, near junctions, it is still incorporated into the voltage boundary condition to maintain a flat potential near the contacts. Figure 2.2 shows the energy band variation across a PN junction, and the corresponding electrostatic potential. This variation is due to the internal physics of the device, and needs to be there even in the event of zero applied voltage. This is partially enforced by the solution to Poisson's equation, and also by the application of equation 2.31.

Schottky Contacts

In the case of a metal-semiconductor contact, it is necessary to add the workfunction difference, Φ_{ms}, to the potential in the semiconductor [30]. Φ_m is a constant for a given metal, and Φ_s is a function of the doping in the semiconductor. The workfunction potential, Φ, when multiplied by q, is the difference between the Fermi level and vacuum in the material. In essence, the workfunction difference represents the distance between the Fermi level in the metal and the Fermi level in the semiconductor when considering the individual band structures.

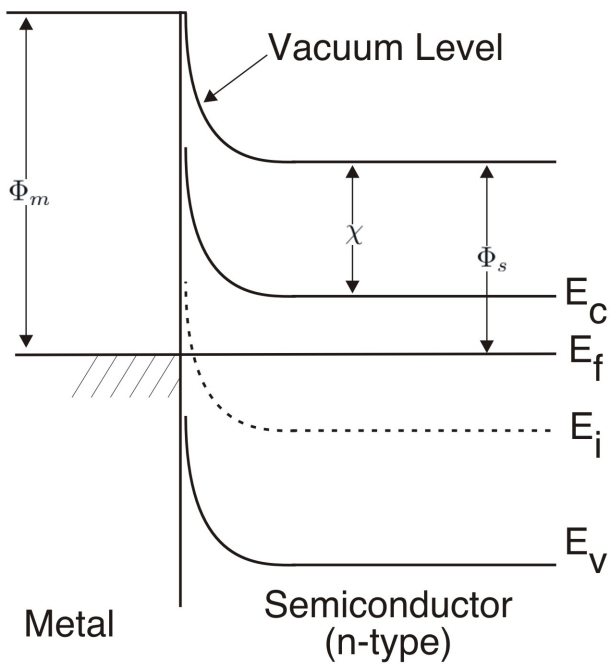


Figure 2.3. Schottky Contact, N-type.

In the case of an n-type semiconductor, the semiconductor workfunction can be represented as

$$\Phi_s = \chi + (E_C - E_{FS})/q \tag{2.34}$$

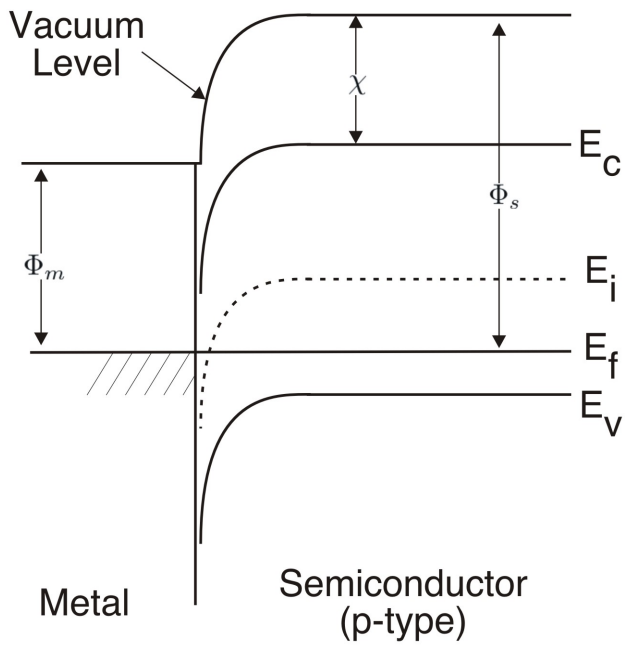


Figure 2.4. Schottky Contact, P-type.

where χ is the electron affinity in the semiconductor and qχ is the distance between the conduction band and vacuum in the semiconductor. E_C is the conduction band energy and E_{FS} is the Fermi level of the semiconductor. Rewriting this expression in terms of the doping concentration, it becomes

$$\Phi_s = \chi + E_g/2 - V_t ln(\frac{N_d}{n_i}) \tag{2.35}$$

In the case of a p-type semiconductor, the semiconductor workfunction can be represented as

$$\Phi_s = \chi + E_g/2 + (E_i - E_{FS})/q \tag{2.36}$$

where E_i is the intrinsic value of the Fermi level, and can be approximated as the halfway point between the conduction band (E_C) and the valance band (E_V). Rewriting this expression in terms of the doping concentration

$$\Phi_s = \chi + E_g/2 + V_t ln(\frac{N_a}{n_i}) \tag{2.37}$$

For the TCAD devices in **Xyce**, for a node at a metal-semiconductor contact, the quantity $\Phi_m - \Phi_s$ is added to the potential at the node to account for the metal-semiconductor barrier. The current values of metal workfunctions used in **Xyce** are given in Table 2.48. The values for electron affinity are given in Table 2.49. The boundary condition for a metal electrode in **Xyce** is given by

$$V_{bc} = V_{ckt} + V_{bi} + \Phi_{ms} \tag{2.38}$$

where V_{ckt} is the potential applied by the circuit to the electrode and V_{bi} is the ”built-in” potential of the semiconductor, a function of the semiconductor doping.

Metal	Symbol	Workfunction, Φ_m (Volts)
aluminum	al	4.10
p+-polysilicon	ppoly	5.25
n+-polysilicon	npoly	4.17
molybdenum	mo	4.53
tungsten	w	4.63
molybdenum disilicide	modi	4.80
tungsten disilicide	wdi	4.80
copper	cu	4.25
platinum	pt	5.30
gold	au	4.80

Table 2.48: Material workfunction values

Semiconductor	Symbol	Electron Affinity, χ (Volts)
Silicon	si	4.17
Germanium	ge	4.00
Galium Arsenide	gaas	4.07
Silicon Dioxide	sio2	0.97
Nitride	nitride	0.97
Sapphire	sapphire	0.97

Table 2.49: Electron affinities

Metal-Oxide-Semiconductor Contacts

To date in **Xyce**, only semiconductor material is included in the PDE solution domain. Metals and oxide materials are currently only included through boundary conditions. This is an adequate approach for a lot of problems. For some problems (such as modeling of low-dose radiation effects) modeling the oxide in more detail, as a PDE, will become necessary. However, since oxides are usually very thin, compared with the semiconductor domain, meshing both materials as part of the same simulation is difficult. Therefore, incorporating the effects of a gate oxide as part of the gate boundary condition is a reasonable approach.

In the case of a contact to a metal-oxide-semiconductor structure, the separation of the Fermi energies in the metal and the semiconductor at equilibrium is due to two effects: the workfunction difference between the metal and the semiconductor, and the effective interface charge. These two effects cause the bands to bend at the surface in equilibrium. The flatband voltage is the sum of these two terms [30]:

$$V_{FB} = \Phi_{ms} - \frac{Q_i}{C_i} \tag{2.39}$$

where Φ_{ms} is the metal-semiconductor workfunction difference, Q_i is the value of interface charge (in C/cm^2), and C_i is the oxide capacitance per unit area, which is given by

$$C_i = \frac{\epsilon_{ox}\epsilon_0}{x_o} \tag{2.40}$$

The voltage V_{FB} is the amount of bias which, when applied to the gate, causes the electron energy bands to be flat. This is the potential that is added to a boundary node in **Xyce** to account for a metal-oxide-semiconductor barrier. The overall boundary condition for a contact to a metal-oxide-semiconductor structure is given by

$$V_{bc} = V_{ckt} + V_{bi} + \Phi_{ms} - Q_i/C_i \tag{2.41}$$

where V_{ckt} is the potential applied by the circuit and V_{bi} is the ”built-in” potential of the semiconductor.

NMOS Device

The default NMOS device currently used in **Xyce** has a substrate doping concentration of $1.0 \times 10^{16}/cm^3$ and an oxide thickness of $1.0 \times 10^{-6}cm$. Since the ideal threshold voltage V_T is given by

$$V_T = 2\phi_F + \frac{\epsilon_s}{\epsilon_{ox}} x_o \sqrt{\frac{2qN_A\phi_F}{\epsilon_s\epsilon_0}} \tag{2.42}$$

V_T is equal to 0.892 V. for this device. Note that

$$\phi_F = \frac{1}{q}[E_i(bulk) - E_F] = \frac{kT}{q} ln(\frac{N_A}{n_i}) \tag{2.43}$$

for a p-type semiconductor substrate and

$$\phi_F = -\frac{kT}{q} ln(\frac{N_D}{n_i}) \tag{2.44}$$

for an n-type substrate.

3. Command Line Arguments

Xyce supports a handful of command line arguments which must be given *before* the netlist filename. While most of these are intended for general use, others simply give access to new features that, while supported, are not enabled by default. These options are designated as *trial* options. The general usage is as follows:

```
runxyce [arguments] <netlist filename>
```

Table 3.1 gives a complete lists of command line options. In this table, the shaded rows indicate the trial options. *DEPRECATED* options are no longer supported and will be removed from future releases.

Argument	Description	Usage	Default
-h	Help option. Prints usage and exits.	`-h`	-
-v	Prints the version banner and exits.	`-v`	-
-delim	Set the output file field.	`-delim <TAB|COMMA|string>`	-
-o	Place the results into specified file.	`-o <file>`	-
-l	Place the log output into specified file.	`-l <file>`	-
-r	Output a binary rawfile.	`-r <file>`	-
-a	Use with `-r` to output a readable (ascii) rawfile.	`-r <file> -a`	-
-nox	Use the NOX nonlinear solver.	`-nox <on|off>`	on
-linsolv	Set the linear solver.	`-linsolv <ksparse|klu|superlu|aztecoo>`	klu (serial) aztecoo (parallel)
-ndl	Set the nonlinear solver debug level. (overrides netlist)	`-ndl <0..N>`	-

Argument	Description	Usage	Default
-tdl	Set the time integrator debug level. (overrides netlist)	`-tdl <0..N>`	-
-ddl	Set the device package debug level. (overrides netlist)	`-ddl <0..N>`	-
-sdl	Set the device sensitivity debug level. (overrides netlist)	`-ddl <0..N>`	-

Table 3.1: List of **Xyce** command line arguments.

4. Runtime Environment

There are two ways to start **Xyce**, using either `runxyce` for serial **Xyce** or `xmpirun` for parallel **Xyce**. These scripts set up the run time environment and call the **Xyce** executable.

Environment Variables

Environment variables are used to configure **Xyce**. Users may override the defaults by applying new values. Table 4.1 lists the environment variables and their usage.

Name	Purpose
`XYCE_METADATA_PATH`	Sets the path to the metadata configuration files.

Table 4.1. Environment variables used to control **Xyce**.

Running **Xyce** under MPICH

The MPICH implementation of MPI requires a file containing a list of machines on which to run. On RedHat Linux the file is installed in /usr/lib/mpich/share. On FreeBSD it is installed in /usr/local/mpich/share. This file must contain one line for each machine on which a process may be started. If you do not have write access this file, specify an alternate file with the `-machinefile <machinefilename>` option to `mpirun`.

MPICH executes parallel jobs by using the remote shell (rsh) or secure shell (ssh) to connect to the target machine. Therefore, you may be prompted for a password when starting a multiple processor job.

Running **Xyce** under LAM MPI

Unlike MPICH, LAM MPI requires a daemon process to run on each machine that will service parallel jobs. The process is started with `lamboot`. By default, `lamboot` will run a

daemon (`lamd`) on the local machine, but it may be given a file name containing a list of machines for multiple-machine jobs. Consult the `bhost` man page for the format of the file.

`lamd` will run until it is explicitly halted. As long as `lamd` is running you may continue to run parallel jobs. Halt `lamd` using the `lamhalt` command.

Running **Xyce** under HP/Compaq's OSF MPI implementation

On HP/Compaq systems running the OSF operating system, the appropriate command to run parallel jobs is `dmpirun`. Its usage is otherwise similar to the MPICH and LAM `mpirun` commands.

xmpirun Implementation Details

The `xmpirun` script abstracts away many details of the underlying MPI implementation. Its use is sufficient for starting most parallel **Xyce** jobs.

For reference, Table 4.2 shows the actual command executed on each of the supported platforms. Execution in parallel is highly dependent on the MPI runtime environment. The table only lists the method used when the `mpirun` program is in the default configuration.

System	Actual MPI command line
HP/Compaq OSF	`dmpirun -np 2 Xyce_alpha-osf1_MPI anExampleNetlist.cir`
SGI / IRIX 6.5	`mpirun -np 2 Xyce_sgi10k_MPI anExampleNetlist.cir`
Intel X86 / RedHat Linux with MPICH	`mpirun.mpich -np 2 Xyce_linux_MPI anExampleNetlist.cir`
Intel X86 / RedHat Linux with LAM MPI	`mpirun -np 2 Xyce_linux_MPILAM anExampleNetlist.cir`
Intel X86 / FreeBSD with MPICH	`/usr/local/mpich/bin/mpirun -np 2 Xyce_freebsd_MPI anExampleNetlist.cir`
Intel X86 / FreeBSD with LAM MPI	`mpirun -np 2 Xyce_freebsd_MPILAM anExampleNetlist.cir`

Table 4.2. Actual command line invoked by **xmpirun**. In this example, **Xyce** is using two processors to simulate anExampleNetlist.cir.

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5. Setting Convergence Parameters for **Xyce**

Because the solution algorithms and methods within **Xyce** are different than those used by other circuit simulation tools (e.g., ChileSPICE), the overall convergence behavior is sometimes different as are the parameters which control this behavior.

With **Xyce** Release 1.1 several of the default transient parameters have been changed to improve overall performance and help make **Xyce** more competitive with other codes. While these defaults have been extensively tested to ensure acceptable accuracy, it is possible that some accuracy has been lost in order to provide improved performance. While this is likely negligible, accuracy can be improved by tightening the error tolerances and/or changing the time-integration order from their default values. As this is typically an issue for transient simulations, the following discussion applies to that context only. For a complete list of available solution control options, go to 2.1 in chapter 2.

Adjusting Transient Analysis Error Tolerances

As of Release 1.1, the default for **Xyce** is to use a Backward Euler (BDF-1) time integration method (also known as a 1-step Gear method) for performing transient analysis [31]. This is equivalent to using a Gear method 1 in ChileSPICE (the ChileSPICE default is to use the trapezoid rule). In general, this method provides acceptable accuracy and improved performance for circuits with highly-oscillatory behavior, which seem to be prevalent among those modeled at Sandia. However, the previous default, BDF-2, is a more stable and more accurate method than the backward Euler method and in circuits which have a "smoother" behavior (e.g., digital circuits), can provide a much faster and more accurate solution. Users who are modeling digital or other "smooth" circuits should select this method via the netlist with an options line:

```
.OPTIONS TIMEINT METHOD=2
```

Setting `RELTOL` and `ABSTOL`

In **Xyce**, there is currently `RELTOL` and `ABSTOL` settings for both the time integration package and the nonlinear solver package. Some general guidelines for settings parameters are [31]:

- Use the *same* RELTOL and ABSTOL values for both the TIMEINT and the NONLIN-TRAN .OPTIONS statements.
- For a conservative approach (i.e., safe), set RELTOL=1.0E-(m+1) where m is the desired number of significant digits of accuracy.
- Set ABSTOL to the smallest value at which the solution components (either voltage or current) are essentially insignificant.
- *Note* that the above suggests that ABSTOL $<$ RELTOL.

The current defaults for these parameters are ABSTOL=1.0E-6 and RELTOL = 1.0E-2. For a complete list of the time integration parameters, see chapter 2.1.

Adjusting Nonlinear Solver Parameters (in transient mode)

In **Xyce**, the nonlinear solver options for transient analysis are set using the .OPTIONS NONLIN-TRAN line in a netlist. This subsection gives some guidelines for setting this parameters.

- For guidelines on setting RELTOL and ABSTOL, see above.
- RHSTOL – This is the maximum residual error for each nonlinear solution. **Xyce** uses this as a "safety" check on nonlinear convergence. Typically, 1.0E-2 (the default) works well.
- DELTAXTOL – This is the weighted update norm tolerance and is the primary check for nonlinear convergence. Since it is weighted (i.e., normalized using RELTOL and ABSTOL), a value of 1.0 would give it the same accuracy as the time integrator. For robustness, the default is 0.33 but sometimes a value of 0.1 may help prevent "time-step too small" errors. A value of 0.01 is considered quite small.
- MAXSTEP – This is the maximum number of Newton (nonlinear) steps for each nonlinear solve. In transient analysis, the default is 20 but can be increased to help prevent "time-step too small" errors. This is roughly equivalent to ITL4 in ChileSPICE.

6. Quick Reference for Orcad PSpice Users

This chapter describes many of the differences between **Xyce** and Orcad PSpice with an eye towards providing the ability for those familiar with using PSpice to begin using **Xyce** quickly. **Xyce** is still under development, so this section will change as new capabilities are added to **Xyce**. Also, note that there is also a quick reference chapter for ChileSPICE users 7, and many of the issues covered in that chapter are also applicable to PSpice.

GUI Support

Graphical User Interface (GUI) support for Xyce was released recently, and will become more tightly integrated into future **Xyce** releases. EsimTools 1.5 consists of an integrated package of schematic capture, simulation job submission (local and remote), and post-analysis plotting tools. A release of EsimTools targeted specifically at **Xyce** 3.0 is planned for October, 2005.

Command Line Options

Command line arguments are supported in **Xyce** but they are different than those of PSPICE. For a complete reference, see chapter 3.

Device Support

Most, but not all, devices commonly found in circuit simulation tools are supported. **Xyce** also contains enhanced versions of many semiconductor devices that simulate various environmental effects. For the complete list, please see the Analog Device Summary in Table 2.7.

Netlist Support

To the extent that specific devices or models are supported in **Xyce**, it supports most of the standard netlist inputs as may be found in standard SPICE. However, the `.OPTIONS` command has several additional features used to expose capabilities specific to **Xyce**. In particular, **Xyce** does not currently support the standard PSpice format `.OPTIONS` line in

netlists. Instead, package specific `.OPTIONS` lines are supported according to the following format: `.OPTIONS {PKG} <<TAG=>VALUE> ...` The **Xyce** packages which currently support `.OPTIONS` are:

Package	PKG keyword
Global:	`GLOBAL`
Device Model:	`DEVICE`
Time Integration:	`TIMEINT`
Nonlinear Solver:	`NONLIN`
Transient Nonlinear Solver:	`NONLIN-TRAN`
Continuation/Bifurcation Tracking:	`LOCA`
Linear Solver:	`LINSOL`
Output:	`OUTPUT`
Restart:	`RESTART`

For a complete description of the supported options, see section 2.1.

Xyce does not support the ".PROBE" statement. Output of Probe format files is done using the ".PRINT" netlist statement. See chapter 2 for syntax.

Xyce does not support PSPICE style abbreviations in the ".PRINT" statement. For example, to print out the value of the voltage at node `A` in a transient simulation you must request `.PRINT TRAN V(A)`, not `.PRINT TRAN A`.

Converting PSpice ABM Models for Use in **Xyce**

As of the **Xyce** Version 3.0 release, **Xyce** is almost fully compatible with PSpice with respect to analog behavioral models. This includes the `E`, `F`, `G`, and `H` device types. A notable exception to this compatibility is in the use of lead and device currents in expressions. These are limited to expressions in the ".PRINT" statement.

Usage of `.STEP` Analysis

The implementation of `.STEP` in **Xyce** is not yet fully compatible with that of PSpice. This will be corrected in subsequent releases of **Xyce**.

Sweep Type

PSpice supports four different sweep types: linear, octave, decade, and list. In **Xyce**, only the linear type is supported. Also, the **Xyce** parser will not understand a keyword specifying the sweep type. As such, this example will cause an error in **Xyce**:

Example: `.step LIN VCE 0V 10V .5V`

However, it should work fine if you remove the `LIN` keyword.

Global `.PARAM` Sweeps

PSpice also supports sweeps over variables specified in `.PARAM` lines. This is not supported in **Xyce**. This block of text will not work in **Xyce**:

```
VAB 2 0 5
VAC 1 0 variable
.param variable=0
.step param variable 0 5 1
.dc VAB 4 5 1
```

An equivalent block of code that will work in **Xyce** is:

```
VAB 2 0 5
VAC 1 0 5
.step VAC 0 5 1
.dc VAB 4 5 1
```

Model Parameter Sweeps

PSpice requires extra keywords to apply a `.STEP` statement to a model parameter. **Xyce** handles model parameters differently, and is actually somewhat more flexible. Unfortunately, this means that the two specifications are not compatible.

A model parameter in PSpice would be handled like this:

```
R1 1 2 RMOD 1
.model RMOD RES(R=30)
.step RES RMOD(R) 30 50 5
```

The equivalent way to specify this in **Xyce** would be:

```
R1 1 2 RMOD 1
.model RMOD RES(R=30)
.step RMOD:R 30 50 5
```

Note that **Xyce** does not require the `RES` keyword on the `.STEP` line. In PSpice, this keyword is needed to specify what type of model is being used. **Xyce** actually has more flexibility than PSpice in this regard - any model or instance variable can be set, on the `.STEP` line, using the same syntax.

Example: `.step D101:IS 1.0e-3 5.0e-3 1.0e-3`

In this example, `D101` is the name of a model, or instance, and `IS` is the name of the parameter within that model or instance.

Other differences

Some other differences between **Xyce** and PSpice are described in table 6.1.

Issue	Comment
`.VECTOR`, `.WATCH`, and `.PLOT` output control analysis are not supported.	**Xyce** currently does not support these commands. If enough users request them, they may be supported in the future.
`.AC`, `.FOUR`, `.NOISE`, `.SENS` and `.TF` analysis types are not supported.	**Xyce** fully supports `.DC` and `.TRAN` analysis. `.OP` is partially supported. `.AC` and `.SENS` are planned features. Other analyses, such as `.NOISE` may be supported in the future, if enough users request them.
`.MC` and `.WCASE` statistical analyses are not supported.	**Xyce** currently does not support these commands. If enough users request them, they may be supported in the future.
`.DISTRIBUTION`, which defines a user distribution for tolerances, is not supported.	**Xyce** does not support this command. This command goes along with `.MC` and `.WCASE` statistical analyses, which are also not supported.
`.LOADBIAS`, `.SAVEBIAS`, and `.NODESET` initial condition commands are not supported.	**Xyce** does not support these commands.
`.ALIASES`, `.ENDALIASES`, are not supported.	**Xyce** does not support these commands.
`.STIMULUS` is not supported.	**Xyce** does not support this command.
`.TEXT` is not supported.	**Xyce** does not support this command.
`.SAVE` does not work	**Xyce** does not support this. Use .PRINT instead.
`.PROBE` does not work	**Xyce** does not support this. Use the FORMAT=PROBE option of .PRINT instead. See section 2 for syntax.
`.OP` is incomplete	An .OP netlist will run in **Xyce**, but will not produce the extra output normally associated with the .OP statement.

Issue	Comment
`.SENS` is only supported in the development builds of **Xyce**	This is currently a research issue in **Xyce**, and will be available in later release versions of **Xyce**.
Pulsed source rise time of zero	A requested pulsed source rise/fall time of zero really is zero in **Xyce**. In other simulators, requesting a zero rise/fall time causes them to use the printing interval found on the tran line.
Mutual Inductor Model	Not the same as PSpice. This is a Sandia developed model.
`.PRINT` line shorthand	Output variables have to be specified as a V(node) or I(source). Listing the node alone will not work.
BSIM3 level	In **Xyce** the BSIM3 level=9. In PSpice the BSIM3 is level=8.
Node names vs. device names	Currently, circuit nodes and devices *MUST* have different names in **Xyce**. Some simulators can handle a device and a node with the same name, but **Xyce** cannot.
Interactive mode	**Xyce** does not have an interactive mode.
Time integrator default tolerances	**Xyce** has much tighter default solver tolerances than some other simulators (e.g., PSpice), and thus often takes smaller time steps. As a result, it will often take a greater number of total time steps for a given time interval. To have **Xyce** take time steps comparable to those of PSpice, set the `RELTOL` and `ABSTOL` time integrator options to larger values (e.g., `RELTOL=1.0E-2`, `ABSTOL=1.0E-6`).
`.OPTIONS` statements	**Xyce** does not support PSpice style `.OPTION` statements. In **Xyce**, the various packages all (potentially) have their own separate `.OPTIONS` line in the netlist. For a complete description, see section 2.1.
`DTMAX`	**Xyce** does support a maximum time step-size control on the .tran line, but we discourage its use. The time integration algorithms within **Xyce** use adaptive time-stepping methods that adjust the time-step size according to the activity in the analysis. If the simulator is not providing enough accuracy, the `RELTOL` and `ABSTOL` parameters should be decreased for both the time integration package (`.OPTIONS TIMEINT`) and the transient nonlinear solver package (`.OPTIONS NONLIN-TRAN`). We have found that in most cases specifying the same maximum timestep that PSpice requires for convergence actually slows Xyce down by preventing it from taking larger timesteps when the behavior warrants.
Nonlinear Dependent Source (B source) syntax	**Xyce** requires curly braces around all ABM expressions, where PSpice does not. See section 2.

Issue	Comment
`.TRAN` "`UIC`" keyword	PSpice requires the use of a keyword `UIC` on the `.TRAN` line in order to use initial conditions via `IC` keywords on instance lines. Doing so also tells PSpice not to perform an operating point calculation. In **Xyce**, `UIC` is ignored and produces a warning message. **Xyce** always uses initial conditions specified with `IC` keywords, and the case of inductors and capacitors automatically inserts a fictitious voltage source around the device that guarantees the correct potential drop across the device during the operating point. If the user desires that Xyce not perform an operating point calculation, but rather use an initial condition for a transient run of all zero voltages, then the user should specify `NOOP` instead.
`.TRAN` **Tstart** parameter	PSpice uses the third parameter of the `.TRAN` line as the time at which to begin outputting results. **Xyce** simply uses it as an offset to be applied to the time variable. To discard early parts of a run in **Xyce**, use a `.OPTIONS OUTPUT` line.
Temperature specification	Device temperatures in **Xyce** are specified through the `.OPTIONS DEVICE` line. PSpice allows a `.TEMP` line that is not recognized (and is ignored) by **Xyce**.

Table 6.1: Incompatibilities with PSpice.

7. Quick Reference for ChileSPICE Users

A large number of potential **Xyce** users have experience using Sandia's ChileSPICE circuit simulator, which is a shared-memory parallel code based on Berkely's SPICE version 3f5. Table 7.1 lists some of the differences between ChileSPICE and **Xyce**. Many of these are the same as the differences between PSpice and **Xyce**, which were listed in table 6.1.

Issue	Comment
`.SAVE` does not work	**Xyce** does not support this. Use .PRINT instead.
`.PROBE` does not work	**Xyce** does not support this. Use the FORMAT=PROBE option of .PRINT instead. See section 2 for syntax.
`.OP` is incomplete	An .OP netlist will run in **Xyce**, but will not produce the extra output normally associated with the .OP statement.
Pulsed source rise time of zero	A requested pulsed source rise/fall time of zero really is zero in **Xyce**. In other simulators, requesting a zero rise/fall time causes them to use the printing interval found on the tran line.
Mutual Inductor Model	Not the same as PSPICE. This is a Sandia developed model.
`.PRINT` line shorthand	Output variables have to be specified as a V(node) or I(source). Listing the node alone will not work.
BSIM3 level	In **Xyce** the BSIM3 level=9. In ChileSPICE the BSIM3 is level=8.
Node names vs. device names	Currently, circuit nodes and devices *MUST* have different names in **Xyce**. Some simulators can handle a device and a node with the same name, but **Xyce** cannot.
Time integrator default tolerances	**Xyce** has much tighter default solver tolerances than some other simulators (e.g., ChileSPICE), and thus often takes smaller time steps. As a result, it will often take a greater number of total time steps for a given time interval. To have **Xyce** take time steps comparable to those of ChileSPICE, set the `RELTOL` and `ABSTOL` time integrator options to larger values (e.g., `RELTOL=1.0E-2`, `ABSTOL=1.0E-6`).
ChileSPICE-specific "operating point voltage sources"	These are not currently supported within **Xyce**. The capacitor, inductor, BSIM3, and B3SOI are the only devices that currently support the "IC=" parameter, both insert the equivalent of operating-point voltage sources automatically when an initial condition is given.

Issue	Comment
.OPTIONS statements	**Xyce** does not support ChileSPICE style .OPTION statements. In **Xyce**, the various packages all (potentially) have their own separate .OPTIONS line in the netlist. For a complete description, see section 2.1.
DTMAX	**Xyce** does support a maximum time step-size control on the .tran line, but we discourage its use. The time integration algorithms within **Xyce** use adaptive time-stepping methods that adjust the time-step size according to the activity in the analysis. If the simulator is not providing enough accuracy, the RELTOL and ABSTOL parameters should be decreased for both the time integration package (.OPTIONS TIMEINT) and the transient nonlinear solver package (.OPTIONS NONLIN-TRAN). We have found that in most cases specifying the same maximum timestep that ChileSPICE requires for convergence actually slows Xyce down by preventing it from taking larger timesteps when the behavior warrants.
Nonlinear Dependent Source (B source) syntax	**Xyce** requires curly braces around all ABM expressions, where ChileSPICE does not. See section 2.
.TRAN "UIC" keyword	SPICE 3F5 requires the use of a keyword UIC on the .TRAN line in order to use initial conditions via IC keywords on instance lines. Doing so also tells SPICE 3F5 not to perform an operating point calculation. In **Xyce**, UIC is ignored and produces a warning message. **Xyce** always uses initial conditions specified with IC keywords, and the case of inductors and capacitors automatically inserts a fictitious voltage source around the device that guarantees the correct potential drop across the device during the operating point. If the user desires that Xyce not perform an operating point calculation, but rather use an initial condition for a transient run of all zero voltages, then the user should specify NOOP instead.
.TRAN **Tstart** parameter	SPICE 3F5 uses the third parameter of the .TRAN line as the time at which to begin outputting results. **Xyce** simply uses it as an offset to be applied to the time variable. To discard early parts of a run in **Xyce**, use a .OPTIONS OUTPUT line.
Temperature specification	Device temperatures in **Xyce** are specified through the .OPTIONS DEVICE line. ChileSPICE allows a .TEMP line that is not recognized (and is ignored) by **Xyce**.
AREA parameter for radiation aware devices	The diode and BJT support a parameter on the instance line called AREA, and in both standard and radiation aware devices this is used to scale certain model parameters. In ChileSPICE this same parameter is used to scale the photocurrent. In **Xyce** it is used only to scale the model parameters, and a new model parameter DEVICEAREA is used to scale the photocurrent. This enables SPUDS data sets for real devices to be used unmodified except for the addition of the radiation-specific parameters. ChileSPICE requires that the scaled model parameters be adjusted to take into account the device area parameter.

Issue	Comment
.STEP syntax is not the same.	This issue is well covered in the PSpice quick reference. See section 6.

Table 7.1: Incompatibilities with ChileSPICE.

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8. Quick Reference for Microsoft Windows Users

Xyce is supported on Microsoft Windows. However, the primary targets for **Xyce** are high-performance supercomputers and workstations, which are almost always running a variant of Unix. Also, 99% of **Xyce** developement is done on Unix platforms. Bearing this in mind, there are occasionally issues with using a Unix application on a Windows platform. Some of these issues are described in the table below.

Issue	Comment
File names need to be case-sensitive	**Xyce** will expect library files, which are referenced in the netlist, to have exactly the same case as the actual filename. If not, **Xyce** will be unable to find the library file.
Xyce is unable to read proprietary file formats.	Programs such as Microsoft Word by default use file formats that **Xyce** cannot recognize. It is best not to use such programs to create netlists, unless netlists are saved as *.txt files. If you must use a Microsoft editor, it is better to use Microsoft Notepad. In general, the best solution is to use a Unix-style editor, such as Vi, Gvim, or Emacs.

Table 8.1: Issues for Microsoft Windows.

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9. Rawfile Format

The rawfile format produced by **Xyce** closely follows Spice3 conventions. Differences are noted in section 9. Details on the both the ascii and binary formats are provided here for reference.

Ascii Format

The ascii format consists of lines or sets of lines introduced by a keyword. The `Title` and `Date` lines should be the first in the file and should occur only once, followed by the `Plotname`, `Flags`, `No. Variables`, `No. Points`, `Variables`, and `Values` lines. Note that after the `Variables` keyword there must be *numvars* declarations of outputs, and after the `Values` keyword, there must be *numpoints* lines, each consisting of *numvars* values.

Line Name	Description
`Title:`	An arbitrary string describing the circuit
`Date:`	A free-format date string
`Plotname:`	A string describing the analysis type
`Flags:`	A string describing the analysis type. *real*
`No. Variables:`	The number of variables
`Variables:`	The number of points
`Variables:`	A newline followed by multiple lines, one for each variable, of the form `[tab] <index> [tab] <name> [tab] <type>` where type is either *current* or *voltage*.
`Values:`	A newline followed by multiple lines, for each point and variable, of the form `[tab] <value>` with an integer index preceeding each set of points.

Table 9.1. Xyce ascii rawfile format.

Binary Format

The binary format is similar to the ascii format, except that strings are null terminated rather than newline terminated. Binary storage of real values as double precision floats is architecture specific.

Line Name	Description
`Title:`	An arbitrary string describing the circuit
`Date:`	A free-format date string
`Plotname:`	A string describing the analysis type
`Flags:`	A string describing the analysis type. *1*
`No. Variables:`	The number of variables
`Variables:`	The number of points
`Variables:`	A newline followed by multiple lines, one for each variable, of the form `[tab] <index> [tab] <name> [tab] <type>` where type is either *current* or *voltage*.
`Binary:`	Each real data point is stored contiguously in `sizeof(double)` byte blocks.

Table 9.2. Xyce binary rawfile format.

Special Notes

- Complex data points are not used.
- `Commands` and `Options` lines are not used.
- Limited to single dimension and single plot.
- Binary header is formatted ascii.

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